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# SAR Induced by Low and High Directivity Antenna Apertures at Distances Greater than $\mathbf{2 5} \mathbf{~ m m}$ from the Body 

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#### Abstract

A comprehensive SAR study of low and high directivity antennas operated at distances greater than 25 mm but less than 200 mm from a large homogeneous elliptical phantom is presented. The study considers antennas, such as dipoles, monopoles, planar inverted-F antennas (PIFAs), IFAs, patches, patch arrays, and dipole arrays. SAR estimation methods for low directivity antennas for both near and far field conditions are proposed and elucidated. For directive antennas and arrays radiating directly towards the phantom interesting phenomena are observed that require more detailed investigation.


Index Terms - Antennas, arrays, directive, RF exposure, small antennas, specific absorption rate (SAR).

## I. INTRODUCTION

Electromagnetic exposures from wireless transmitters are regulated by respective regulatory bodies that restrict such exposure both for the general public and occupational professionals. The respective exposure limits (specific absorption rate - SAR) for the general public are identified as $1.6 \mathrm{~W} / \mathrm{Kg}$ averaged over $1-\mathrm{g}$ of tissue as established by the Federal Communications Commission (FCC) [1], and $2.0 \mathrm{~W} / \mathrm{Kg}$ averaged over $10-\mathrm{g}$ of tissue as established by the European Committee for Electrotechnical Standardization (CENELEC), which refers to exposure limits recommended in [2]. SAR induced in homogeneous and heterogeneous head and body phantoms has been studied for decades leading to new knowledge and standards set forth by respective standards bodies, such as the IEEE [3-4] and ICNIRP [5]. SAR studies have been conducted considering different types and sizes of antennas, various wireless device models, head models, head shapes, and sizes [6-18]. Traditionally from a compliance point of view, wireless device manufacturers
have to measure SAR except for devices that are inherently compliant because of their very low transmit power; for example 1 mW for the FCC and 20 mW for CENELEC.

Given the presence of myriad wireless devices with variety of output power specifications, device geometry and size variations, and antenna geometry and size variations, it is quite overwhelming to fully grasp and quantify SAR as function of simple metrics, such as operating frequency, power, distance from device, and some simple easy to measure antenna characteristics. A simple method of estimation has two benefits, one, it leads to clear understanding by the antenna designer whether the device is in the ballpark to meet the requirements and whether for low power transmitters the device may be automatically exempt from SAR testing given such tests are costly, man-power intensive, and time consuming. With these outcomes in mind our research groups undertook SAR studies of a variety of antenna sizes and geometries when they were operated next to a flat phantom at distances less than 25 mm . The results of the first phase of our research were published in [19-21]. Subsequently, a more extensive study was undertaken to explore any empirical relationships between antenna performance metrics and SAR [22-25]. Based on that comprehensive study SAR estimation formulas were developed for devices that operate at distances 25 mm or less from the body within the frequency range of 300 MHz to 6 GHz [25]. These formulas can be used to estimate the threshold power levels that satisfy both the $1.6 \mathrm{~W} / \mathrm{Kg}$ and the $2.0 \mathrm{~W} / \mathrm{Kg}$ SAR limits. These formulas were developed as function of frequency, antenna to body separation, and antenna free-space bandwidth (BW). Later on the results of this study were adopted into an IEC Standard [26].

The reason for choosing the antenna free-space BW for the rationale lies in the fact that BW is the
reciprocal of antenna quality factor $(\mathrm{Q})$, and Q is expressed as the ratio of the stored and radiated energies of the antenna. Since SAR is strongly dependent on the stored near-fields of wireless device antennas (within $5-25 \mathrm{~mm}$ from the user's body), an empirical relationship between SAR or threshold power and BW was possible. As mentioned, the empirical formulas were developed considering SAR data of dipole antennas against a flat phantom.

Although that study covered the frequency range of $300-6000 \mathrm{MHz}$, the antenna to body distances over which the study focused on was less than 25 mm . Furthermore, the study also did not consider the SAR induced by directive antennas radiating directly towards the body. This led us to carry on a follow on further investigation that addresses these particular issues. Some preliminary results and conclusions of this work were presented earlier [27-28].

In this work we report the simulation and experimental results of SAR induced by a variety of electrically small non-resonant dipoles, resonant dipoles, resonant monopoles, planar inverted-F antennas, inverted-F antennas, microstrip patches, patch arrays and dipole arrays. The goal of this paper is to understand the SAR implications due to small low directivity antennas as well as highly directive antennas radiating directly towards the phantom when the antenna to phantom separation distance is within 40200 mm . Since the distances are large, we considered to use a large elliptical flat phantom as defined in [29].

The details of the simulation and measurement methods are available in our earlier work [25]. Briefly, all simulations were performed using the Remcom Inc. commercial FDTD code called XFDTD. The XFDTD models containing dipole antennas were earlier validated [21] against the half-wave dipole data presented in IEEE Std. 1528-2003. The Liao absorbing boundary condition (ABC) was used to save simulation time. Before doing so, the Liao ABC usage was verified by comparing with PML (perfectly matched layers) ABC data. For impedance simulations, Gaussian pulses were used with automatic convergence at a threshold of -40 dB , while for SAR simulations, a sinusoidal waveform was used. The mesh size was generally uniform ( 1 mm ), except for planar antennas we used graded mesh having a minimum mesh size of 0.25 mm and a maximum mesh size of 1 mm . All SAR measurements were carried out with the antennas placed next to the elliptical flat phantom ELI4 (Schmid \& Partner Engineering AG, Zurich, Switzerland) containing tissue equivalent liquids for the respective frequencies. The dielectric properties of the liquids were measured prior to SAR measurements using a dielectric probe kit in combination with a vector network analyzer. All SAR measurements were conducted using the DASY3 system (Schmid \& Partner

Engineering AG, Zurich, Switzerland).
As it will transpire from the results and discussions, the issue of SAR at larger distances are governed by many factors including the location of the body (near-field, far field, aperture size to phantom size comparison, aperture directivity etc.).

The paper is organized as follows. First, the simulation and experimental landscape is defined that includes the frequencies, the distances, and the antennas considered in the study. Second, SAR results of low directivity antennas such as dipoles, monopoles, and PIFAs are described. Third, SAR results of directional patch antennas, patch arrays, and dipole arrays are elucidated. Fourth, a detailed comparison of the SAR data among different antenna classes is provided. And finally, an attempt is taken to suggest SAR estimation algorithms for these large distances followed by suggestion for future research works.

## II. ANTENNA AND PHANTOM MODELS

The antenna types studied and their associated operating frequencies are listed in Table 1. Antenna simulation models as well as experimental prototypes were designed and developed for operation at 900, 1900, 2450, 3700 , and 6000 MHz to reflect many commercial wireless applications in those frequency bands. Antennas were oriented and placed next to a large elliptical phantom at distances of 40,100 , and 200 mm for SAR calculation and measurements. Here distance, $d$, is defined as the distance from the antenna feed point to the phantom. Although data at other intermediate distances could have added more insight for the sake of saving simulation and measurement time, the above distances were considered.

Table 1: Antenna types studied and their associated frequencies. Distances from phantom were 40, 100, and 200 mm for all antennas

| Antenna Type | Frequency (MHz) |  |  |  |  |
| :--- | :---: | :---: | :---: | :---: | :---: |
|  | 900 | 1900 | 2450 | 3700 | 6000 |
| Dipole | X | X | X | X | X |
| Monopole | X | X | X |  |  |
| PIFA air | X | X |  |  |  |
| PIFA surface |  |  | X | X |  |
| IFA |  |  | X | X |  |
| DB-PIFA | X | X |  |  |  |
| DB-IFA |  |  | X |  | X |
| Patch |  | X | X | X | X |
| Patch array |  | X | X | X | X |
| Dipole array |  |  | X |  |  |

All low directivity apertures are identified in Table 2, while the directive apertures are defined in Table 3. Among directive antennas, microstrip patch antennas printed on FR substrates and then placed on the edge of
a metal box ( 10 mm thick) were considered. Patches were designed and built for operation at 1900, 2450, 3700 , and 6000 MHz . Similarly, corporate-fed four element microstrip patch array apertures were also designed and built for operation at 1900, 2450, 3700, and 6000 MHz . Collinear arrays of 3,5 , and 7 element dipoles were simulated with and without the presence of reflectors for SAR at 2450 MHz only.

Table 2: Low directivity antenna specifics; e.g., sizes and geometrical properties

| Photographs | Description |
| :---: | :---: |
| 入/2 |  |
|  | $\lambda / 15$ (simulation only) and $\lambda / 2$ wire dipoles, center fed; $\lambda / 4$ balun used; wire radius $=1.8 \mathrm{~mm}$ for frequencies up to 2450 MHz and wire radius $=0.5 \mathrm{~mm}$ at 3700 and 6000 MHz |
| Dipoles |  |
|  | $\lambda / 4$ long, wire radius $=1.8 \mathrm{~mm}$; wire on top of a metal box (box dimensions 100 mm by 40 mm by 19 mm ) |
|  | $L=40 \mathrm{~mm}, W=31 \mathrm{~mm}$ by 6 mm at 900 MHz and $L=20 \mathrm{~mm}, W=13.5 \mathrm{~mm}$ by 6 mm at 1900 MHz ; feed/shorting pin using 1 mm wide strips; spacings of 2.5 and 2 mm at 900 and 1900 MHz |
|  | $L=16 \mathrm{~mm}, W=1 \mathrm{~mm}$ at 2450 MHz on 100 mm by 40 mm by 10 mm metal box |
|  | 2450 MHz IFA shown |
|  | 2450/6000 MHz DB-PIFA |
|  | 2450/6000 MHz DB-IFA |

Table 3: High directivity antenna/array specifics; e.g., sizes and geometrical properties

| Photographs/ Diagrams | Description; Dimensions in mm |  |  |  |
| :---: | :---: | :---: | :---: | :---: |
|  | Freq. (GHz) | $L$ | W | Feed Offset |
| $40 . y$ | 1.9 | 35.5 | 36.5 | 9.25 |
|  | 2.45 | 27.5 | 36.5 | 6.25 |
|  | 3.7 | 17.5 | 24 | 4.00 |
| Patch | 6.0 | 11 | 15 | 1.00 |
| Patch array | Directivities of $10.9,13.2,11.6$, and 11.4 dBi at $1900,2450,3700$, and 6000 MHz respectively. Array approximately 1.5 wavelength. 1.9 GHz array photo shown. |  |  |  |
|  |  |  |  |  |
| 2.45 GHz linear dipole array |  |  |  |  |

Dipoles were studied at all frequencies while monopoles were studied at 900, 1900, and 2450 MHz . PIFAs on air or foam were studied at 900 and 1900 MHz to reflect mobile phone frequency bands. Surface mount PIFAs and IFAs were studied at higher frequencies to reflect their operation to support Bluetooth and WLAN type operations. Directional microstrip patches and patch arrays were investigated at $1900,2450,3700$, and 6000 MHz . All planar antennas were studied both in the conventional (antenna element or array faces away from the body) and flipped orientations (antenna element or array faces the body) with respect to the phantom.

The geometry of the elliptical phantom used is shown in Fig. 1. The phantom consisted of a 2 mm thick shell with dielectric constant $\varepsilon_{\mathrm{r}}=3.7$ and $\sigma=0$. The antenna to phantom distance is d . The tissue dielectric constant and conductivity values are given in Table 4. These values were obtained from [29].


Fig. 1. Geometry of the phantom.

Table 4: Phantom tissue relative permittivity and conductivity. Tissue mass density, $\rho=1000 \mathrm{Kg} / \mathrm{m}^{3}$

| Frequency <br> $(\mathrm{MHz})$ | 900 | 1900 | 2450 | 3700 | 6000 |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Relative <br> Permittivity, $\varepsilon_{\mathrm{r}}$ | 41.5 | 40 | 39.2 | 37.7 | 35.1 |
| Conductivity, <br> $\sigma(\mathrm{S} / \mathrm{m})$ | 0.97 | 1.4 | 1.8 | 3.12 | 5.48 |

## III. RESULTS

## A. SAR results of dipole antennas

Computed peak $1-\mathrm{g}$ and $10-\mathrm{g}$ averaged SAR for $\lambda / 15$ and $\lambda / 2$ dipoles placed at $d=40 \mathrm{~mm}, 100 \mathrm{~mm}$ and 200 mm from the phantom are shown in Figs. 2 (a)-(c). All data are normalized to 1 W of power. Measured $1-\mathrm{g}$ and $10-\mathrm{g}$ averaged SAR data for $\lambda / 2$ dipoles are also shown. For all cases, the simulated and measured results are in good agreement. From Fig. 2 (a) for the case when $d=40 \mathrm{~mm}$, it is clear that the largest difference in SAR between the $\lambda / 15$ and $\lambda / 2$ dipoles occurs at the lowest frequency ( 900 MHz ). At this frequency the phantom is still in the near field of the antenna. Therefore, the shorter antenna induces almost twice as much SAR than that induced by the longer antenna. As explained in [21], when the phantom is in the near field of the antenna, the shorter antenna acts almost as a point source resulting in a more localized SAR distribution. Also for $d=40 \mathrm{~mm}$, as the frequency increases (e.g., at 2450 MHz and higher) the SAR induced by the $\lambda / 15$ and $\lambda / 2$ dipoles are nearly identical to each other as because the aforementioned near field effect disappears.

From Figs. 2 (b) and 2 (c) ( $d=100 \mathrm{~mm}$ and 200 mm ), it is clear that if the phantom is in the far field of the antennas, the antenna with the slightly higher directivity induces slightly higher SAR. The SAR behavior observed at around 2450 MHz can be explained from the tissue conductivity versus frequency characteristics. The non-linear conductivity increase from 900 MHz to 2450 MHz is responsible for the non-linear SAR profiles shown in Figs. 2 (a) and 2 (c).

(a)

(b)

(c)

Fig. 2. SAR versus frequency of dipole antennas for $d=40 \mathrm{~mm}, 100$ and 200 mm .

## B. SAR results of monopole antennas

Computed and measured peak $1-\mathrm{g}$ and $10-\mathrm{g}$ averaged SAR induced by quarter-wavelength long monopole antennas are compared with those induced by half-wave dipoles in Figs. 3 (a)-(c) for $d=40,100$, and 200 mm . Note that, since the monopole box measures 19 mm in thickness for $d=40 \mathrm{~mm}$, the box is at a distance of 21 mm from the phantom.

For all three distances, the SAR due to monopole antennas are always smaller than the SAR due to dipole antennas. For $d=40 \mathrm{~mm}$, the SAR variation due to monopole antennas with frequency is monotonous (decreases almost linearly with frequency). For $d=100 \mathrm{~mm}$, the SAR versus frequency characteristics for the monopoles is similar to that of the dipoles except for the inflection point at 1900 MHz . The situation is nearly similar at $d=200 \mathrm{~mm}$. At 100 and 200 mm distances, monopole $1-\mathrm{g}$ and $10-\mathrm{g}$ SAR decrease till 1900 MHz and then increase with frequency. This does not occur for the dipoles because the SAR distributions for monopoles are different than dipoles. There are multiple SAR hot spots for the monopoles (caused by the current distribution along the metallic box) while there is a distinct one hot spot for the dipoles.

(a)

(b)

(c)

Fig. 3. SAR versus frequency of monopole antennas for $d=40 \mathrm{~mm}$ and $d=100 \mathrm{~mm}$.

## C. SAR results of planar inverted-F antennas (PIFAs)

SAR induced by planar inverted-F antennas (PIFAs) in the conventional orientation with respect to the phantom (here the antenna faces away from the phantom) for $d=40,100$, and 200 mm are shown in Figs. 4 (a)-(c). At $d=40 \mathrm{~mm}$, the SAR due to PIFAs decrease with frequency monotonously like that for the monopole antennas on boxes. In almost all cases the SAR due to PIFAs is smaller than the SAR due to $\lambda / 2$ dipoles except for the PIFA operating at 900 MHz and $d=40 \mathrm{~mm}$.

(a)

(b)

(c)

Fig. 4. SAR versus frequency of PIFAS in conventional orientation for $d=40 \mathrm{~mm}, 100 \mathrm{~mm}$ and $d=200 \mathrm{~mm}$.

Nevertheless, even in this case the SAR due to a $\lambda / 15$ dipole is considerably higher ( $4 \mathrm{~W} / \mathrm{kg}$ - Fig. 2 (a)) than that due to the PIFA in question here ( $3 \mathrm{~W} / \mathrm{kg}$ ). For larger distances (e.g., $d=100$ and 200 mm ), the rate of decrease in SAR from 1900 MHz to 2450 MHz is rapid. This occurs because the 2450 MHz PIFAs being printed on FR4 substrates are lossy $(\tan \delta=0.02)$ as opposed to the 900 and 1900 MHz PIFAs which are fabricated in air. This results in decreased SAR which did not occur for the dipoles or the quarter-wave monopoles on boxes. For example, at $d=200 \mathrm{~mm}$ and at 2450 MHz the power dissipated for a $\lambda / 2$ dipole in the tissue was
0.112 W out of 1 W of input power. By contrast, for the same distance and at the same frequency the power lost in the FR4 substrate was 0.504 W and the power dissipated in the tissue was 0.0283 W .

## D. Comparison

SAR induced by other antenna types, sizes were also simulated and measured. All simulation and measurement data are available in [30] and [31]. However, for the sake of clarity and brevity instead of showing SAR results for each individual antenna class separately, a comparison of the simulated peak $1-\mathrm{g}$ averaged SAR induced by all low directivity antennas studied are plotted as scatter plots in Fig. 5 (i). The same for peak $10-\mathrm{g}$ averaged SAR induced by all low directivity antennas studied are plotted as scatter plots in Fig. 5 (ii).

For comparison, the SAR induced by single microstrip patch antennas radiating directly towards the phantom are also shown in these figures. Microstrip patch results are available at $1900,2450,3700$, and 6000 MHz . It is evident from Figs. 5 (i) and 5 (ii) that, patches radiating away from the phantom (ground plane facing the phantom) induce very low SAR.

Comparing the peak $1-\mathrm{g}$ SAR data at all three distances it is clear that:

- Except for the microstrip patch antennas that are radiating directly towards the phantom, the SAR induced by dipole antennas are the highest compared to all antennas in this study. This observation is consistent with our earlier work [25].
When comparing the SAR due to dipoles and patches flipped, it is clear that:
- At 1900 MHz , the SAR due to patches at all three distances are smaller than the SAR due to dipoles or about the same.
- At 2450 MHz , the SAR due to patches is only slightly higher than the SAR due to dipoles.
- At 3700 MHz and higher, the SAR due to patches are consistently higher than the SAR due to dipoles. Specifically at 6000 MHz and at $d=200 \mathrm{~mm}$, the SAR due to a flipped patch is about 3 times the SAR due to a dipole.
To put these results in perspective, the near-field and radiating near-field boundaries of different antenna apertures are plotted in Fig. 6. For antennas smaller than $0.5 \lambda$, this boundary was evaluated as $\lambda / 2 \pi$. At 900 MHz , this boundary starts at a radius of 50 mm from the antenna. As the frequency increases the radius of
this boundary decreases and vice versa. This is exactly what we see from the $1-\mathrm{g}$ SAR data of the flipped patches. When the frequency is sufficiently high, e.g., 6 GHz the phantom is indeed in the far field of the antenna and thus the $1-\mathrm{g}$ SAR induced is the SAR due to a small dipole (at that frequency and distance) times the linear gain of the patch antenna over the dipole.

However, if the phantom is not sufficiently in the far field, then estimating SAR by multiplying dipole SAR with the linear gain of the directive antenna will result in an over estimation of the SAR. Now for low directivity antennas that are strictly in the near field, we examine in the following if our earlier developed formulas that were reported in [25] can still be used at other distances than they were originally developed for (antenna to phantom separation, $s<25 \mathrm{~mm}$ ).





Fig. 5 (i). Peak 1-g averaged SAR comparison of all antennas at 40, 100, and 200 mm distances.


Fig. 5 (ii). Peak 10-g averaged SAR comparison of all antennas at 40,100 , and 200 mm distances.


Fig. 6. Near-field boundary distances of different apertures.

In contrast, peak $10-\mathrm{g}$ averaged SAR data plotted in Fig. 5 (ii) clearly shows that the only frequency at
which the SAR due to the flipped patch is higher than the dipoles is only 6 GHz . This can be explained by the fact that, under far field conditions, the patch in flipped orientation causes a more focused SAR hot spot on the phantom when compared to the dipoles. This is not the case when the phantom is in the near field of the antennas. The general trend of lower average SAR values for larger averaging volumes is therefore increasingly more enhanced for the patch antenna when the distance between patch antenna and phantom approaches or exceeds the near-field/far field boundary distance. In [25], we developed a rationale to estimate the threshold power that corresponded to the $1-\mathrm{g}$ and $10-\mathrm{g}$ averaged SAR based on the operating frequency, $f$, antenna to phantom separation, $s$, and the antenna half power free-space bandwidth, $B W$. This equation is given below:

$$
\begin{equation*}
P_{\max , m}=\exp \left(A s+B s^{2}+C \ln (B W)+D\right) \tag{1}
\end{equation*}
$$

Both $1-\mathrm{g}$ and $10-\mathrm{g}$ averaged SAR can be calculated from (2) if $P_{m a x, m}$ is known from (1) and considered as a best fit underestimate for $P_{t h, m}$ :

$$
\begin{equation*}
S A R_{m}=P_{t} \frac{S A R_{\mathrm{limit}, m}}{P_{\mathrm{P} h, m}} \tag{2}
\end{equation*}
$$

This led to the following solution for $S A R_{1 \mathrm{~g}}=1.6 \mathrm{~W} / \mathrm{kg}$ :

$$
\begin{gather*}
A=\left(-0.4922 f^{3}+4.831 f^{2}-6.620 f+8.312\right) / 100  \tag{3a}\\
B=\left(0.1191 f^{3}-1.470 f^{2}+3.656 f-1.697\right) / 1000  \tag{3b}\\
C=\left(-0.4228 f^{3}+13.24 f^{2}-108.1 f+339.4\right) / 1000  \tag{3c}\\
D=-0.02440 f^{3}+0.4075 f^{2}-2.330 f+4.730 \tag{3d}
\end{gather*}
$$

For $S A R_{10 \mathrm{~g}}=2 \mathrm{~W} / \mathrm{kg}$, the following solution was obtained:

$$
\begin{aligned}
& A=\left(-0.4588 f^{3}+4.407 f^{2}-6.112 f+2.497\right) / 100, \\
& B=\left(0.1160 f^{3}-1.402 f^{2}+3.504 f-0.4367\right) / 1000, \\
& C=\left(-0.1333 f^{3}+11.89 f^{2}-110.8 f+301.4\right) / 1000,
\end{aligned}
$$

$$
\begin{equation*}
D=-0.03540 f^{3}+0.5023 f^{2}-2.297 f+6.104 \tag{4d}
\end{equation*}
$$

In (3) and (4), $f$ is expressed in GHz. The freespace BW (assuming antennas are perfectly matched at their operating frequencies using lossless components) of dipole antennas are listed in Table 5.

Table 5: Dipole antenna half power free-space bandwidth. Wire radius 1.8 mm for $\mathrm{f}<3.7 \mathrm{GHz}$ and wire radius $=0.5 \mathrm{~mm}$ for $\mathrm{f}>=3.7 \mathrm{GHz}$

| $\mathrm{f}(\mathrm{GHz})$ | 0.9 | 1.9 | 2.45 | 3.7 | 6 |
| :--- | :--- | :--- | :--- | :--- | :--- |
| $\lambda / 15$ | 0.22 | 0.32 | 0.41 | 0.50 | 0.96 |
| $\lambda / 2$ | 22.2 | 28.2 | 29.6 | 45.5 | 60.2 |

The objective of equations (1)-(4) is to provide a conservative estimate of $P_{m a x, m}$ or $S A R_{m}$ for $s<25 \mathrm{~mm}$ for small low directivity apertures, such as dipoles, monopoles, PIFAs IFAs etc. However, applying $s=38 \mathrm{~mm}$ (which is $d=40 \mathrm{~mm}$ in Fig. 1) in equations (1)-(4) and
using the BW data for the $\lambda / 15$ dipole in Table 5, results in 1 -g SAR values of $6.44,3.17,2.38,2.12$, and $33.8 \mathrm{~W} / \mathrm{kg}$ at $0.9,1.9,2.45,3.7$, and 6 GHz . Comparing these data with the actual simulated data shown in Fig. 2 (a), it is clear that the data agrees well for frequencies of up to 2.45 GHz . The corresponding estimated $10-\mathrm{g}$ SAR values of $2.74,1.26,0.90,0.69$, and $8.8 \mathrm{~W} / \mathrm{kg}$ at $0.9,1.9,2.45,3.7$, and 6 GHz agree reasonably well for frequencies of up to 1.9 GHz when compared with the actual simulated data shown in Fig. 2 (a).

To be conservative, if we observe the near-field boundary defined by Fig. 6 at 40 mm distance, only the SAR for $f<1.9 \mathrm{GHz}$ could be estimated with reasonable accuracy. Thus, the data at higher frequencies cannot be estimated using equations (1)-(4). Therefore, to apply equations (1)-(4) for $s>25 \mathrm{~mm}$, the frequency that corresponds to $s=\lambda / 2 \pi$ should be first determined and then $P_{m a x, m}$ or $S A R_{m}$ should be estimated at frequencies below that.

Note that, for frequencies of 300,400 , and 500 MHz the cutoff distances are 159,119 , and 95 mm respectively. Therefore, it is plausible that at frequencies such as 300 , and 400 MHz the range over which equations (1)-(4) can be used may be extended pending further numerical and experimental validation.

## E. SAR results of antenna arrays

Computed and measured peak $1-\mathrm{g}$ and $10-\mathrm{g}$ SAR results for the patch arrays in the flipped orientation are plotted in Figs. 7 (a)-(c). For comparison, the simulated SAR of $\lambda / 15$ dipoles are also shown. It is clear that for $d=40 \mathrm{~mm}$ the patch flipped arrays only induce higher SAR compared to a $\lambda / 15$ dipole at frequencies above 3700 MHz . For $d=100 \mathrm{MHz}$, this occurs at 2450 MHz , and for $\mathrm{d}=200 \mathrm{~mm}$ at 1900 MHz .

Thus, at higher frequencies and larger distances the SAR induced by antenna arrays are substantially higher. The phenomena of lower SAR at shorter distances and lower frequencies and higher SAR at longer distances and higher frequencies will be explained in details in section V. Simulated peak $1-\mathrm{g}$ and $10-\mathrm{g}$ averaged SAR data of linear 3,5, and 7 element dipole arrays at 2450 MHz and 200 mm from the phantom are shown in Table 6 . For comparison, the SAR data of a single $\lambda / 2$ dipole, a single flipped patch and a 4 element patch array are also shown. Interestingly, the $\mathrm{N}=3$ element array with reflector induces roughly the same SAR as the 4 -element patch array. Note that, the directivities of these two arrays are very close.

Increasing the number of elements for the dipole array does not increase the SAR linearly as expected, because with increasing array size two things occur: (1) a larger array for the fixed distance means that the phantom moves more and more to the near/radiating near field, and (2) the array size becomes an
appreciable fraction of the phantom size.


Fig. 7. SAR vs. frequency of patch antenna arrays at 40, 100, and 200 mm distance (flipped orientation).

Table 6: Comparison of SAR induced by linear dipole arrays with other antennas. Linear dipole arrays with 3, 5, 7 elements with and without reflector at 2450 MHz and 200 mm from the phantom

| Antenna <br> Type | $\mathrm{D}_{0}$ <br> (linear) | SAR 1 g <br> $(\mathrm{~W} / \mathrm{Kg})$ | SAR 10g <br> $(\mathrm{W} / \mathrm{Kg})$ | Dim. <br> $(\mathrm{mm})$ |
| :---: | :---: | :---: | :---: | :---: |
| $\lambda / 2$ dipole | 1.75 | 0.0949 | 0.0633 | 51 |
| 3 dipole array | 4.24 | 0.1779 | 0.1087 | 196 |
| 3 dipole array <br> \& reflector | 18.3 | 0.4816 | 0.2943 | 352 |
| 5 dipole array | 6.77 | 0.108 | 0.0573 | 335 |
| 5 dipole array <br> \& reflector | 28.18 | 0.2529 | 0.1554 | 488 |
| 7 dipole array <br> \& reflector | 38.85 | 0.1699 | 0.1045 | 627 |
| 4 patch array | 20.89 | 0.45 | 0.28 |  |
| 1 patch | 2.28 | 0.1088 | 0.0677 |  |

## IV. ANALYSES

From [8], the SAR induced in an infinite lossy plane considering plane wave analysis is given by:

$$
\begin{equation*}
S A R=\frac{\sigma}{\rho} \frac{\mu \omega}{\rho \sqrt{\sigma^{2}+\varepsilon^{2} \omega^{2}}}\left(1+c_{c o r r} \gamma_{p w}\right)^{2} H_{\text {tinc }}^{2} \tag{5}
\end{equation*}
$$

where $\varepsilon$ is the tissue permittivity, $\mu=\mu_{0}=4 \pi \times 10^{-7} \mathrm{H} / \mathrm{m}$ is the tissue permeability, $\sigma$ is the tissue conductivity, $\rho$ is the tissue mass density, $H_{\text {tinc }}$ is the rms value of the incident magnetic field intensity, and $\gamma_{p w}$ is the plane wave reflection coefficient for the $H_{\text {tinc }}$ field. Also note that,

$$
\begin{equation*}
\varepsilon^{\prime}=\varepsilon-\sigma / j \omega \tag{6}
\end{equation*}
$$

and

$$
\begin{equation*}
\gamma_{p w}=\frac{2\left|\sqrt{\varepsilon^{\prime}}\right|}{\left|\sqrt{\varepsilon^{\prime}}+\sqrt{\varepsilon_{0}}\right|}-1 \tag{7}
\end{equation*}
$$

where $\quad \varepsilon_{0}=8.854 \times 10^{-12} \mathrm{~F} / \mathrm{m}$ is the free-space permittivity.

Considering 1 W transmit power, the power density caused by an isotropic antenna at a distance of $r$ from the antenna is $P_{D}=1 /\left(4 \pi r^{2}\right)$. Considering a $\lambda / 2$ dipole antenna with directivity of 1.64 the $P_{D}=1.64 /\left(4 \pi r^{2}\right)$, which results in $H_{\text {tinc }}=P_{D} / 377$.

Considering the permittivity, conductivity, and mass density values of the homogeneous phantom given in Table 4, the above equations were used to calculate SAR as function of frequency on the surface of an infinite lossy media. After that, SAR was calculated at depths of up to 23 mm of the lossy surface at 1 mm intervals using the skin depth formula below. From these table of SAR values the $1-\mathrm{g}$ and $10-\mathrm{g}$ averaged SAR data were calculated:

$$
\begin{equation*}
\delta=\frac{1}{\omega}\left[\left(\frac{\mu_{0} \varepsilon_{r} \varepsilon_{0}}{2}\right)\left(\sqrt{1+\left(\frac{\sigma}{\omega \varepsilon_{0} \varepsilon_{r}}\right)^{2}}-1\right)\right]^{-1 / 2} \tag{8}
\end{equation*}
$$

Calculated SAR data using this method are compared with direct simulation and measurement data for dipoles and monopoles at 40,100 , and 200 mm distance in Fig. 8.

For antennas smaller than half-wavelength, the near field boundary is 50 mm at 900 MHz . This agrees with the results shown in Fig. 8. As seen at 40 mm distance, the only frequency at which the plane wave approximation for both $1-\mathrm{g}$ and $10-\mathrm{g}$ SAR deviates is 900 MHz . Thus, SAR caused by dipoles and monopoles for frequencies below 900 MHz should be estimated using our earlier proposed free-space bandwidth based approximation method. For distances greater than 50 mm , the phantom is in the far field of the small low
directivity antennas. Thus, SAR can be estimated using the plane wave approximation.


Fig. 8. Comparison of plane wave calculated SAR (dipole fed with 1 W ) and SAR results obtained from direct simulations.

For large aperture directive antennas that radiate directly towards the phantom SAR estimation is not so simple. One may consider the EIRP (effective isotropically radiated power) instead of the power to estimate the SAR. Thus, if the transmit power is $P_{t}$ and the antenna gain is $G_{t}$, then the EIRP should be $P_{t} G_{t}$. Thus, if the antenna gain is 10 times the gain of a small dipole antenna, the SAR should be multiplied by 10. However, this will only satisfy if the aperture is sufficiently far from the phantom or body such that the aperture far field radiation beam has formed. It is difficult to pin-point the exact far field distance because it will depend on the aperture electrical size and the frequency of operation. From Table 7, it is clear that for a fixed antenna to phantom separation the smaller the aperture the lower is the frequency where the near-field
boundary transition takes place. Conversely for a fixed aperture, say $1.5 \lambda$, if the antenna to phantom distance increases, the reactive near-field to radiating near-field boundary occurs at a lower frequency. Thus, it is clear that for a fixed aperture size and fixed antenna to phantom separation the higher the frequency the more the likelihood that the aperture far-field beam will have formed. Thus, for similar directivity apertures (meaning apertures with similar dimensions) the SAR is likely to be much higher at higher frequencies simply because the directive beam has formed.

Table 7: Aperture size and near-field boundary for directive apertures

|  | Aperture Size |  |  |
| :---: | :---: | :---: | :---: |
| Aperture to <br> phantom distance | $1 \lambda$ | $1.5 \lambda$ | $2 \lambda$ |
| 100 mm | 1900 <br> MHz | 3500 <br> MHz | 5200 |
|  | MHz <br> 200 mm900 <br> MHz | 1800 <br> MHz | 2800 <br> MHz |

## V. DISCUSSIONS

Figures 9 (a) and 9 (b) illustrate the SAR factors (SF) of patch arrays over $\lambda / 15$ dipole antennas for various frequencies at various distances from the phantom. Peak 1-g average SAR factors of planar patch arrays over a $\lambda / 15$ dipole antenna show that at 40 mm distance only the 6000 MHz array has an SAR factor larger than 1. At 100 mm most patch arrays have an SAR factor $>1$ but $<2$ except the 6 GHz patch array which has an SAR factor $>10$. At 200 mm all patch arrays have an SAR factor $>1$ and the 6 GHz patch array has an SAR factor $>10$. Two factors in play are array size with respect to phantom and array electrical distance from phantom. It must be noted that all results presented here are based on SAR analysis in homogeneous phantoms as used for compliance testing according to IEC 62209-2 [29]. As reported in [32] and [33], $1-\mathrm{g}$ and $10-\mathrm{g}$ averaged SAR results obtained in homogeneous phantoms according to [29] can underestimate the corresponding SAR in anatomical body models when the body or phantom is no longer in the reactive near field of the antenna. The reasons for this phenomenon are standing wave effects in low conductivity tissue layers which may appear in worst case tissue layer compositions. According to [32] and [33], the extent of the possible underestimation depends on frequency and distance to the antenna and lies in the range of 2.2 to 4.7 dB . In order to stay conservative, all estimated SAR values based on the results presented in the present paper should be correspondingly scaled taking into account the results reported in [32] and [33].


Fig. 9. SAR factors (SF) of patch arrays over $\lambda / 15$ dipole antennas.

## VI. CONCLUSIONS

The SAR induced in a large 600 mm by 400 mm by 150 mm elliptical flat phantom by a large class of small low directivity antennas and directive patch antennas and arrays at distances of 40,100 , and 200 mm are studied and analyzed. The frequency range within which the study is conducted is from 900-6000 MHz . Both simulation and measurement results are presented which illustrate a number of significant findings. It is observed that for small low directivity antennas, the SAR may be estimated using our earlier reported antenna free-space bandwidth based formulas when the phantom is still within the near field boundary of the antenna. Conversely, if the phantom is clearly in the far field, SAR can be estimated using plane wave approximation methods by multiplying with the proper linear antenna gain. For directive antennas and arrays radiating directly towards the phantom, the plane wave approximation for SAR and multiplying by the linear gain allows a good estimate as long as the phantom is clearly in the far field of the aperture. For phantoms in the near field or radiating near field, estimating the SAR using this method will result in an overestimation
due to the fact that the radiation beam has not formed yet and that the aperture could be physically larger than the phantom resulting in multiple diffused distributions. The presented results do not consider the standing wave effects in a layered tissue structure.

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# Design of Shaped-Beam Parabolic Reflector Antenna for Peninsular Malaysia Beam Coverage and its Overlapping Feed Issues 

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#### Abstract

Design and performance of a shaped beam 12.2 GHz array-fed reflector antenna for broadcasting satellite is presented in this paper. Initial design, employing a cluster of feed horns illuminating a parabolic reflector is initially proposed for multi beam antenna (MBA) system to produce a contoured beam for Peninsular Malaysia. The precise feed positions are determined through a newly developed ray tracing program. Due to the small size of the coverage area, an issue with regards to physical constructability of the feed horns is raised. The MBA is modified by utilizing 18element microstrip array as the feed, where each element positions are calculated by using the same caustic model. In this case, the preceding issue is solved, and high gain shaped beam coverage with uniform aperture is generated. This paper shows the results of the contoured beam antenna that have been achieved for beam scanned over a coverage size of approximately $0.9^{\circ}$ long and $0.5^{\circ}$ wide. Small variation of radiation level, which is less than 3 dB within the edge of coverage (EOC), is also demonstrated in the performance analysis.


Index Terms - Antenna feeds, arrays, caustic model, ray tracing, reflector, satellite antenna.

## I. INTRODUCTION

Reflector technologies have experienced many significant developments in the recent years. However,
as satellite requirements become more stringent, the needs for shaped or contoured beam have rapidly increased. Contoured beam antennas have been used for various applications, such as high-speed internet access, broadcasting and military communication. In broadcasting satellite scenario, the needs for more compact and economical earth stations on user terminals have increased the power and bandwidth requirements of satellite [1]. Due to the demands for high quality of services, antennas with narrow beamwidth are requested. Narrow-beam antenna becomes desirable due to its ability to support high data rates while maintaining low satellite power. However, one spot beam can only support small coverage area on the earth [2]; thus, an approach to generate larger satellite footprint is requested. To guarantee constant high-gain signal availability to the coverage area, fine contoured beams shall be accurately designed.

Designing contoured beams involves reflector shaping and combination of multiple beams [3]. Reflector shaping technique can be performed by designing correct reflector curvature. Meanwhile, in the case of MBA, an array of feeds can be arranged to simultaneously generate multiple beams to form the desired contours. Through multi beams technique, higher gain and wider coverage are achieved at the same time. This MBA concept has been widely used by spacecraft manufacturers and researchers [3-9].

Many studies have been conducted to determine the optimum feed positions of the reflector. One of them is through optimization of radiation pattern in physical optic (PO)-based tool [10]. However, in that case, the relation of feed locations and beam direction was not clarified. Some researchers have introduced the theoretical concept of caustics on parabolic surfaces. As a fundamental research, caustic surface equations at focal region for plane waves were derived in two planes [11]. In that literature, the equal-path-length model was demonstrated to express the rays. The focusing ability was defined based on the physical extent of the focal spots. The concept of determining focal surfaces based on caustic data has been employed in [12]. Here, an analytical program was developed to determine the best focal spot. In the program, all incoming rays to a reflector surface, scanned in elevation (EL) and azimuth (AZ) plane were observed. As a result, the best focal spots were shown in two-dimensional; however the important feed position data such as the caustic dependency on focal-length-to-diameter ratio $(F / D)$ and the locus equation were not clarified.

Recently, a parametric study on obtaining the best focal point based on minimizing phase aberrations has been carried out [13]. For that particular study, a program is developed to analyze the phase errors when the beam is scanned to different target points. Comparisons with previous approaches have been made. However, the observations were for limited cases of $F / D$. Furthermore, similarly, the significant changes of caustic with respect to $F / D$ were not explained by locus equations or curves. Optimum feed position is represented by maximum scan-gain contour in [14]. It was concluded that small $F / D$ values tend to have a maximum scan-gain contour closer to Petzval surface. However, this study was performed for small $F / D$ only, and not for $F / D>1$, which is more preferable for satellite MBA. In reflector antenna, the $F / D$ is a crucial parameter [15]. Due to its importance, authors have developed a ray tracing program in MATLAB to calculate the optimum feed position of a parabolic for various $F / D[16,17]$. In the tool, a precise caustic model with an accurate caustic locus equation has been developed. The locus equation allows fast calculation of feed positioning, and is used to design a contoured beam for Peninsular Malaysia.

In this paper, two reflector feed designs are proposed. The initial design consists of a cluster of feed horns. However, due to some issues, an 18 -element microstrip array is designed as a replacement. The design procedures are presented and discussed in detail in the next segment.

## II. CONTOURED BEAM FOR PENINSULAR MALAYSIA COVERAGE

Figure 1 demonstrates the Malaysia region as viewed from satellite, which consists of two beams, $\mathrm{B}_{1}$
and $\mathrm{B}_{2}$ representing west and east part of the country respectively. In this paper, only the case of the west region, known as Peninsular Malaysia $\left(\mathrm{B}_{1}\right)$ is observed. To produce precise beam shape, $\mathrm{B}_{1}$ shall consist of multiple smaller beams. In preliminary design, two spot beams denoted as $\mathrm{B}_{11}$ and $\mathrm{B}_{12}$ are used to construct $\mathrm{B}_{1}$.


Fig. 1. Illustration of Malaysia beam from satellite point-of-view.

## A. MBA concept

In designing the antenna system for $\mathrm{B}_{1}$, several conditions are assumed. Figure 2 shows the application of multi beam technique to produce contoured beam for $\mathrm{B}_{1}$, as viewed from $91.5^{\circ} \mathrm{E}$ orbital slot. The antenna field of view is centred at O. As Peninsular Malaysia is considered as geographically small, thus $B_{1}$ is designed to only comprise of two spot beams $B_{11}$ and $B_{12}$, each having a narrow beamwidth, $\theta_{3 d B}=0.5^{\circ}$.


Fig. 2. Application of multi-beam technique for Peninsular Malaysia region by utilizing cluster feeds.

## B. MBA design parameters

This section describes various parameters that influence the performance of the parabolic antenna.

## Antenna diameter, $\boldsymbol{D}$

$D$ is chosen based on the $\theta_{3 d B}$ and sidelobe level (SLL) requirements. In practice, trade-off between antenna directivity and $\theta_{3 d B}$ to the SLL is a major consideration to antenna designers to yield high aperture efficiency [18]. Thus, characteristics of tapered distribution shall be taken into account. $D$ is estimated as
follows [19]:

$$
\begin{equation*}
D=(1.2 \pm 0.2 \mathrm{rads}) \frac{\lambda}{\theta_{3 d B}(\mathrm{rads})} \tag{1}
\end{equation*}
$$

The constant value reflects the aperture distribution, where 1 represents a uniform aperture with unity efficiency and high directivity. To reduce the SLL and by taking into account the trade-off, the value of 1.1 rads is chosen, and the $D$ is calculated as $126 \lambda$ or 3 m .

## Focal-length-to-diameter ratio, $F / D$

$F / D$ is a crucial parameter because it has strong effect on the achievable aperture and spillover efficiency. In designing satellite MBA, large $F / D$ usually gives better scan performance [15]. For small F/D, especially in the case of $F / D<0.5$, the scan performance deteriorates and the caustic data used to determine feed position are less accurate. The behavior of caustic and its focusing ability for various $F / D$ values have been studied in [17]. In this paper, the parameter $F / D$ is set to 1.5 for better scanning performance, especially in the satellite application $[8,10]$.

## Design of radiating elements

Due to its good performance and simplicity, pyramidal horns are chosen as the feeds. Based on the single feed per beam concept, two feed horns of similar dimensions are employed to produce $B_{11}$ and $B_{12}$ simultaneously. The horn aperture size depends on the $F / D$. The data of how the increase of $F / D$ relates to the raise in optimum horn dimension is shown in [15]. To estimate the horn size, the tilt angle between the horn to the reflector rim, $\theta_{m}$ is given as follows [18]:

$$
\begin{equation*}
\theta_{m}=2 \tan ^{-1}\left(\frac{D}{4 F}\right) \tag{2}
\end{equation*}
$$

For $F / D=1.5$, the $\theta_{m}$ is approximately $19^{\circ}$. The main concern in the horn design is to obtain radiation of at least -10 dB down at the reflector rim. This is to allow efficient illumination of reflector surface. After few adjustments and verifications using EM tool, the full dimensions of the feed horn, as illustrated in Fig. 3 is obtained as follows: $h h=54 \mathrm{~mm}, h w=70 \mathrm{~mm}, h l=63 \mathrm{~mm}$, $w h=12 \mathrm{~mm}$ and $w w=37 \mathrm{~mm}$.


Fig. 3. Dimension of feed horn.

## III. DETERMINATTION OF FEED POSITIONS

Beam deviation factor (BDF) concept has been widely used to demonstrate the dependency of feed position on $F / D$ [20]. This model is very convenient to determine the optimum feed position based on the aperture-phase aberration for antennas with arbitral $F / D$ value. However, there are some constraints. Due to the study model of deriving the expression, this method demonstrates the shifted beam $\theta_{B I}$ for one-dimensional lateral feed displacement $F_{1}$ only, as shown in Fig. 4. In designing MBA for $\mathrm{B}_{1}$, the ray tracing program, together with a derived caustic locus is used.


Fig. 4. Relationship of feed positions ( $\mathrm{F}_{1}, \mathrm{~F}_{2}$ ) and angles of radiated beams $\left(\theta_{B 1}, \theta_{B 2}\right)$.

In the ray tracing model, the caustic point $\mathrm{F}_{2}$ formed by the incoming wave from $\theta_{B 2}$ is measured. The caustic movement in $x$ and $z$ component for various values of incident wave directions, $-\theta_{i n}=0^{\circ}$ to $15^{\circ}$ is demonstrated as shown in Fig. 5. Large $\theta_{\text {in }}$ are chosen at this stage to analyze the common behavior of the caustics and to observe the trajectory. $D$ of 3 m is used and by considering the broadcasting satellite application, $f=12.2 \mathrm{GHz}$ is selected. The results are compared to the approximate equation of caustic locus below, where $S(x, z)$ indicates the distance from the centre of reflector to the caustic point:

$$
\begin{equation*}
S(x, z)=F \cos \theta_{i n} \tag{3}
\end{equation*}
$$



Fig. 5. Two-dimensional caustic positions.

From the good agreements of all curves, it is clarified that the optimum feed positions can be determined by equation (3). The feed positions of the MBA system can thus be calculated by using this method. It seems that higher accuracy is obtained at lower $\theta_{i n}$; thus, the application of ray tracing technique for designing contoured beam of Peninsular Malaysia is appropriate.

## IV. EM COMPUTATIONS AND RADIATION CHARACTERISTICS OF MBA

The arrangement of the MBA in FEKO is shown in Fig. 6. The optimum positions for the feed horn of $\mathrm{B}_{11}$ and $B_{12}$ are determined from equation (3). In the calculation, the incident beam directions $\theta_{i n}$ are associated with the $\mathrm{AZ}(\theta)$ and $\mathrm{EL}(\varphi)$ components. For $\mathrm{B}_{11}$ beam, the $\theta_{\text {in }}$ is $\left(-1^{\circ},-0.6^{\circ}\right)$, meanwhile for the $\mathrm{B}_{12}$ beam, the $\theta_{\text {in }}$ is $\left(-1.16^{\circ},-0.17^{\circ}\right)$. Both beams are very small in size; thus, the calculated caustics are very close to each other. This scenario has caused the horn apertures to be overlapped.


Fig. 6. A parabolic and two overlapped feed horns.

## V. MICROSTRIP ARRAY FEED FOR CONTOURED BEAM OF PENINSULAR MALAYSIA

Due to the non-constructible structure, the overlapped feed horns shall be replaced with a physically realizable solution. One of the solutions is to use a microstrip array antenna. The first step is to compute the beam size of the whole $\mathrm{B}_{1}$ region, denoted as $\theta_{W}$ and $\theta_{L}$ respectively in Fig. 7. Point 1 to 4 represents the minmax reference point.

Prior to designing the array feed, an on-focus square patch is first designed on a substrate having $\varepsilon_{r}=2.6$, thickness $h=1.2 \mathrm{~mm}$ and $\tan \delta=0.0018$. The single element size is $0.3 \lambda$ in both sides. After a few adjustments, -11 dB return loss with almost $50 \Omega$ impedance and a very good gain performance of 5.5 dBi is obtained at 12.2 GHz . The single patch element has wide beamwidth of $\theta_{3 d B}=100^{\circ}$ for both E-plane and H-plane. In the case of array feed, the beamwidth of a single element patch does not play an important role, as the actual $\theta_{3 d B}$ is determined through total number of elements on the array structure radiating on a single
parabolic reflector. Thus, the single element design is then be duplicated to represent all four beam points on the required area. The positions of each feed elements are computed via ray tracing and translated into FEKO.


Fig. 7. Illustration showing the beam coverage for $\mathrm{B}_{1}$ region with the -3 dB EOC points.

The calculated positions of all 4 beam points and the associated feeds, arranged together with 14 additional elements within the desired boundary are illustrated in Fig. 8. The figure also illustrates the overlapped horn areas that have been replaced by array elements. The randomly-distributed extra elements are added to ensure a good performance of the array system, particularly to achieve the desired beamwidth with uniform radiation gain ( -3 dB ) across the EOC.

All elements are assigned to various amplitude excitations $A_{i}$ values from 0.3 to 1 V to get uniform contour throughout EOC. Far-field simulation is performed based on the MoM-PO method, which is the integration of two techniques; method of moment (MoM) for microstrip array structure and physical optic (PO) for parabolic reflector. In this case, the dimension of the parabolic reflector is considered as electrically large, which is about $122 \lambda$; therefore, simulation of the parabolic reflector alone by using MoM involves a lot of memory usage and computation time. The simulation parameters are shown in Table 1.

Figure 9 shows the normalized contoured beam coverage for $\mathrm{B}_{1}$, with four test points representing the maximum extent of the beam area, having -3 dB deviations from $G_{\max }$. To ensure the correct beam size, the coordinates of all test points are compared with the actual peninsular beam. Table 2 presents the expected and the measured data taken at EOC. All measured EOC points match with the required test points, with the maximum deviation is around $0.05^{\circ}$ only. Therefore, from these sets of results it can be concluded that a uniform contoured beam can be designed by the ray tracing method, regardless through the usage of horn arrays or multi-element microstrip as the feeds.


Fig. 8. Design concept of the microstrip array feed for Peninsular Malaysia and illustration of overlapped horn structure with the corresponding beam points.

Table 1: Simulation parameters

| Items | Parameters | Details |
| :---: | :---: | :---: |
| Computer | Memory (RAM) | 96 GB |
|  | Clock time | 1.8 GHz |
| Reflector | Mesh size | $\lambda / 2(12.3 \mathrm{~mm})$ |
| Array feed | Mesh size | $\lambda / 20(1.23 \mathrm{~mm})$ |
| Calculation | Simulation memory | 59.43 GB |
| process | Simulation time | 73.53 hours |



Fig. 9. Two-dimensional contoured beam for Peninsular Malaysia.

Table 2: Comparison of EOC data between calculated and obtained results

| Beam Points | Required $\left({ }^{\circ}\right)$ | Obtained $\left({ }^{\circ}\right)$ |
| :---: | :---: | :---: |
| 1 | $-0.80,-0.30$ | $-0.81,-0.25$ |
| 2 | $-0.80,-0.80$ | $-0.81,-0.82$ |
| 3 | $-1.3,-0.50$ | $-1.3,-0.53$ |
| 4 | $-1.4,0.1$ | $-1.4,0.12$ |

## VI. EXCITATION COEFFICIENTS OF FEEDS

The displacement of feed from the focal plane introduces non-linear phase variation called phase error, which can cause gain loss, beamwidth changes and pattern distortion [15]. In designing contoured beam, the estimation of amplitude excitation $A_{i}$ at the feeds is important in obtaining uniform amplitude distribution at the reflector beam. By controlling the $A_{i}$, the gain can be adjusted so that the associated power will be transmitted without any interruption. In the array feed for $B_{1}$, as shown in Fig. 10, all elements located at the edges of the structure are assigned at 1 V . Meanwhile, to achieve broader beam and to reduce gain variation along EOC, the middle and adjacent elements are excited at 0.3 V and 0.8 V . This arrangement results in almost uniform amplitude distribution over the region.


Fig. 10. Arrangement of radiating elements with the corresponding input $A_{i}$ for $\mathrm{B}_{1}$ beam.

Figure 11 demonstrates the distributions of magnetic field density for the antenna, which is useful to examine the behavior of induced currents at each element. Figure 12 shows the numerical data of the output H -field intensity. Theoretically, the induced current at each element is proportional to the input $A_{i}$. Based on the comparison between these two data, the correct relation is achieved.


Fig. 11. Magnetic field distributions on the microstrip surface for $\mathrm{B}_{1}$ beam.


Fig. 12. Comparison between H -field intensity and input $A_{i}$ for $\mathrm{B}_{1}$ beam.

## VII. CONCLUSION

A Ku-band satellite-mount antenna system to produce contoured beam coverage for Peninsular Malaysia is designed. Justifications and design equations of antenna parameters are shown. A design issue with regards to physical configuration of the initial feed horn design is discussed and an alternative solution is presented. Final antenna system, which consists of a single parabolic reflector, and a radiating feed that comprises of 18 -element microstrip patch array are simulated and analyzed. The accuracy of the ray tracing method, developed to determine the precise positions of the feed elements are clarified in this paper through 3D EM solver. Uniform aperture distribution with less than -3 dB EOC gain variation and accurate beam shape with maximum angular deviation of $0.05^{\circ}$ over the Peninsular Malaysia is obtained.

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# Enhancement of Scan Angle Using a Rotman Lens Feeding Network for a Conformal Array Antenna Configuration 

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#### Abstract

An antenna with a wide scan angle in a wide frequency band is obtained by feeding a conformal arc array with a modified formulation of Rotman lens design. In this paper, two kinds of Rotman lenses are designed to feed a linear array and a conformal array and their scan angles are compared in a specified frequency band. The phase distributions of the linear array elements are linear in all scan angles, but these phase distributions are nonlinear in the conformal array. Therefore in order to design a Rotman lens for conformal arrays, the conventional Rotman lens design formulations must be modified. For this purpose, first the phase distributions of conformal array elements were obtained using the particle swarm optimization (PSO) process. Then by modifying the conventional Rotman Lens design formulations used for linear arrays, appropriate formulations for conformal arrays are obtained. In the end, by selecting two specified linear and conformal arrays with equal number of elements, their maximum scan angles in a specified frequency band are studied. It is shown that in the same frequency band the maximum scan angle increases about $20 \%$ in the Rotman Lens fed conformal array antenna.


Index Term - Conformal array, PSO, Rotman lens.

## I. INTRODUCTION

Using an appropriate beam forming network that can feed array antennas has several applications in radar and satellite communication systems. The main problem of usual beam forming networks is their small bandwidth which causes the locations of radiation beams of the array to vary with frequency. Rotman lens [1] is a wideband feed network that relies on path lengths and is designed based on a true time delay (TTD) response. Using the TTD scheme to feed array antennas prevents the dependence of scanning angles on frequency [2]. To have different scan angles, the Rotman lens should provide linear phase distributions with different slopes, along equi-spaced linear array antenna elements which are independent from frequency. Up to now, many types
of Rotman lenses have been designed, constructed and modified with various applications in microwave and millimeter-wave frequency bands $[1,3]$. Also, various works in Rotman lens design have been done with the goals of low phase error [4] and low insertion loss [5].

There is an increasing demand for conformal arrays in modern systems and that is due to their ability in being mounted on surfaces with different shapes. This causes the aerodynamic drag to reduce considerably and the structures get less visible to the human eye. Another important advantage of conformal arrays which is of vital importance in radar applications is their wide angle coverage. Other benefits include space saving, potential increase in the available aperture, reduction of radar cross-section (RCS), elimination of radome-included bore-sight error, etc. [6].

In this study, an increase in the maximum scan angle is obtained from a conformal array that is fed by a Rotman lens. To this purpose, in the first step, the design formulations of a trifocal Rotman lens [7] which is used to feed linear arrays are modified to feed the conformal array. Next, in order to compare the maximum scan angles, two linear and conformal arrays fed by their corresponding Rotman lenses are examined. Also, to obtain the phase distribution of the conformal array antenna at different scan angles, the PSO procedure has been used.

In Section II, the modified formulations of Rotman lens for conformal array antennas are presented. In Section III, the optimum phase distributions for the modified Rotman lens formulations are obtained based on the PSO method. Finally in Section IV, the designed Rotman lenses are simulated with the EM full wavesimulation software (HFSS) and the simulation results of the linear and conformal arrays are compared. It must be noticed in the mentioned procedures the modified formulations of input and output curvatures of Rotman lens are obtained by suitable code in Matlab software. Then the obtained shapes are imported to the EM full wave simulator HFSS to simulate electromagnetic characteristics of Rotman lens.

## II. ROTMAN LENS FORMULATIONS BASED ON ARRAY ANTENNA CONFIGURATIONS

Different design methods have been reported for Rotman lenses used for linear arrays [1,4,8]. These methods include the trifocal method, quadrufocal method and non-focal method of which the trifocal method is the most frequently used one. Based on the conventional trifocal lens principles, some trifocal Rotman lens formulations have been developed to obtain the desired phase distributions for linear array antennas $[7,9,10]$. In this section, these formulations are developed such that they can be used for conformal array antennas.

## A. Modified Rotman lens formulations for feeding conformal array antennas

Figure 1 represents a general structure of a Rotman lens to feed a conformal array. Curve E represents the desired configuration of the conformal array antenna.


Fig. 1. Trifocal Rotman lens structure for conformal arrays.

The conventional trifocal Rotman lens for linear arrays produces linear phase distributions for linear array elements. For conformal array antennas, Rotman lens formulations must be modified to produce suitable phase distributions which depend on the configuration of the array antenna. An important point that must be noticed in the new design formulations is determining the required phase distributions to create a set of three design equations. This is done by using a procedure similar to the one used in [1]. Based on the design procedure in [1], the modified formulations for Rotman lens design are presented in Eqs. ( $1 \mathrm{a}-\mathrm{c}$ ). In these equations, $l \varphi_{0}$ produces the required phase distribution of the conformal array for zero scan angle and similarly $l \varphi_{0} \pm 1 \varphi_{1}$ create the suitable phase distributions of conformal array to produce the
radiation pattern with maximum scan angles, $\pm \Psi_{\alpha}$, respectively. The optimization procedure to determine these phase distributions are presented in the next section;

$$
\begin{align*}
& F_{2} P \sqrt{\epsilon_{r}}+W \sqrt{\epsilon_{e}}+\left(l \varphi_{0}+l \varphi_{1}\right)= \\
& f_{2} \sqrt{\epsilon_{r}}+W_{0} \sqrt{\epsilon_{e}},  \tag{1a}\\
& F_{3} P \sqrt{\epsilon_{r}}+W \sqrt{\epsilon_{e}}+\left(l \varphi_{0}-l \varphi_{1}\right)= \\
& f_{2} \sqrt{\epsilon_{r}}+W_{0} \sqrt{\epsilon_{e}},  \tag{1b}\\
& \quad F_{1} P \sqrt{\epsilon_{r}}+W \sqrt{\epsilon_{e}}+l \varphi_{0}= \\
& \quad f_{1} \sqrt{\epsilon_{r}}+W_{0} \sqrt{\epsilon_{e}}, \tag{1c}
\end{align*}
$$

where $\mathrm{F}_{\mathrm{i}} \mathrm{P}$ is the physical distance between points $\mathrm{F}_{\mathrm{i}}$ and P. Also, $1 \varphi_{0,1}=\varphi_{0,1} \times\left(\lambda_{\mathrm{g}} / 2 \pi\right)$ and $\lambda_{\mathrm{g}}$ is the wavelength.

Normalizing Eqs. (1a-c) by the electrical length of the central focal length, $\sqrt{\epsilon_{r}} f_{1}$, results in:

$$
\begin{gather*}
\frac{F_{2} P}{f_{1}}=\beta-\omega-a-b,  \tag{2a}\\
\frac{F_{3} P}{f_{1}}=\beta-\omega+a-b,  \tag{2b}\\
\frac{F_{1} P}{f_{1}}=1-\omega-b, \tag{2c}
\end{gather*}
$$

where

$$
\beta=\frac{f_{2}}{f_{1}}, a=\frac{\varphi_{1}}{f_{1}}, b=\frac{\varphi_{0}}{f_{1}} \text { and } \omega=\frac{W-W_{0}}{f_{1}} .
$$

Based on the geometrical configuration of Rotman lens (Fig. 1),

$$
\begin{gather*}
F_{2} P^{2}=\left(-f_{2} \cos \alpha-X\right)^{2}+\left(-f_{2} \sin \alpha+Y\right)^{2} \\
=f_{2}^{2}+X^{2}+Y^{2}+2 f_{2} X \cos \alpha-2 f_{2} Y \sin \alpha,  \tag{3a}\\
F_{3} P^{2}=\left(-f_{2} \cos \alpha-X\right)^{2}+\left(-f_{2} \sin \alpha-Y\right)^{2} \\
=f_{2}^{2}+X^{2}+Y^{2}+2 f_{2} X \cos \alpha+2 f_{2} Y \sin \alpha,  \tag{3b}\\
F_{1} P^{2}=\left(f_{1}+X\right)^{2}+Y^{2} . \tag{3c}
\end{gather*}
$$

After normalizing Eqs. (3a), (3b) and (3c) by $f_{1}^{2}$ and equating them with the square of Eqs. (2a), (2b) and (2c) respectively, the set of three goal equations is obtained. By solving these three equations, the positions of the X and $Y$ coordinates of the phase centers of array ports and transmission line lengths $\left(\mathrm{W}_{\mathrm{i}}\right)$ are obtained. This method can be used for any practical array curves including linear arrays. For conventional linear array configurations the expressions $l \varphi_{0}$ and $l \varphi_{0}+l \varphi_{1}$ are replaced by zero and $\pm Y_{3} \sqrt{\epsilon_{i}} \sin \left(\psi_{a}\right)$ respectively, in which $\Psi_{\alpha}$ is the maximum scan angle of the array. But in this paper, we use the modified phase distributions for both linear and conformal arrays. In the next section, the optimization procedures to obtain the phase distributions for a linear array and a specified conformal array are explained.

## III. OPTIMUM PHASE AND AMPLITUDE DISTRIBUTIONS OF THE CONFORMAL

 AND LINEAR ARRAYSTo obtain the required phase distributions of $\varphi_{1}$ and $\varphi_{0}$ in Rotman lens design formulations, at first the configuration of the conformal array and its radiating elements, must be determined. Therefore, antenna elements and array configurations are discussed in the following sections.

## A. Conformal and linear array configurations and their radiation elements

Because of the wide operating frequency band in this study ( $10-14 \mathrm{GHz}$ ), double ridged horn antennas are used as the radiating elements of the array antennas. As shown in the Fig. 2, radiation characteristics of this antenna are almost constant and VSWR $<2$ in the operating frequency band.


Fig. 2. Radiation characteristics of double ridged horn antenna: (a) VSWR, (b) normalized amplitude of electric field radiation patterns, E and H-plane.

Two configurations of array antennas including the linear array and the conformal arc array are synthesized
in this study. To have a precise comparison of the radiation patterns of the synthesized arrays, we use equal number of elements with equal element spacing for both of these arrays. The main problem of the array designs with wide scan angles is the existence of grating lobes, so the array elements are placed as close as possible to each other. Figure 3 (a) shows a linear array of 16 double ridged horn antennas. The conformal array can be formed on any desired curves. Without loss of generality in this paper, the conformal array elements stand on a quarter of a circle. Figure 3 (b) shows the conformal array configuration $\left(\gamma=45^{0}\right)$.


Fig. 3. Array antenna configurations of double ridged horn antennas: (a) linear array, (b) arc curve conformal $\operatorname{array}\left(\gamma=45^{0}\right)$.

Since one of the most important parameters in a finite array is the coupling between array elements, in the next section active element radiation patterns [11] of the arrays are used in the synthesis process of the array antennas.

## B. Synthesis of linear and conformal arrays using the PSO algorithm

In this section, the PSO algorithm is used to obtain the optimum phase and amplitude distributions for linear and conformal array elements. The phase distributions are used to construct the Rotman lens design formulations and the amplitude distributions are used to design of the Rotman lens ports. To this end, the phases and amplitudes of the array elements are used to produce the particles of the PSO algorithm. The particles move in a multidimensional search space so that every particle adjusts its position with respect to its adjacent particles while considering their prior experience. In general, the velocity and position of each particle, $p_{k}$, is expressed as follows [12]:

$$
\begin{align*}
& \bar{v}_{k}(t)=\bar{v}_{k}(t-1)+c_{1} r_{1}\left[\bar{P}_{k}(t-1)-\bar{x}(t-1)\right] \\
& +c_{2} r_{2}\left[\bar{G}_{k}(t-1)-\bar{x}(t-1)\right]  \tag{4}\\
& -\quad-\quad-\quad-\quad-\quad
\end{align*}
$$

In Eq. (4), $\bar{x}$ and $\bar{v}$ represent the position and the velocity of particles respectively. The positive constants $c_{1}$ and $c_{2}$ are usually equal, $c_{1}=c_{2}=2 . r_{1}$ and $r_{2}$ are two random values in the range $(0,1)$. The best previous position of $\mathrm{k}_{\mathrm{th}}$ particle (coefficient) is presented as $\bar{P}_{k}(t-1)$ and $\bar{G}_{k}(t-1)$ denotes the best $\mathrm{k}_{\mathrm{th}}$ particle in the population. Equation (4) is used to update the velocity and position of the coefficients as a function of their previous velocity and positions, then the coefficients move towards a new position. In each update the phases and amplitudes of the array elements are replaced with new ones and the obtained radiation pattern is compared with the desired radiation pattern. To this purpose, the error function or the fitness function is defined as the absolute difference between the target and calculated patterns of the array.

The optimization process is continued until the error function converges to the acceptable value. Figure 4 shows the desired radiation patterns in broadside and the maximum scan angle of $-65^{0}$. The fitness function used in the PSO procedure is defined as:

$$
\text { Fitness function }=\sum_{i=1}^{5} W_{i} \sum_{\theta=\theta_{i-1}}^{\theta_{i}}\left|F_{o}-F_{d}\right|,
$$

$F_{d}$ is the desired goal radiation pattern and $F_{N}$ is the normalized calculated complex array factor. Also, $F_{N}(\theta, \varphi)=\sum_{\mathrm{n}=1}^{\mathrm{N}} \mathrm{A}_{\mathrm{n}} \mathrm{e}^{\mathrm{j} \varphi_{\mathrm{n}}} \mathrm{E}_{\mathrm{n}}(\theta, \varphi)$, in which $E_{n}(\theta, \varphi)$ is an embedded complex number that represents active radiation fields for the $n^{\text {th }}$ element and must be multiplied by the amplitude and phase vector $A_{n} e^{j \varphi_{n}}$. Weighting coefficients depicted in the desired patterns are defined in each part of the patterns to scale the error of that part in the optimization procedure.

## C. Phase and amplitude distributions for linear and conformal array Rotman lens designs

Considering the modified formulations in Eq. (1), knowing the phase distributions of $\varphi_{0}$ and $\varphi_{1}$ is necessary in the Rotman lens design. Also, because the Rotman lens operates based on the TTD properties, it is possible to use the radiation pattern of the array elements at an arbitrary frequency in the operating frequency band (1014 GHz ) for the PSO procedure. Therefore, in this paper we use the active element radiation patterns at center frequency to synthesize the conformal array antenna.

The PSO algorithm has been run with the use of 800 particles and 500 iterations to obtain the optimized amplitude and phase distributions of the arrays. Figure 4 (a) shows the optimized radiation pattern for zero scan angle and Fig. 4 (b) shows the optimized radiation
pattern for $-65^{\circ}$ scan angle for the linear and conformal arrays.


Fig. 4. Optimized radiation patterns: (a) zero scan angle $\left(\mathrm{w}_{1}=\mathrm{w}_{5}=0.4, \mathrm{w}_{2}=\mathrm{w}_{4}=2.2\right.$ and $\left.\mathrm{w}_{3}=1.8\right)$, (b) $-65^{0}$ scan angle $\left(\mathrm{w}_{1}=0.8, \mathrm{w}_{2}=1.8, \mathrm{w}_{3}=3.4, \mathrm{w}_{4}=2.8\right.$ and $\left.\mathrm{w}_{5}=1.6\right)$.

Figure 4 (b) shows the fitted pattern for $-65^{0}$ scan angle. It is shown that the linear array could not make a good fitted pattern. Figures 5 and 6 show the phase and amplitude distributions of array elements for zero and $-65^{0}$ scan angles.

(a)

(b)

Fig. 5. Phase distributions of array elements: (a) zero scan angle, (b) $-65^{\circ}$ scan angle.


Fig. 6. Amplitude distributions of array elements: (a) zero scan angle, (b) $-65^{\circ}$ scan angle.

In the conformal array antenna, unlike the linear array antenna, the phase distributions for zero and $-65^{\circ}$ scan angles, represent the nonlinear behavior of the phase distributions. Also, the amplitude distribution for $-65^{\circ}$ scan angle shows that the elements which point to the $-65^{\circ}$ scan angle have greater amplitudes. Difference between the amplitude distributions in conformal and linear arrays is due from the different orientation of array ports and radiating elements. Unlike the linear array, in
the conformal array the radiating elements are oriented in different directions based on the array curvature. Therefore, the radiation patterns of conformal array elements are different. In the Rotman lens design the amplitude distributions for different scan angles are realized by suitable design of the beam ports corresponding to each scan angle in the radiation pattern. This principle is studied in the next section.

## IV. DESIGN OF THE ROTMAN LENSES

As mentioned earlier, to design the Rotman lenses to feed the linear and conformal array antennas, it is necessary to have the phase distributions $\varphi_{0}$ and $\varphi_{1}$. Beside the phase distributions, the amplitude distributions of array elements for these scan angles must be produced by the Rotman lenses. To design the Rotman lens for the arc-shaped array, two points must be made clear. First, the phase distributions of the array elements and second the amplitude distributions of the array elements for different scan angles. By obtaining the optimized phase distributions and applying them to the modified Rotman lens equations, the lens can realize the desired phase distributions. To create the desired amplitude distributions, especially for maximum scan angles, the input ports must be designed and directed correctly. These amplitude distributions depend on beam ports widths, the shape of the inner receiver curve and the angle of input ports orientations. The widths of the beam ports and shape of the inner receiver curve can be realized by controlling the trifocal lens parameters. Table 1 shows the parameters used for designing the proposed Rotman lenses.

Table 1: Rotman lens design parameters

| $f_{1}$ | Center focal length | 262 mm |
| :---: | :--- | :--- |
| $f_{2}$ | Off focal length | 249.5 mm |
| NB | Number of beam ports | 11 |
| NA | Number of array ports | 16 |
| $\alpha$ | Focal angle | $24 \varrho$ |
| $\varepsilon_{r}$ | Cavity permittivity | 2.2 |
| $w_{0}$ | Center transmission line length | 194 mm |
| $f_{0}$ | Center frequency | 12 GHz |

The optimization results for amplitude distribution of $-65^{\circ}$ scan angle shows that the elements which correspond to this scan angle have higher amplitudes. This amplitude distribution has an important role in controlling the side lobes of the radiation pattern. To have this amplitude distribution on antenna elements, beam ports have to be oriented towards the desired angle. Figure 7 shows the designed Rotman lenses with 11 beam ports and 16 array ports for linear and conformal arrays respectively. Because of amplitude tapering for the linear array in Fig. 6, each beam port is directed towards the center of the array port contour, like in [13].

Figure 7 (b) shows that the orientation of beam port 1 for the conformal array Rotman lens is not towards the center of the array port contour. In fact, the orientation of beam port 1 is shifted by $\Gamma$ degrees from the center of the array curve, as shown in Fig. 7 (b). This is done based on the obtained optimized amplitude distributions for the conformal array (as shown by the solid lines in Fig. 6) and causes certain array elements to have higher amplitudes.


Fig. 7. Modified Rotman lens structures: (a) linear array, (b) conformal array.

The purpose of the dummy ports is to minimize the multipath interference [14]. The substrate of the microstrip structure is Rogers RT/duroid $5880(\mathrm{tm})$ with $\varepsilon_{r}=2.2, \tan \delta=0.0009$. Figure 8 shows two amplitude distributions across array ports for the two Rotman lens designs shown in Fig. 7, when beam port 1 is excited.


Fig. 8. Amplitude distribution across array ports when port 1 is excited.

## V. SIMULATION RESULTS OF THE PROPOSED ROTMAN LENSES

Figure 9 shows the radiation patterns of the linear array of Fig. 3 (a) fed by the modified Rotman lens of Fig. 7 (a) at the frequencies of 10,12 and 14 GHz . To better clarify the grating lobes, the radiation patterns of 7-11 beam ports are not shown.

Figures 9 (a) and 9 (b) show that the gain of the array antenna at the maximum scan angle decreases considerably at the frequencies of 10 and 12 GHz , and Fig. 9 (c) shows that not only the gain decreases, but also the grating lobes increase considerably at 14 GHz . At the maximum scan angle the decrease in the gain is 3.45 dB and 5.3 dB at the frequencies of 12 and 14 GHz respectively, compared to the gain at the zero scan angle.

Figures $10(\mathrm{a}-\mathrm{c})$ show the radiation patterns of the conformal array of Fig. 3 (b) fed by the modified Rotman lens of Fig. 7 (b) at the frequencies of 10,12 and 14 GHz . These figures show that the maximum gain reduction of the conformal array at different frequencies is acceptable up to the $-65^{\circ}$ scan angle and the grating lobes do not increase at these frequencies.

To better compare the maximum scan angle of linear and conformal arrays, the acceptable radiation patterns for the maximum available scan angles are depicted for both of the array configurations in Fig. 11. The acceptable maximum scan angles for the conformal array and the linear array are $-65^{\circ}$ and $-55^{\circ}$ respectively.



Fig. 11. Optimized radiation patterns for $-65^{\circ}$ and $-55^{\circ}$ scan angles for conformal and linear arrays.

## VI. CONCLUSION

An improvement in the scan angle of a wide band array antenna is obtained through feeding a conformal array antenna with a modified design of the Rotman lens. The proposed Rotman lens structure is based on the trifocal design method with new phase distributions in zero and maximum scan angles. The effect of amplitude distributions across array elements are fully considered in the design process. These phase and amplitude distributions are obtained by synthesizing the conformal array using the PSO algorithm. The radiation patterns of the linear and conformal arrays with equal numbers of elements are compared and the enhancement in the scan angle of the conformal array antenna is clearly observed.

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# Reflectarray Nano-Dielectric Resonator Antenna Using Different Metals 

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#### Abstract

Nano-antennas have been introduced with wide bandwidth for faster data communications. The material properties of good conducting metals introduce plasmonic behavior at THz frequencies. The material property of good conducting metals using the Durde Lorentz model have been investigated. The radiation characteristics of nano-dielectric resonator antenna NDRA reflectarray at 633 nm have been investigated. A parametric study for the NDRA unit-cell dimensions and material has been introduced. Different types of metals are used as a supporting plane of the NDRA unit-cell. A NDRA with silver, copper, and aluminum supporting plane have been designed and analyzed for reflectarray antennas. A nano-reflectarray unit-cells with supporting plane having different metals have been introduced. Comparisons between the radiation characteristics of reflectarrays with different supporting plane metals have been illustrated. A compromise between the size, maximum gain, and operating bandwidth of the nanoreflectarray is investigated for terahertz applications. The finite integral technique is used to carry a full wave analysis to design a NDRA reflectarray.


Index Terms - DRA, nano-antenna, reflectarray.

## I. INTRODUCTION

The radiation characteristics of a conventional radio-frequency RF antenna have been presented in detail [1]. Nano-antenna is a resonant device, which converts the EM wave into a localized energy at terahertz frequencies [2]. Recently, wide bandwidth nanoantennas have been introduced for faster information exchange. Nano-antennas have many applications including solar cells, on-chip wireless optical communication and biological imaging. Different forms of the microwave antennas such as dipole, monopole, Yagi-Uda, and bow-tie antenna have been investigated at the terahertz frequencies [3-6] which focus on resonant metallic nanostructures. The materials of nanoantennas are generally good conducting metals such as gold and silver [7]. The resonant structures of good conducting metals show electromagnetic resonances, when being excited by an incident light, this is called
surface plasmon polariton resonances SPPRs. The optical properties of these metals are described by the Drude-Lorentz model, which considers both the free electrons contributions and harmonic oscillator SPPRs contributions [8]. However, only the high ohmic losses of metals at THz frequencies affect the radiation efficiency of nano-antennas [2]. The nano-antenna resonance length is not determined by the free space wavelength, but by the SPP wavelength in the metal [2]. The current distribution on the nano-antenna has a standing wave pattern similar to that of the RF antennas, but with non-uniform spacing between subsequent current lobes. Nano-antenna arrays introduce a superior directivity, field confinement, absorption cross-section and flexibility in beam shaping compared with single nano-antennas. Dielectric resonator antennas DRAs have many attractive features and applications at microwave frequencies [9]. The DRAs have different shapes such as a hemisphere, cylinder, or rectangular and are typically mounted on a metal layer regarded as perfect electric conductor. The DRAs are generally constructed from low-loss high-permittivity dielectric materials up to $\varepsilon_{\mathrm{r}}=100$. To increase the efficiency of resonant nano-antennas, the low-loss high-permittivity dielectric materials available at THz frequencies are used. At THz frequencies, the wave penetrates the metals due to the plasmonic effect and the antenna scaling property is not valid. The radiation characteristics of the DRA at 633 nm have been investigated in [10]. Highgain microwave antennas have been employed in many applications such as radar and satellite communications. The parabolic reflector and phased array antenna have high gain, narrow main lobe and high power capacity, but suffer some disadvantages as high cost, large volume, and lossy feed networks. Reflectarray antenna combines the advantages of parabolic reflector and phased array and overcomes their disadvantages [11]. The reflectarray antenna consists of a primary source illuminating a planar surface composed of an array of unit-cells. The phase shift of each unit-cell is adjusted to collimate the reflected wave in the desired direction. Reflectarray suffers from feeder blocking effect, so it requires an offset feed to avoid blockage losses, which
leads to destroying the symmetry of the antenna aperture and increases the angle of incidence to some individual elements [12-14]. The detailed analysis of the radiation characteristics of NDRA element and NDRA reflectarray at 633 nm investigated in [10].

In this paper, the optical material properties of different conducting metals at THz frequencies have been investigated. A parametric study of the NDRA unitcell for reflectarray at 633 nm has been introduced. The effect of changing the type of the metal material properties on the performance of the NDRA unit-cell is investigated. A $21 \times 21$ unit-cell elements NDRA reflectarray has been designed and analyzed using the finite integral technique based on the commercial software CST Microwave Studio [15,16]. Reflectarray with different metal supporting plane have been introduced. A comparison between the radiation characteristics of reflectarray with silver, copper and aluminum supporting plane has been presented.

## II. MATERIAL PROPERTIES AT TERAHERTZ RANGE

At THz frequencies, the behavior of conventional metals properties behaves in a different way compared to the microwave frequencies [7]. In microwave frequency range the electric field inside the conductors is zero, which leads to perfect reflection from the surface of the metal, as the conductivity of metal is very high. However, at THz frequencies, the assumption of perfect conductor metals is not valid and the losses cannot be neglected [8]. The material properties in the THz range can be described by a free electron gas moving through a lattice of positive ions. The frequency dependent complex permittivity and the electrical conductivity of metal in the THz frequency range are described using Durde Lorentz model [8]:

$$
\begin{gather*}
\varepsilon_{r}=\varepsilon_{1}+j \varepsilon_{2}=\left[1-\frac{\omega_{p}^{2}}{\omega \omega-j \vartheta_{p}}\right],  \tag{1}\\
\sigma=\sigma_{1}+j \sigma_{2}=\varepsilon_{o} \frac{\omega_{p}^{2}}{j \omega+\vartheta_{p}}, \tag{2}
\end{gather*}
$$

where $\varepsilon_{1}$ is the real part of permittivity and is a measure of how much energy from an external field is stored in a material. $\varepsilon_{2}$ is the imaginary part of permittivity loss factor. It is a measure of how dissipative or lossy a material is to an external field, $\varepsilon_{o}$ is the dielectric constant of vacuum, $\omega$ is the angular frequency of the electromagnetic wave, $\vartheta_{p}$ is the angular collision frequency, and $\omega_{p}$ is the electron plasma angular frequency [8]:

$$
\begin{equation*}
\omega_{p}=\sqrt{n_{e} q^{2} / \varepsilon_{o} m_{e}}=56.40 \sqrt{n_{e}} \tag{3}
\end{equation*}
$$

where $n_{e}$ is the free electron density, $m_{e}$ is the electron mass, and $q$ is the charge of the electron. Figure 1 shows the variation of electric permittivity $\varepsilon$, and the conductivity $\sigma$, versus frequency in the THz range of gold, copper, silver and aluminum. The electrical
permittivity and conductivity of all metals take an exponential variation with frequency. $\varepsilon_{1}$ and $\sigma_{2}$ are increased by increasing frequency negative with reduced magnitude with higher frequency while $\varepsilon_{2}$ and $\sigma_{1}$ are decreased in magnitude by increasing frequency. The skin depth is representing how deep the electromagnetic wave can penetrate the material surface [8]:

$$
\begin{equation*}
\delta(\omega)=\frac{2 c \sqrt{\frac{\varepsilon_{1}}{2}+\frac{1}{2} \sqrt{\varepsilon_{1}^{2}+\varepsilon_{2}^{2}}}}{\omega \varepsilon_{2}} \tag{4}
\end{equation*}
$$

where c is the speed of light. The variations of skin-depth versus frequency for different types of metals are shown in Fig. 2. At 474 THz , the skin depth is 32 nm for gold, 28 nm for copper, 24.5 nm for silver and 17 nm for aluminum.


Fig. 1. The variations of complex permittivity and electrical conductivity versus frequency for different types of metals: (a) electrical dispersion, and (b) electrical conductivity.


Fig. 2. The skin depth variation versus frequency.

## III. THEORY OF REFLECTARRAY ANTENNA

The reflectarray operation can be seen as a phased array with spatial feed located at $\left(x_{f}, y_{f}, z_{f}\right)$ from the array aperture. For the reflectarray located in $x-y$ plane, the wave is reflected from each unit-cell at direction $\left(\theta_{0}, \varnothing_{0}\right)$ suffer from additional phase shift due to the position of the element in the array $\left(x_{c i}, y_{c i}\right)$ and spacing between the cell element and the feeding horn $d_{i j}$, as shown in Fig. 3. To collimate the reflected wave at direction ( $\theta_{0}, \varnothing_{o}$ ) each unit-cell require a compensation phase:

$$
\begin{equation*}
\varphi_{i j}\left(x_{c i}, y_{c i}\right)=k_{o} d_{i j}+\emptyset_{c i j} \tag{5}
\end{equation*}
$$

where $k_{o}=2 \pi / \lambda_{o}$ is the wave number, $d_{i j}$ is given by [12]:

$$
\begin{equation*}
d_{i j}=\sqrt{x_{c i}-x_{f}^{2}+\left(y_{c i}-y_{f}\right)^{2}+z_{f}^{2}} \tag{6}
\end{equation*}
$$

and $\emptyset_{c i j}$ is the phase shift due to the location of the unitcell in the array:

$$
\begin{equation*}
\varphi_{c i j}=-x_{c i} \sin \theta_{0} \cos \emptyset_{o}-y_{c i} \sin \theta_{0} \sin \emptyset_{o} \tag{7}
\end{equation*}
$$



Fig. 3. The detailed structure of the reflectarray configuration.

## IV. DESIGN OF NDRA REFLECTARRAY WITH SILVER SUPPORTING PLANE

The unit-cell of nano dielectric resonator reflectarray consists of a NDRA made of titanium dioxide $\mathrm{TiO}_{2}$, with anisotropic frequency independent dielectric permittivity of 8.29 in x - and y -axis directions and 6.71 in z -axis direction. The estimated loss tangent is 0.001 [10]. The NDRA has a cylindrical shape with radius $R$ and height $h_{d}$ placed on a square ground plane with side length $L$ and thickness $h$ as shown in Fig. 4 (a). To calculate the required reflection coefficient phase compensation in each unit-cell, the unit-cell is put in a waveguide simulator [13]. The perfect electric and magnetic wall boundary conditions are posted onto the sides of the surrounding waveguide, and result in an infinite array. A linearly polarized plane wave was applied as the far-field excitation of the unit-cells inside the waveguide simulator and only normal incidence angle is considered. There are several limitations to the
infinite array approach. First, all elements of the reflectarray/transmitarray are identical; this is not the case in the real reflectarray/transmitarray in which the diameters of the NDR in each cell element must vary according to the required phase compensation. Secondly, the reflectarray/transmitarray itself is not infinite in extent. Finally, only normal incidence is considered. However, the plane wave has an oblique angle on the real array element, but the phase variation is nearly the same for incidence angles up to $30^{\circ}$ [14]. Different types of metals are used for ground plane as silver, gold, copper, and aluminium. The properties of the ground plane metals are determined using Eq. (1) at 474 THz and are listed in Table 1. The required compensation phase of the reflection coefficient for each unit-cell is achieved by varying the NDRA radius $R$. Figure 5 shows the variation of the reflection coefficient magnitude and phase versus the NDRA radius at 474 THz for different types of ground plane metals. The gold ground plane has the worst reflection coefficient variation from -30.4 to -2.9 , while the silver ground plane gives the best reflection coefficient magnitude varies from -5.8 to -1.7 dB for the NDRA radius varying from 85 nm to 170 nm . This is because the conductivity of the aluminum material is higher than that of the silver material at 474 THz as appeared in Fig. 1 (b), and the penetration depth in aluminum ground plate is higher than that of silver as shown in Fig. 2. The phase of the reflection coefficient span of variation is $360^{\circ}$ for the silver, $19^{\circ}$ for gold, $215^{\circ}$ for the copper, and $136^{\circ}$ for the aluminum ground plate. The silver material has the best performance for the reflectarray unit-cell with reflection coefficient magnitude variation from -5.8 to -1.7 dB , and phase variation from 0 to 360 degrees.


Fig. 4. The detailed structure of the NDRA reflectarray unit-cell: (a) 3-D view, and (b) side view.

Table 1: The optical properties of the different types of metals at 474 THz [17]

| Metal | $\omega_{p}(\mathrm{rad} / \mathrm{sec})$ | $\mathrm{v}_{p}(\mathrm{rad} / \mathrm{sec})$ | $\delta(\mathrm{nm})$ |
| :---: | :---: | :---: | :---: |
| Silver | $1.28 \times 10^{16}$ | $9.19 \times 10^{13}$ | 24.5 |
| Gold | $0.98 \times 10^{16}$ | $2.8 \times 10^{14}$ | 32 |
| Copper | $1.13 \times 10^{16}$ | $3.2 \times 10^{14}$ | 28 |
| Aluminum | $2.3 \times 10^{16}$ | $1.04 \times 10^{15}$ | 17 |



Fig. 5. The variation of the reflection coefficient magnitude and phase versus the NDRA radius at 474 THz: (a) reflection coefficient magnitude, and (b) reflection coefficient phase magnitude.

Figure 6 shows the effect of changing the silver ground plane thickness of the unit-cell on the variation of the reflection coefficient magnitude and phase. By increasing the ground plane thickness, the reflection coefficient magnitude is decreased and the reflection coefficient phase variation is increased to achieve 360 degrees. A compromise between the magnitude and phase of the reflection coefficient has been made. A ground plane thickness of 200 nm has been chosen for reflection coefficient magnitude variation from -1.7 to -5.8 and 360 degrees phase variations. The electric field distribution on the unit-cell of the NDRA reflectarray with silver supporting plane $h=200 \mathrm{~nm}, h_{d}=50 \mathrm{~nm}$, and $R=130 \mathrm{~nm}$ is shown in Fig. 7. The incident plane wave penetrate the silver supporting plane at a distance equal to the skin depth at this frequency 24.5 nm and reflects back to the source direction. The reflection occurs because the thickness of the silver supporting plane is much bigger than the silver skin depth about $8.16 \delta$.

A $21 \times 21$ unit-cell elements NDRA reflectarray is constructed using silver plane with $L=350 \mathrm{~nm}, h=200 \mathrm{~nm}$, and $h_{d}=50 \mathrm{~nm}$ as shown in Fig. 8. The array has total dimensions of $7.35 \times 7.35 \mu^{2}$. A linearly polarized pyramidal nano-horn antenna is used to feed the NDRA
reflectarray located at $8.133 \mu \mathrm{~m}$ from the array aperture. The nano-horn antenna is constructed from gold with $L_{h}=487.5 \mathrm{~nm}$, and aperture size $a \times b$ of $810 \mathrm{~nm} \times 1275 \mathrm{~nm}$. The nano-horn antenna has a maximum gain of 11.1 dBi at 474 THz . The E- and H-plane radiation patterns at 474 THz of the nano-horn and the NDRA reflectarray with different plane thickness $h=30,70$ and 200 nm are shown in Fig. 9. The maximum gain of the NDRA reflectarray is increased by increasing the plane thickness and the SLL is decreased. For $h=200 \mathrm{~nm}$, the first SLLs are -17.9 dB and -15.1 dB in E- and H-plane respectively. The HPBW of the NDRA reflectarray is 4.5 degrees in E-plane and 4.7 degrees in H-plane compared to 40.3 degrees in E-plane and 41.3 degrees in H-plane for the nano-horn antenna.


Fig. 6. The variations of the reflection coefficient magnitude and phase versus the NDRA radius: (a) reflection coefficient magnitude, and (b) reflection coefficient phase magnitude.


Fig. 7. The electric field distribution on the unit-cell with silver supporting plane, $h=200 \mathrm{~nm}, L=350 \mathrm{~nm}, h_{d}=50$ nm and $R=130 \mathrm{~nm}$.


Fig. 8. The $21 \times 21$ unit-cell elements NDRA reflectarray with silver supporting plane.


Fig. 9. The gain patterns plot for a $21 \times 21$ NDRA reflectarray with silver supporting plane for variable ground plane thickness.

## V. DESIGN OF NDRA REFLECTARRAY WITH COPPER SUPPORTING PLANE

The NDRA unit-cell with copper supporting plane has the same construction as shown in Fig. 4. The supporting plane is replaced by copper material. The dimensions of the NDRA unit-cell with copper supporting plane is designed and optimized to operate at 474 THz . The unit-cell dimensions are $h_{d}=105 \mathrm{~nm}$ placed on a square copper ground plane with side length $L=350 \mathrm{~nm}$, thickness $h=200 \mathrm{~nm}$ and variable values for NDRA radius $R$. The incident wave penetrate the copper supporting plane down to the skin depth and reflects back to the source. The variations of the reflection coefficient magnitude and phase for the unit-cell with
copper supporting plane are shown in Fig. 10. A $300^{\circ}$ phase shift of the reflection coefficient unit-cell is achieved by varying the NDRA radius $R$ from 75 to 175 nm . While the reflection coefficient magnitude is changed from -1.8 to -5.6 dB at 474 THz . A $21 \times 21$ unitcell elements NDRA reflectarray with copper supporting plane of thickness $h=200 \mathrm{~nm}$, length of $7.35 \mu \mathrm{~m}$ and NDRA height of 105 nm is constructed. The NDRA reflectarray has maximum gain of 27.2 dBi with front to back ratio of 21 dB . The gain variation versus frequency for the NDRA reflectarray with copper supporting plane and the nano-horn are shown in Fig. 11. The 1-dB gain bandwidth is 35 dB .


Fig. 10. The variation of the reflection coefficient phase and magnitude versus the NDRA radius at 474 THz .


Fig. 11. The gain variation versus frequency for a $21 \times 21$ NDRA reflectarray with copper supporting plane at $L=350 \mathrm{~nm}, h=200 \mathrm{~nm}$, and $h_{d}=105 \mathrm{~nm}$.

## VI. DESIGN OF NDRA REFLECTARRAY WITH ALUMINUM SUPPORTING PLANE

A NDRA reflectarray unit-cell with aluminum supporting plane with side length $\mathrm{L}=350 \mathrm{~nm}$, thickness $\mathrm{h}=200 \mathrm{~nm}$, and $\mathrm{hd}=170 \mathrm{~nm}$ operated at 474 THz is investigated. Figure 12 (a) shows the electric field distribution on NDRA reflectarray unit-cell with aluminum supporting plane at 474 THz with $\mathrm{h}=200 \mathrm{~nm}$, $\mathrm{hd}=170 \mathrm{~nm}$ and $\mathrm{R}=130 \mathrm{~nm}$. The reflection coefficient magnitude and phase variations versus the NDRA radius are shown in Fig. 12 (b). A $360^{\circ}$ phase variation and reflection coefficient magnitude variation from -4.7 to -5.4 dB are achieved. The gain variation versus
frequency for the NDRA reflectarray with aluminum supporting plane is shown in Fig. 13.


Fig. 12. (a) The electric field distribution on the NDRA reflectarray unit-cell with aluminum supporting plane, and (b) the reflection coefficient phase and magnitude versus the NDRA radius at 474 THz .


Fig. 13. The gain variation versus frequency for a $21 \times 21$ NDRA reflectarray with aluminum supporting plane.

## VII. COMPARISON BETWEEN NDRA REFLECTARRAYS WITH DIFFERENT METAL SUPPORTING PLANES

The E-and H-plane gain patterns for $21 \times 21$ NDRA reflectarrays with silver, copper, and aluminum supporting planes are shown in Fig. 14. The reflectarray with copper supporting plane has the maximum gain of 27.8 dBi with lower HPBW of $4.4^{\circ}$ due to the higher reflection coefficient magnitude relative to the other metals. The reflectarray with aluminum supporting plane has the lower gain and the higher bandwidth, due to the increase in the NDRA height with variation of its relative permittivity in the z -direction. Table 2 lists a comparison between the radiation characteristics of the reflectarrays
with different metals supporting plane. A compromise between gain, $1-\mathrm{dB}$ bandwidth, SLL, and HPBW has been applied for choosing the appropriate reflectarray for THz applications.


Fig. 14. The gain radiation patterns plot for a $21 \times 21$ NDRA reflectarray with different supporting plane nano metals.

Table 2: Comparison between the radiation characteristics of NDRA reflectarrays with different metals supporting planes

| Material | Silver | Copper | Aluminum |
| :---: | :---: | :---: | :---: |
| Gain dBi | 25.8 | 27.2 | 25.4 |
| 1-dB BW | 30 THz | 35 THz | 40 THz |
| SLL (dB) | -17.9 | -19.4 | -12.51 |
| HPBW (degrees) | 4.5 | 4.5 | 4.3 |

## VIII. CONCLUSION

The use of NDRA in the design of nano-reflectarray for terahertz application at 633 nm is introduced. The reflectarray unit-cell consists of a cylindrical NDR on a square ground plane of a good conductor. A parametric study for the unit-cell dimensions has been introduced. The gold ground plane has got the worst reflection coefficient, while the silver ground plane gives the best reflection coefficient magnitude. A compromise between the magnitude and phase of the reflection coefficient has been made. A silver ground plane thickness of 200 nm has been chosen for reflection coefficient magnitude variation from -1.7 to -5.8 dB and 360 degrees phase variation. A $21 \times 21$ unit-cell elements NDRA reflectarray is constructed using silver supporting plane
with $\mathrm{L}=350 \mathrm{~nm}$, $\mathrm{h}=200 \mathrm{~nm}$, and $\mathrm{hd}=50 \mathrm{~nm}$. The maximum gain of the NDRA reflectarray is increased by increasing the plane thickness and the SLL is decreased.

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# Compact Triple-Band S-Shaped Monopole Diversity Antenna for MIMO Applications 

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#### Abstract

In this paper, a novel WLAN frequency range monopole antenna is designed and manufactured for MIMO applications. The proposed antenna consists of two L-shaped slots in the S -shaped radiating patch. In this structure, the S -shaped monopole antenna can create dual resonances within the WLAN frequency range. The placement of two L-shaped slots within the S-shaped monopole antenna creates an extra resonance and the desired resonant frequencies are obtained by adjusting the dimension of the S-shaped monopole and the Lshaped slots. The operating frequencies of the proposed antenna are $2.4 / 5.2 / 5.8 \mathrm{GHz}$, which covers WLAN systems. Also, the two elements array configuration of this S-shaped monopole antenna which can be used in MIMO with a very high isolation over three operational bands is studied. The prototypes of the proposed antenna have been constructed and studied experimentally. Good diversity performance, return loss and radiation pattern characteristics are obtained in the frequency band of interest. Simulated and measured results are presented to validate the usefulness of this small proposed antenna structure for MIMO applications.


Index Terms - Diversity antenna, Multi-Output MultiInput (MIMO) applications, triple-band S -shaped monopole.

## I. INTRODUCTION

In wireless systems, signals may combine destructively at a receiver, causing fading to occur. With the rapid growth of wireless communication, it is important to attain sufficient channel capacity and combat multi-path fading and co-channel interferences [1]. In order to improve the quality of wireless downlink
signal, more than one antenna is necessary for the terminal side. In this kind of mobile terminal, two or more antenna elements are envisaged and the restricted space available for antenna is an open issue [2]-[3]. Antenna diversity is a well-known technique to enhance the performance of wireless communication systems by reducing the short term fading and co-channel interference effects of the channel [1]. The reliability of the system can be improved with the use of diversity technology, which is achieved by using the information from the different branches available to the receiver so as to increase the signal-to-noise ratio (SNR) at the decoding stage.

In the last few years, there have been rapid developments in wireless local area networks (WLAN). The $2.4 / 5.2 / 5.8 \mathrm{GHz}(2.4-2.84 \mathrm{GHz} / 5.15-5.35 \mathrm{GHz} /$ $5.725-5.825 \mathrm{GHz}$ ) bands are demanded in practical WLAN applications. During the last years, there are various antenna designs, which enable antennas with low-profile, lightweight, flush mounted and WLAN devices. These antennas include the planar inverted-F antennas [4], and the slot antennas [5]. Planar monopoles are extremely attractive to be used in WLAN applications, and growing research activities are being focused on them in MIMO application systems, because of its advantages, such as simple structure, small size and low cost. Consequently, a number of planar monopoles with different geometries have been experimentally characterized [6]-[9].

In this paper, we propose a printed omni-directional antenna using S -shaped radiating patch. An S-shaped radiating patch with a pair of L-shaped slots which are printed on a dielectric substrate to generate triple-band operation at $2.4,5.2$, and 5.8 GHz is reported. This
structure is suitable particularly for WLAN applications. Two-element arrays of such antennas for MIMO applications are analyzed and the results of the pair that provides the lowest mutual coupling and better omnidirectional radiation pattern are given. The proposed structure is designed based on the antenna presented in [10], but with a lower mutual coupling and higher isolation. In this paper we present a structure for the MIMO antenna elements, in which the identical two antenna elements are orthogonally placed. Then the two antenna elements have orthogonal polarization which can reduce the mutual coupling between the two antennas. The proposed antenna shows advantages of small size, low cost and good omni-directional radiation characteristics. The presented monopole antenna has a small size of $12 \times 18 \mathrm{~mm}^{2}$.

## II. ANTENNA DESIGN

The presented small monopole antenna fed by a microstrip line is shown in Fig. 1, which is printed on an FR4 substrate of thickness 0.8 mm , permittivity 4.4, and loss tangent 0.018 . The basic monopole antenna structure consists of a square patch, a feed line, and a ground plane. The square patch has a width of W. The patch is connected to a feed line with the width of $W_{f}$ and the length of $L_{f}+L_{g n d}$. On the other side of the substrate, a conducting ground plane is placed. The proposed antenna is connected to a $50-\Omega$ SMA connector for signal transmission.

In this study, two L-shaped slots in the S-shaped radiating patch is used to perturb an additional resonance at higher frequencies of WLAN frequency range. In other words, in this structure two L-shaped slots are playing an important role in the triple-band characteristics of this antenna. The final dimensions of the designed antenna are specified in Table 1.


(c)

Fig. 1. Geometry of the proposed S-shaped monopole antenna with a pair of L-shaped slots on the radiating patch: (a) top view, (b) side view, and (c) geometry of the proposed diversity antenna.

Table 1: The final dimensions of the designed antenna

| Param. | mm | Param. | mm | Param. | mm |
| :--- | :--- | :--- | :--- | :--- | :--- |
| $W_{\text {Sub }}$ | 12 | $L_{\text {Sub }}$ | 18 | $W_{f}$ | 1.5 |
| $L_{f}$ | 3 | $W$ | 10 | $L_{g n d}$ | 4 |
| $W_{S}$ | 9.25 | $L_{S}$ | 3.5 | $W_{S 1}$ | 0.25 |
| $L_{S 1}$ | 1 | $W_{L}$ | 9.5 | $L_{L}$ | 4.75 |
| $W_{L 1}$ | 0.25 | $L_{L 1}$ | 0.25 | $L_{X}$ | 15 |
| $W_{X}$ | 30 | $L_{\mathrm{g}}$ | 25 | $W_{d}$ | 8 |
| $L_{d}$ | 2 | $W_{d 1}$ | 7 | $L_{P}$ | 11 |
| $W_{P}$ | 1 | $W_{P 1}$ | 4 | $L_{P 1}$ | 9 |
| $W_{P 2}$ | 4.5 | $W_{f 1}$ | 7 | $W_{f 2}$ | 5 |

## III. RESULTS AND DISCUSSIONS

## A. Monopole antenna for WLAN applications

The proposed microstrip monopole antenna with various design parameters as constructed, and the numerical and experimental results of the input impedance and radiation characteristics are presented and discussed. The parameters of this proposed antenna are studied by changing one parameter at a time and fixing the others. Ansoft HFSS simulations are used to optimize the design and agreement between the simulation and measurement is obtained [11].

Return loss characteristics for ordinary square patch antenna with a rectangular slit (Fig. 2 (a)), S-shaped monopole antenna (Fig. 2 (b)), and the proposed antenna (Fig. 2 (c)) are compared in Fig. 3. As shown in Fig. 3, in order to generate dual-band characteristics (2.4/5.2 GHz ), we use S -shaped radiating patch. By adding two

L-shaped slots in the S -shaped radiating patch, a tripleband is achieved that covers all the $2.4 / 5.2 / 5.8 \mathrm{GHz}$ WLAN.

In order to understand the phenomenon behind this additional resonance performance, the simulated current distributions on the radiating patch for the ordinary square antenna with a rectangular slit and the S -shaped radiating patch at 2.4 GHz and 5.2 GHz are presented in Figs. 4 (a) and (b), respectively. It is found that by using this S -shaped radiating patch, the second resonance at 5.2 GHz can be achieved. Other important design parameters of this structure are L-shaped slots on the Sshaped radiating patch. Figures 5 (a) and (b) present the simulated current distributions on the radiating patch of the proposed antenna at the second resonance $(5.2 \mathrm{GHz})$, and the third resonance $(5.8 \mathrm{GHz})$, respectively. As shown in Figs. 5 (a) and (b), at the second and third resonances, the current flows are more dominant around of the L-shaped slots [12].


Fig. 2. (a) Ordinary square monopole antenna with a rectangular slit, (b) ordinary S-shaped monopole antenna, and (c) the proposed antenna.


Fig. 3. Simulated return loss characteristics for the various square monopole antenna structures shown in Fig. 2.


Fig. 4. Simulated surface current distributions on radiating patch for the proposed antenna without Lshaped slots: (a) at the first resonance frequency (2.4 $\mathrm{GHz})$, (b) at the second resonance ( 5.2 GHz ).


Fig. 5. Simulated surface current distributions on radiating patch for the proposed antenna: (a) at second resonance frequency $(5.2 \mathrm{GHz})$, (b) at third resonance frequency $(5.8 \mathrm{GHz})$.

## B. Monopole antenna array structures for MIMO applications

This antenna element can be arrayed for MIMO applications. The performance of an antenna array suitable for MIMO applications is based on various parameters such as mutual coupling, and radiation pattern. As shown in Fig. 1 (c), two such monopole antennas can be arranged back to back with symmetric configuration and is printed on a printed circuit board (PCB). As shown in Fig. 1 (c), in order to increase the isolation and reduce the mutual coupling between the two monopoles, the L-shaped sleeves are introduced in the ground plane of this design. These sleeves on ground plane act as parasitic elements which help to adjust the resonant frequency and improve bandwidth [4]. Each antenna is directly fed by a $50 \Omega$ microstrip line with 1.5 mm in width.

The antenna configuration with detailed dimensions and the effects of some important parameters of the
proposed antenna have been fabricated as shown in Fig. 6 , and discussed to show how this diversity antenna works. The measured and simulated return loss and mutual coupling characteristic of the proposed antenna were shown in Figs. 7 and 8, respectively. The operating frequencies of the proposed antenna are $2.4 / 5.2 / 5.8 \mathrm{GHz}$, which covers WLAN system. Figure 8, in which the antenna elements are orthogonal, show lower mutual coupling than those structures in which the elements are parallel. For such orthogonal elements, the pattern of each element lies on a plane. As shown in Figs. 7 and 8, there exists a discrepancy between measured data and the simulated results. This discrepancy is mostly due to a number of parameters such as the fabricated antenna dimensions as well as the thickness and dielectric constant of the substrate on which the antenna is fabricated, the wide range of simulation frequencies and also the effect of SMA. In order to confirm the accurate return loss characteristics for the designed antenna, it is recommended that the manufacturing and measurement process need to be performed carefully, besides, SMA soldering accuracy and FR4 substrate quality needs to be taken into consideration [13].


Fig. 6. Photograph of the realized diversity antenna.


Fig. 7. Measured and simulated return loss of the MIMO configured proposed antenna for arrangement of two elements beside.


Fig. 8. Measured and simulated insertion loss (mutual coupling) of the MIMO configured proposed antenna for arrangement of two elements beside.

Figures 9, 10 and 11 illustrate the measured radiation patterns at resonance frequencies, including the copolarization and cross-polarization, in the H-plane ( $x-z$ plane) and E-plane ( $\mathrm{y}-\mathrm{z}$ plane) of the two antenna elements. It can be seen that the two antenna elements have orthogonal polarizations, and also the radiation patterns in $x-z$ plane are nearly omni-directional for the three frequencies.


Fig. 9. Measured radiation patterns for monopole 1 (left) and monopole 2 (right) excitations at 2.4 GHz (first resonance frequency).


Fig. 10. Measured radiation patterns for monopole 1 (left) and monopole 2 (right) excitations at 5.2 GHz (second resonance frequency).


Fig. 11. Measured radiation patterns for monopole 1 (left) and monopole 2 (right) excitations at 5.8 GHz (third resonance frequency).

The envelope correlation can be computed from the S-parameters using the following formula [14]:

$$
\rho_{e}=\frac{\left|S_{11}^{*} S_{12}+S_{21}^{*} S_{22}\right|^{2}}{\left(1-\left|S_{11}\right|^{2}-\left|S_{12}\right|^{2}\right)\left(1-\left|S_{22}\right|^{2}-\left|S_{21}\right|^{2}\right)^{2}}
$$

Figure 12 shows the simulated envelope correlation of the array structure of Fig. 1 (c). For the antenna diversity, the practically acceptable envelope correlation is less than 0.5 . The calculated envelope correlation of the proposed antenna array structure of Fig. 1 (c) can be shown to be less than 0.002 . The evaluation of results shows that the antenna is a good candidate for diversity system for MIMO application.


Fig. 12. Simulated envelope correlation coefficient against frequency using HFSS.

## IV. CONCLUSION

A new triple-band diversity small printed monopole antenna (PMA) with triple-band performance for WLAN applications, presented in this paper. The operating frequencies of the proposed antenna are $2.4 / 5.2 / 5.8 \mathrm{GHz}$ which covers WLAN system. In order to generate a triple-band performance, we insert two L-shaped slots in the S-shaped radiating patch. Also two-element arrays of such antennas in MIMO applications are analyzed. To evaluate the diversity performance, the envelope correlation coefficient of the antenna elements from measured results is calculated. It is proved that the proposed antenna can provide pattern diversity to mitigate multi-path fading problem for WLAN operations. The designed antenna has a small size of $12 \times 18 \mathrm{~mm}^{2}$. Simulated and experimental results show that the proposed antenna could be a good candidate for MIMO applications.

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# Study on Band Gaps of the Photonic Crystal in THz Frequency Range Based on the Periodic WCS-PSTD Method 

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#### Abstract

In this paper, a periodic weakly conditionally stable -pseudospectral time domain (WCS-PSTD) method is presented to simulate photonic crystal in Terahertz frequency range. The time step size in this method is only determined by the mesh length $\Delta z$ and the spatial discretization along the $z$ direction only needs two cells per minimum wavelength. The 3D formulas of the method are presented and the time stability condition of the method is demonstrated. Numerical results show that this method is more efficient than the periodic finite difference time domain (FDTD) method in terms of computer memory and computation time.


Index Terms - Finite difference time domain, pseudospectral method, time stability condition, weakly conditionally stable.

## I. INTRODUCTION

Terahertz (THz) wave has significant transmission loss in free space, so the design and fabrication of controlling device for THz frequency radiation are imperative. Photonic crystal as a novel artificial material has photonic band gaps characteristic [1, 2]. It can be used to control the transmission of THz wave. Therefore, study on the photonic crystal has important effect on the development of Terahertz technique.

The finite-difference time-domain (FDTD) method is one of the most effective tools for the analysis of the photonic crystal [3, 4]. However, because the crosssection of the photonic crystal is circular, staircase approximation is used to model the curved surface. To decrease the approximation error, the cells' size must be very small compared with the wavelength. These fine cells reduce the time step size in the FDTD method, and hence, the FDTD method is computationally expensive. In addition, in the THz frequency region, the longitudinal direction of the photonic crystal is electrically large structure in most cases. Applying the FDTD method to simulate electrically large object, to decrease the dispersion error, a large number of cells (typically 10-20 cells per wavelength) are required. This stringent requirement severely limits the length of the photonic
crystal solvable and increases the computation time inevitably.

Recently, a new weakly conditionally stablepseudospectral time domain (WCS-PSTD) method [5] which is based on the hybrid implicit explicit difference technique [6-9] and the pseudospectral scheme [10-12] is presented. In this method, the time step size is not confined by fine cells and is extremely useful for problems with very fine structures along one or two directions. Meanwhile, this method allows a coarse spatial discretization that only needs two cells per minimum wavelength. Thus, for the simulation of the object which has fine and electrically large structures simultaneously, the WCS-PSTD algorithm is more efficient than the FDTD method in terms of computer memory and computation time. However, for the simulation of the photonic crystal which has periodic structures, the WCS-PSTD method needs to cope with the periodic boundary.

To solve this problem, this paper presents a periodic WCS-PSTD method which introduces the periodic boundary in the conventional WCS-PSTD method [5]. It also combines the hybrid implicit explicit difference technique with the pseudospectral scheme. The time step size in this method is not confined by fine cells and the space discretization along electrically large direction only needs two cells per minimum wavelength. The 3D formulas of the periodic WCS-PSTD method are presented, and final updating equations are given. The time stability condition and space discretization limitation of the method are discussed. When this method is applied to simulate photonic crystal, high computational efficiency is obtained and less computer memory is required, which is demonstrated through numerical examples by comparing with the periodic FDTD method.

By using the periodic WCS-PSTD method to simulate the photonic crystal, some useful conclusions are obtained. The simulation result shows that the photonic crystal has obvious band gap characteristic. The frequency and bandwidth of the band gap have relation with the permittivity of the photonic crystal. As the
increase of the permittivity, the frequency of the band gap decreases and the relative bandwidth of the band gap becomes wider. Besides, the smaller the radius and period length of the photonic crystal are, the higher the frequency range of the band gap. The relative bandwidth of the band gap reaches maximum value when the ratio between the diameter of the photonic crystal and the period length is 0.6 .

## II. FORMULATIONS

Figure 1 shows a schematic view of the photonic crystal under study. The cross-section of the photonic crystal is circular and needs to use very small cells to staircase approximation, as shown in Fig. 2. The length (L) of the photonic crystal is much larger than the wavelength in the THz frequency region. Typically, it is 20-30 times the wavelength. So, the photonic crystal is a complicated structure which has fine size (along the x and $y$ direction) and electrically large size (along the $z$ direction) simultaneously.


Fig. 1. Schematic view of photonic crystal.


Fig. 2. The staircase approximation of the photonic crystal's cross-section.

In the FDTD method, the small cell sizes $\Delta x 1$ and $\Delta y 1$ will confine the time step size $\Delta t$ and result in a
large number of computation time. To remove the confine of the fine space increment on the time step size, the periodic WCS-PSTD method uses a hybrid implicit explicit difference technique to replace the explicit difference along the x and y directions. The 3D formulas for the periodic WCS-PSTD method are as follows: $<$ First procedure $>$

$$
\begin{gather*}
\varepsilon \frac{E_{x}^{n+1 / 2}-E_{x}^{n}}{\Delta t}=\frac{\partial\left(H_{z}^{n+1 / 2}+H_{z}^{n}\right)}{2 \partial y}-\frac{\partial H_{y}^{n}}{\partial z}  \tag{1.1}\\
E_{y}^{n+1 / 2}=E_{y}^{n}  \tag{1.2}\\
\varepsilon \frac{E_{z}^{n+1 / 2}-E_{z}^{n}}{\Delta t}=\frac{\partial\left(H_{y}^{n+1 / 2}+H_{y}^{n}\right)}{2 \partial x},  \tag{1.3}\\
H_{x}^{n+1 / 2}=H_{x}^{n}  \tag{1.4}\\
\mu \frac{H_{y}^{n+1 / 2}-H_{y}^{n}}{\Delta t}=\frac{\partial\left(E_{z}^{n+1 / 2}+E_{z}^{n}\right)}{2 \partial x}-\frac{\partial E_{x}^{n+1 / 2}}{\partial z}  \tag{1.5}\\
\mu \frac{H_{z}^{n+1 / 2}-H_{z}^{n}}{\Delta t}=\frac{\partial\left(E_{x}^{n+1 / 2}+E_{x}^{n}\right)}{2 \partial y} \tag{1.6}
\end{gather*}
$$

<Second procedure>

$$
\begin{gather*}
E_{x}^{n+1}=E_{x}^{n+1 / 2}  \tag{2.1}\\
\varepsilon \frac{E_{y}^{n+1}-E_{y}^{n+1 / 2}}{\Delta t}=\frac{\partial H_{x}^{n+1 / 2}}{\partial z}-\frac{\partial\left(H_{z}^{n+1 / 2}+H_{z}^{n+1}\right)}{2 \partial x},  \tag{2.2}\\
\varepsilon \frac{E_{z}^{n+1}-E_{z}^{n+1 / 2}}{\Delta t}=-\frac{\partial\left(H_{x}^{n+1 / 2}+H_{x}^{n+1}\right)}{2 \partial y},  \tag{2.3}\\
\mu \frac{H_{x}^{n+1}-H_{x}^{n+1 / 2}}{\Delta t}=\frac{\partial E_{y}^{n+1}}{\partial z}-\frac{\partial\left(E_{z}^{n+1 / 2}+E_{z}^{n+1}\right)}{2 \partial y},  \tag{2.4}\\
H_{y}^{n+1}=H_{y}^{n+1 / 2}  \tag{2.5}\\
\mu \frac{H_{z}^{n+1}-H_{z}^{n+1 / 2}}{\Delta t}=-\frac{\partial\left(E_{y}^{n+1 / 2}+E_{y}^{n+1}\right)}{2 \partial x}, \tag{2.6}
\end{gather*}
$$

where $n$ and $\Delta t$ are the index and size of time step.
The calculation for one discrete time step is performed using two procedures in the periodic WCSPSTD method. The first procedure is based on Eqs. (1.1)(1.6), and the second procedure is based on Eqs. (2.1)(2.6). It can be seen from these equations that for the spatial derivatives $\partial x$ and $\partial y$, a hybrid implicit explicit difference technique is used; thus, the equations (1.1), (1.3), (1.5), (1.6), (2.2)-(2.4) and (2.6) can't be calculated directly, because they all include the unknown components defined at the same time step. For example, updating of $E_{x}^{n+1 / 2}$ component, as shown in Eq. (1.1), needs the unknown $H_{z}^{n+1 / 2}$ components at the same time step; thus the $E_{x}^{n+1 / 2}$ component has to be updated implicitly. By substituting Eq. (1.6) into Eq. (1.1), the equation for $E_{x}^{n+1 / 2}$ component is given as:

$$
\begin{align*}
& \left(1-\frac{\Delta t^{2}}{4 \varepsilon \mu} \frac{\partial^{2}}{\partial^{2} y}\right) E_{x}^{n+1 / 2} \\
& =\left(1+\frac{\Delta t^{2}}{4 \varepsilon \mu} \frac{\partial^{2}}{\partial^{2} y}\right) E_{x}^{n}-\frac{\Delta t}{\varepsilon} \frac{\partial H_{y}^{n}}{\partial z}+\frac{\Delta t}{\varepsilon} \frac{\partial H_{z}^{n}}{\partial y} . \tag{3}
\end{align*}
$$

Because the periodic WCS-PSTD method applies the hybrid implicit explicit difference technique to the derivatives $\partial x$ and $\partial y$, its time step size will have no relation with the spatial increments $\Delta x$ and $\Delta y$. This will be demonstrated in the next section.

In the FDTD method, to decrease the dispersion error resulted from the spatial finite difference, spatial discretization should satisfy the condition that 10-20 cells per wavelength are required. This stringent requirement causes a large number of cells along the $z$ direction in the simulation of the photonic crystal, because the longitudinal direction of the photonic crystal is often larger than the wavelength. It not only severely increases the memory requirement, but also increases the computation time.

To overcome the limit of the wavelength on the space discretization $\Delta z$, the periodic WCS-PSTD method uses a Fourier transform algorithm instead of finite difference to represent the spatial derivative $\partial z$. This allows a coarse spatial discretization along z direction that only two nodes per minimum wavelength are required (the demonstration will be shown in the next section). For other spatial derivatives $\partial x$ and $\partial y$, it also applies centered second-order finite differences as that in the standard FDTD method. Thus, the equation for $E_{x}^{n+1 / 2}$ component can be obtained as follows:

$$
\begin{align*}
& \left(1+2 \tau_{1}\right) E_{x}^{n+1 / 2}(i+1 / 2, j, k)-\tau_{1} E_{x}^{n+1 / 2}(i+1 / 2, j+1, k) \\
& -\tau_{1} E_{x}^{n+1 / 2}(i+1 / 2, j-1, k) \\
& =\left(1-2 \tau_{1}\right) E_{x}^{n}(i+1 / 2, j, k)+\tau_{1} E_{x}^{n}(i+1 / 2, j+1, k) \\
& +\tau_{1} E_{x}^{n}(i+1 / 2, j-1, k) \\
& +\frac{\Delta t}{\varepsilon \Delta y}\left[H_{z}^{n}(i+1 / 2, j+1 / 2, k)-H_{z}^{n}(i+1 / 2, j-1 / 2, k)\right] \\
& -\frac{\Delta t}{\varepsilon} \mathfrak{J}^{-1}\left\{\hat{j} k_{z} \mathfrak{J}\left[H_{y}^{n}(i+1 / 2, j, k)\right]\right\}, \tag{4}
\end{align*}
$$

where, $\hat{j}=\sqrt{-1}, \quad \tau_{1}=\Delta t^{2} / 4 \varepsilon \mu \Delta y^{2}, \quad \Delta y$ is the spatial increment along y direction; $i, j$, and $k$ denote the indices of spatial increments respectively along $\mathrm{x}, \mathrm{y}$, and z directions; $\mathfrak{J}$ and $\mathfrak{J}^{-1}$ represent the Fourier transforms and inverse Fourier transforms which were described in detail in references [13].

After $E_{x}^{n+1 / 2}$ component is obtained by using equation (4), component $H_{z}^{n+1 / 2}$ is explicitly updated straightforward as follows:

$$
\begin{align*}
& H_{z}^{n+1 / 2}(i+1 / 2, j+1 / 2, k)=H_{z}^{n}(i+1 / 2, j+1 / 2, k) \\
& +\frac{\Delta t}{2 \mu \Delta y}\left[\begin{array}{l}
E_{x}^{n+1 / 2}(i+1 / 2, j+1, k)-E_{x}^{n+1 / 2}(i+1 / 2, j, k) \\
+E_{x}^{n}(i+1 / 2, j+1, k)-E_{x}^{n}(i+1 / 2, j, k)
\end{array}\right] . \tag{5}
\end{align*}
$$

By following the same procedure, the equation for $E_{z}^{n+1 / 2}$ component can be obtained as follows:
$\left(1+2 \tau_{2}\right) E_{z}^{n+1 / 2}(i, j, k+1 / 2)-\tau_{2} E_{z}^{n+1 / 2}(i+1, j, k+1 / 2)$
$-\tau_{2} E_{z}^{n+1 / 2}(i-1, j, k+1 / 2)$
$=\left(1-2 \tau_{2}\right) E_{z}^{n}(i, j, k+1 / 2)+\tau_{2} E_{z}^{n}(i+1, j, k+1 / 2)$
$+\tau_{2} E_{z}^{n}(i-1, j, k+1 / 2)$
$+\frac{\Delta t}{\varepsilon \Delta x}\left[H_{y}^{n}(i+1 / 2, j, k)-H_{y}^{n}(i-1 / 2, j, k)\right]$
$-\frac{\Delta t^{2}}{2 \varepsilon \mu \Delta x} \mathfrak{J}^{-1}\left\{\hat{j} k_{z} \mathfrak{J}\left[E_{x}^{n+1 / 2}(i+1 / 2, j, k)\right]\right\}$
$+\frac{\Delta t^{2}}{2 \varepsilon \mu \Delta x} \mathfrak{J}^{-1}\left\{\hat{j} k_{z} \mathfrak{J}\left[E_{x}^{n+1 / 2}(i-1 / 2, j, k)\right]\right\}$,
where, $\tau_{2}=\Delta t^{2} / 4 \varepsilon \mu \Delta x^{2}, \Delta x$ is the spatial increment along x direction.

Because the photonic crystal has periodic structure along the x direction, the computation of $E_{z}^{n+1 / 2}$ component at the periodic boundary needs to be modified as follows:

$$
\begin{align*}
& E_{z}^{n+1 / 2}(i, j, k+1 / 2) \\
& -\tau_{2}\left[E_{z}^{n+1 / 2}(2, j, k+1 / 2)-E_{z}^{n+1 / 2}(1, j, k+1 / 2)\right] \\
& +\tau_{2}\left[E_{z}^{n+1 / 2}(I, j, k+1 / 2)-E_{z}^{n+1 / 2}(I-1, j, k+1 / 2)\right] \\
& =E_{z}^{n}(i, j, k+1 / 2) \\
& +\tau_{2}\left[E_{z}^{n}(2, j, k+1 / 2)-E_{z}^{n}(1, j, k+1 / 2)\right] \\
& -\tau_{2}\left[E_{z}^{n}(I, j, k+1 / 2)-E_{z}^{n}(I-1, j, k+1 / 2)\right]  \tag{7}\\
& +\frac{\Delta t}{\varepsilon \Delta x}\left[H_{y}^{n}(1+1 / 2, j, k)-H_{y}^{n}(I-1 / 2, j, k)\right] \\
& -\frac{\Delta t^{2}}{2 \varepsilon \mu \Delta x} \mathfrak{J}^{-1}\left\{\hat{j} k_{z} \mathfrak{J}\left[E_{x}^{n+1 / 2}(1+1 / 2, j, k)\right]\right\} \\
& +\frac{\Delta t^{2}}{2 \varepsilon \mu \Delta x} \mathfrak{J}^{-1}\left\{\hat{j} k_{z} \mathfrak{J}\left[E_{x}^{n+1 / 2}(I-1 / 2, j, k)\right]\right\},
\end{align*}
$$

here, $i=1$ and $I$ denote the meshes at the periodic boundary respectively.

The computations for other components $H_{y}^{n+1 / 2}$, $E_{y}^{n+1}, E_{z}^{n+1}, H_{x}^{n+1}$ and $H_{z}^{n+1}$ can be obtained by following the same procedure and will not be discussed in detail.

It should be noted that, in contrast to the standard Yee's algorithm, the periodic WCS-PSTD method does not require a spatially staggered grid along the z direction, because Fourier transforms operation is
global. It means that the field components $E_{x}$ and $H_{y}$, $E_{y}$ and $H_{x}$ are located at the same nodes in the periodic WCS-PSTD method, as shown in Fig. 3.

where,

Fig. 3. Spatial grid of the field components in the periodic WCS-PSTD method.

## III. STABILITY AND NUMERICAL DISPERSION ANALYSIS

The relations between field components of Eqs. (1) and (2) can be represented in a matrix form as follows:

$$
\begin{align*}
& {[E] U^{n+1 / 2}=[F] U^{n},}  \tag{8}\\
& {[C] U^{n+1}=[D] U^{n+1 / 2},} \tag{9}
\end{align*}
$$

$$
\begin{align*}
& {[E]=\left[\begin{array}{cccccc}
1 & 0 & 0 & 0 & 0 & -a D_{y} / 2 \\
0 & 1 & 0 & 0 & 0 & 0 \\
0 & 0 & 1 & 0 & -a D_{x} / 2 & 0 \\
0 & 0 & 0 & 1 & 0 & 0 \\
b D_{z} & 0 & -b D_{x} / 2 & 0 & 1 & 0 \\
-b D_{y} / 2 & 0 & 0 & 0 & 0 & 1
\end{array}\right],}  \tag{10}\\
& \left([E][C] \zeta-[E][D][E]^{-1}[F]\right) U^{n}=0, \\
& \zeta \text { indicates growth factor. By applying the forward } \\
& \text { Fourier transforms to both sides of equation (10), it } \\
& \text { obtains equation (11), where, } X=\frac{a b D_{x}^{2}}{4}, Z=\frac{a b\left(j k_{z}\right)^{2}}{4} \text {, } \\
& Y=\frac{a b D_{y}^{2}}{4}, S=(1-X)(1-Y), T=\frac{a b D_{x} D_{y}}{4}: \\
& {\left[\begin{array}{cccccc}
\zeta-1 & -T(\zeta+1) & 0 & 0 & a D_{z} & -\frac{a D_{y}}{2}(\zeta+1) \\
\frac{2 T}{(1-Y)} & \zeta-1 & 0 & -a D_{z} & \frac{-a D_{z} T}{(1-Y)} & \frac{a D_{x}}{2}\left(\zeta+\frac{1+Y}{1-Y}\right) \\
0 & 0 & \zeta-1 & \frac{a D_{y}}{2}(\zeta+1) & \frac{-a D_{x}(\zeta+1)}{2} & 0 \\
\frac{-b D_{z} T(1+Y)}{S} & -b \zeta D_{z} & \frac{b D_{y}}{2}\left(\zeta+\frac{(1+X)}{(1-X)}\right) & \zeta-1 & \frac{2 T(1-Y+2 Z)}{S} & \frac{-a b D_{x} D_{z} Y}{S} \\
b \zeta D_{z} & 0 & \frac{-b D_{x}}{2}(\zeta+1) & -T(\zeta+1) & \zeta-1 & 0 \\
\frac{-b D_{y}}{2}(\zeta+1) & \frac{b D_{x}}{2}(\zeta+1) & 0 & 0 & 0 & \zeta-1
\end{array}\right] U^{n}=0 .} \tag{11}
\end{align*}
$$

$[D]=\left[\begin{array}{cccccc}1 & 0 & 0 & 0 & 0 & 0 \\ 0 & 1 & 0 & a D_{z} & 0 & -a D_{x} / 2 \\ 0 & 0 & 1 & -a D_{y} / 2 & 0 & 0 \\ 0 & 0 & -b D_{y} / 2 & 1 & 0 & 0 \\ 0 & 0 & 0 & 0 & 1 & 0 \\ 0 & -b D_{x} / 2 & 0 & 0 & 0 & 1\end{array}\right]$,
$U^{n}=\left[\begin{array}{llllll}E_{x}^{n} & E_{y}^{n} & E_{z}^{n} & H_{x}^{n} & H_{y}^{n} & H_{z}^{n}\end{array}\right], a=\Delta t / \varepsilon, b=\Delta t / \mu$, $D_{m}=\partial / \partial m(m=x, y, z)$ represents the first derivative operator with respect to $m$.

By substituting Eq. (9) into Eq. (8), it obtains:

For a nontrivial solution of (11), the determinant of the coefficient matrix in (11) should be zero. It can be obtained:

$$
\begin{equation*}
(\zeta-1)^{2}\binom{(\zeta-1)^{2}-4 Z \zeta-Y(\zeta+1)^{2}}{-X(\zeta+1)^{2}+X Y(\zeta+1)^{2}}^{2}=0 \tag{12}
\end{equation*}
$$

By solving equation (12), the growth factor $\zeta$ is obtained:

$$
\begin{gather*}
\zeta_{1}=1  \tag{13}\\
\zeta_{2,3}=\frac{N \pm \sqrt{N^{2}-R^{2}}}{R} \tag{14}
\end{gather*}
$$

where, $\quad R=1-X-Y+X Y, \quad N=1+X+Y+2 Z-X Y$. According to the stability condition during field advancement, the module of growth factor $\zeta$ cannot be larger than 1. In equation (14), the relation $\left|\zeta_{2,3}=1\right|$ can be obtained when the condition $R^{2} \geq N^{2}$ is satisfied. $D_{x}$ and $D_{y}$ represent the first derivative operator with respect to $x$ and $y$. They are approximated by centered second-order finite differences. So it has the relations $D_{x}=2 j \sin \left(k_{x} \Delta x / 2\right) / \Delta x$ and $D_{y}=2 j \sin \left(k_{y} \Delta y / 2\right) / \Delta y$ [6],

$$
\begin{equation*}
R^{2} \geq N^{2} \Rightarrow 1+Z \geq 0 \tag{15}
\end{equation*}
$$

Because the maximum value of $k_{z}$ is $\frac{2 \pi}{2 \Delta z}$, it has:

$$
\begin{equation*}
a b\left(\frac{2 \pi}{2 \Delta z}\right)^{2} \leq 4 \Rightarrow \Delta t \leq \frac{2 \Delta z}{c \pi} \tag{16}
\end{equation*}
$$

where, $c=1 / \sqrt{\varepsilon \mu}$ is the speed of light in the medium.
It can be seen from Eq. (16) that the maximum time step size in the periodic WCS-PSTD method is only determined by the cell size $\Delta z$. This is very useful when the object of analysis has fine scale dimensions along the $x$ and $y$ directions.

By substituting the expression $\zeta=e^{j \omega \Delta t}$ into equation (12), the dispersion relation for the periodic WCS-PSTD method can be obtained as follows:

$$
\begin{equation*}
\sin ^{2}\left(\frac{\omega \Delta t}{2}\right)=\frac{r_{y}^{2}+r_{x}^{2}+r_{z}^{2}+r_{x}^{2} r_{y}^{2}}{1+r_{x}^{2}+r_{y}^{2}+r_{x}^{2} r_{y}^{2}} \tag{17}
\end{equation*}
$$

where, $\quad r_{z}=\left(c \Delta t k_{z} / 2\right)^{2}, \quad r_{x}=\left(c \Delta t \sin \left(k_{x} \Delta x / 2\right) / \Delta x\right)^{2}$, $r_{y}=\left(c \Delta t \sin \left(k_{y} \Delta y / 2\right) / \Delta y\right)^{2}$. It can be seen from equation (17) that the numerical dispersion error of the periodic WCS-PSTD method has no relation with the spatial cell size $\Delta z$. It is only decided by the cell sizes $\Delta x, \Delta y$, and the time step size $\Delta t$. As a result, the spatial cell size $\Delta z$ is not confined by the wavelength. It only needs to satisfy the Nyquist sampling theorem that only two nodes per minimum wavelength are
required along the $z$ direction.
It concludes from above analysis that in the periodic WCS-PSTD method, the time step size $\Delta t$ is only determined by the spatial increment $\Delta z$, and spatial increment $\Delta z$ only needs to satisfy with the condition: $\Delta z \leq \lambda_{\text {minimum }} / 2$. This will be very useful in the simulation of the photonic crystal, because the photonic crystal has very fine scale along x and y directions and is electrically large along $z$ direction. For solving this problem the periodic WCS-PSTD method is more efficient than the periodic FDTD method in terms of computer memory and computation time, which will be demonstrated in next section.

## IV. SIMULATION AND ANALYSIS

To demonstrate the accuracy and efficiency of the periodic WCS-PSTD method, the photonic crystal shown in Fig. 1 is simulated. The radius (r) and length (L) of the photonic crystal are 20 um and 3000 um, respectively. The period length of the photonic crystal is $\mathrm{T}=100 \mathrm{um}$. The material of the photonic crystal is silicon with dielectric constant $\varepsilon_{r}=11.7$. A uniform plane wave polarized along the x direction is normally incident on the photonic crystal. The propagation direction of the wave is along the y direction. The time dependence of the excitation function is as follows:

$$
\begin{equation*}
E_{x}(t)=\exp \left[-\frac{4 \pi\left(t-t_{0}\right)^{2}}{t_{1}^{2}}\right] \tag{18}
\end{equation*}
$$

where, $t_{0}$ and $t_{1}$ are constants, and both equal to $1 \times 10^{-12} \mathrm{~s}$. In such a case, the highest frequency of interest is 2 THz and the minimum wavelength of the source is about 150 um .

The periodic WCS-PSTD method is used to simulate the transmitted field at the back of the photonic crystal. For comparison, the results calculated by the periodic FDTD method are also shown. Because the structure has circular cross-section, it is discretized by using staircase approximation, as shown in Fig. 2. To guarantee the computational accuracy, the circle is discretized by using $20 \times 20$ cells, so the cell sizes $\Delta x 1$ and $\Delta y 1$ are both equal to $2 u m$, corresponding to $1 / 75$ of the minimum wavelength. In other computation domain, $\Delta x 2$ and $\Delta y 2$ are $3 u m$ and $15 u m$, respectively. Along the z direction, for the periodic FDTD method, considering the limit of the wavelength on the space discretization, the space increment $\Delta z$ is selected to be 15 um , corresponding to $1 / 10$ of the minimum wavelength. While for the periodic WCS-PSTD method, space increment $\Delta z$ can be increased to 75 um, corresponding to $1 / 2$ of the minimum wavelength. To cut off the outer boundary, periodic boundary condition is applied along the x direction and convolutional perfectly matched layer (CPML) that are ten cells thick are applied along the $y$ and $z$ directions. Thus, for the periodic FDTD
and periodic WCS-PSTD methods, the total mesh numbers are $40 \times 110 \times 240$ and $40 \times 110 \times 80$, respectively. The time step size in the periodic FDTD method is:
$\Delta t=1 / c \sqrt{\left(\frac{1}{2 \times 10^{-6}}\right)^{2}+\left(\frac{1}{2 \times 10^{-6}}\right)^{2}+\left(\frac{1}{15 \times 10^{-6}}\right)^{2}}=4.69 \times 10^{-3} \mathrm{ps}$, which is the maximum time step size to ensure the numerical stability. In the periodic WCS-PSTD method, the time step size that is only determined by cell size $\Delta z$
is selected to be $\Delta t=\frac{2 \times 75 \times 10^{-6}}{c \pi}=159 \times 10^{-3} \mathrm{ps}$, which is 34 times as that of the periodic FDTD method.

Figure 4 depicts the transmitted field $E_{x}$ calculated by using the periodic FDTD method and the periodic WCS-PSTD method. It can be seen from this figure that the results of these two methods agree very well with each other, which shows the periodic WCS-PSTD method has high computational accuracy.


Fig. 4. The transmitted field $E_{x}$ calculated by using periodic FDTD method and periodic WCS-PSTD method.

The computation time and memory requirement of the simulation above are summarized in Table 1. It can be seen from this table that both the memory requirement and computation time of the periodic WCS-PSTD method are reduced significantly compared with those of the periodic FDTD method. Because large spatial cell and large time step size are used, the memory requirement of the periodic WCS-PSTD method is reduced by $60 \%$, and its computation time is almost $1 / 30$ of that of the periodic FDTD method.

Table 1: Simulation time and memory requirement for the periodic FDTD method and periodic WCS-PSTD method

|  | $\Delta z$ <br> $(\mathrm{um})$ | $\Delta t$ <br> $(\mathrm{ps})$ | Time <br> (minute) | Memory <br> Requirement $(\mathrm{Mb})$ |
| :---: | :---: | :---: | :---: | :---: |
| FDTD <br> method | 15 | 0.0046 | 320 | 311.73 |
| WCS-PSTD <br> method | 75 | 0.159 | 12 | 115.45 |

The transmission coefficient ( Tr ) of the photonic crystal calculated by using the periodic FDTD method
and the periodic WCS-PSTD method are presented in Fig. 5. The computation formula of Tr is as follows:

$$
\begin{equation*}
T_{r}=20 \log _{10}\left|E_{x} / E_{x}^{\prime}\right| \tag{19}
\end{equation*}
$$

here, $E_{x}$ denotes the transmitted field $E_{x}$ calculated by using the periodic FDTD method and the periodic WCSPSTD method; $E_{x}^{\prime}$ is the magnitude of the incident wave.

It can be seen from Fig. 5 that in the frequency range from 1.5 THz to 1.8 THz , the transmission coefficient Tr is below to -10 dB . This is a direct evidence of that the photonic crystal has obvious band gap in this frequency range. The relative bandwidth of the band gap is $18.18 \%$. The distribution of the electric field $E_{x}$ at frequency 1.7 THz is shown in Fig. 6. From this figure, it can be seen that the incident wave is reflected completely and little wave penetrates the photonic crystal at this frequency.


Fig. 5. The transmission coefficient of the photonic crystal calculated by using the periodic FDTD method and the periodic WCS-PSTD method.


Fig. 6. The distribution of the electric field $E_{x}$ at frequency 1.7 THz .

It should be noted that in Fig. 5 there is a slightly divergence between the results of the periodic FDTD method and the periodic WCS-PSTD method at 1.7 THz . The difference between these two methods in time domain is too small to be neglected, as shown in Fig. 4, but in frequency domain, it is enlarged by the resonance effect of the photonic crystal at 1.7 THz . The divergence between these two methods is brought about by the
splitting-error in the periodic WCS-PSTD method. The periodic WCS-PSTD method applies the hybrid implicit explicit difference technique. This technique will bring a splitting error which is proportional to the time step size. The detailed discussion about the splitting error of the hybrid implicit explicit difference technique has been presented in [14]. So, compared with the periodic FDTD method, the accuracy of the WCS-PSTD is reduced slightly. However, this reduction of the accuracy doesn't affect the periodic WCS-PSTD method to get correct results. The periodic WCS-PSTD method can be used in the analysis which doesn't require the accuracy strictly.

Because the periodic WCS-PSTD method is more efficient than the periodic FDTD method in terms of computer memory and computational time, it is used to analyze the band gap characteristic of the photonic crystal in detail.

Firstly, the relation between the frequency range of band gap and the radius of the photonic crystal is analyzed. The length and period of the photonic crystal is 3000 um and 100 um . The radius of the photonic crystal increases from 5 um to 40 um . The variations of the frequency range of the band gap with respect to radius are shown in Table 2. In this table, Rt which is equal to $2 \times r / T$ represents the ratio between the diameter of the photonic crystal and the period length. It can be seen from this table that as the increase of the radius, the band gap of the photonic crystal moves to a lower frequency range. The relative bandwidth of the band gap has maximum value equal to $29.85 \%$ when the radius of the photonic crystal is 30 um .

Table 2: Variations of the frequency range of the band gap with respect to the radius

| r (um) | Rt | Frequency <br> Range (THz) | Relative <br> Bandwidth |
| :---: | :---: | :---: | :---: |
| 10 | 0.2 | $2.70-2.80$ | $3.64 \%$ |
| 15 | 0.3 | $1.97-2.06$ | $4.47 \%$ |
| 20 | 0.4 | $1.50-1.80$ | $18.18 \%$ |
| 25 | 0.5 | $1.30-1.75$ | $29.51 \%$ |
| 30 | 0.6 | $1.14-1.54$ | $29.85 \%$ |
| 35 | 0.7 | $1.03-1.33$ | $25.42 \%$ |
| 40 | 0.8 | $0.97-1.18$ | $19.53 \%$ |

When it keeps the radius $\mathrm{r}=20$ um unchanged and increases the period length of the photonic crystal from 50 um to 200 um , the band gap of the photonic crystal also moves to a lower frequency range, as shown in Table 3. The relative bandwidth of the band gap has maximum value equal to $30.12 \%$ when period length of
the photonic crystal is 66.66 um .
From Table 2 and 3, we can see that the relative bandwidth of the band gap is mainly determined by the ratio between the diameter and the period length. It reaches its maximum value when the ratio is 0.6 , no matter what the radius and period length are.

Table 3: Variations of the frequency range of the band gap with respect to the period length

| T (um) | Rt | Frequency <br> Range (THz) | Relative <br> Bandwidth |
| :---: | :---: | :---: | :---: |
| 50 | 0.8 | $1.94-2.37$ | $19.95 \%$ |
| 60 | 0.7 | $1.78-2.32$ | $26.34 \%$ |
| 66.66 | 0.6 | $1.72-2.33$ | $30.12 \%$ |
| 80 | 0.5 | $1.62-2.19$ | $29.92 \%$ |
| 100 | 0.4 | $1.50-1.80$ | $18.18 \%$ |
| 133 | 0.3 | $1.48-1.61$ | $4.85 \%$ |
| 200 | 0.2 | $1.34-1.37$ | $3.97 \%$ |

In addition, the frequency range and relative bandwidth of the band gap also have relation with the dielectric constant of the photonic crystal. The variations of the frequency range and bandwidth with respect to relative dielectric constant $\varepsilon_{r}$ are shown in Table 4. Here, the geometry of the photonic crystal, including the period length, radius and length, are unchanged. It can be seen from this table that as the increase of the dielectric constant, the frequency of the band gap decreases and the relative bandwidth becomes wider.

However, if the polarization of the incident wave is along the z direction, namely, the longitudinal direction of the photonic crystal, the band gap characteristic will become unobvious. The transmission coefficient of the photonic crystal impinged by a plane wave polarized along the z direction is shown in Fig. 7. In this figure, the transmission coefficient is above -10 dB in all the frequency range, which means that some incident wave passes through the photonic crystal and the band gap of the photonic crystal disappears.

Table 4: Variations of the frequency range of the band gap with respect to relative dielectric constant

| $\varepsilon_{r}$ | Frequency Range (THz) | Relative Bandwidth |
| ---: | :---: | :---: |
| 3 | $2.64-2.67$ | $1.13 \%$ |
| 5 | $2.23-2.67$ | $7.34 \%$ |
| 7 | $1.94-2.16$ | $10.73 \%$ |
| 9 | $1.74-2.01$ | $14.40 \%$ |
| 11 | $1.60-1.90$ | $17.14 \%$ |
| 13 | $1.48-1.83$ | $21.25 \%$ |



Fig. 7. The transmission coefficient of the photonic crystal impinged by a plane wave polarized along the $z$ direction.

To validate this, the distribution of the electric field $E_{z}$ at the frequency 1.7 THz is depicted in Fig. 8. It can be seen from this figure, that at this case most of the incident wave penetrate the photonic crystal obviously.


Fig. 8. The distribution of the electric field $E_{z}$ at frequency 1.7 THz .

It concludes from the analysis above that when the photonic crystal is impinged by a plane wave polarized along the radial direction, the photonic crystal exhibits obvious band gap characteristic; the smaller the radius and period length of the photonic crystal are, the higher the frequency range of the band gap. The relative bandwidth of the band gap reaches maximum value when the ratio between the diameter of the photonic crystal and the period length is 0.6. Besides, the frequency and bandwidth of the band gap have relation with the permittivity. As the increase of the permittivity, the frequency of the band gap decreases and the relative bandwidth of the band gap becomes wider.

## VI. CONCLUSION

This paper introduces a periodic WCS-PSTD method which is based on the hybrid implicit explicit difference technique and pseudospectral scheme to simulate the photonic crystal. The maximum time step size in this method is only determined by cell size $\Delta z$
and the spatial discretization along $z$ direction only needs two cells per wavelength. When this method is applied to simulate the photonic crystal, high computational efficiency is obtained and less computer memory is required, which is demonstrated through numerical examples by comparing with the periodic FDTD method. This method not only can be used in the simulation of photonic crystal, but also be useful in other electromagnetic problems where both fine and electrically large structures are used.

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# Reconfigurable Circular Polarization Antenna with Utilizing Active Devices for Communication Systems 

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#### Abstract

In this paper, the reconfigurable antenna with circular polarization diversity is proposed for wireless local area network (WLAN) communication systems. The proposed antenna consisting of two PIN diodes are appropriately positioned to achieve polarization diversity. By switching the PIN diodes ON/OFF mode, the proposed antenna enables to operate either RHCP mode or LHCP mode. A good impedance match ( $\mathrm{S}_{11} \leq-10 \mathrm{~dB}$ ) of $935 \mathrm{MHz}(1.995 \sim 2.930 \mathrm{GHz})$ at RHCP mode, an impedance bandwidth ( $\mathrm{S}_{11} \leq-10$ ) of 965 MHz (1.935~2.960 GHz) at LHCP mode. The experimental result shows that the proposed antenna has a circular polarization bandwidth ( $\mathrm{AR} \leq 3 \mathrm{~dB}$ ) of about 415 MHz at the center frequency of 2.4 GHz for both RHCP and LHCP mode.


Index Terms - Circular polarization, microstrip antenna, PIN diode, reconfigurable.

## I. INTRODUCTION

Circular polarization is one of the common polarization schemes used in current wireless communication systems, such as radar and satellite systems, since it can provide better mobility and weather penetration than linear polarization. With the rapid development of wireless communication systems, such as wireless local area network (WLAN), multi-input and multi-output (MIMO) and personal communications service (PCS), radio frequency terminals with multiple functions are required to adapt to various standards and systems. Reconfigurable antennas with frequency adjustability, radiation pattern selectivity, and polarization diversity are good candidates for these applications [1,2].

In general, a polarization reconfigurable antenna can be designed to switch between different linear polarizations, two circular polarizations (right hand and left hand circular polarization) and any number of elliptical polarizations (with different axial ratios and tilt angles). In most investigations the point refers to the switch between (right hand circular polarization) RHCP and (left hand circular polarization) LHCP in a desired frequency $[3,4]$. In some papers, antenna could switch to linear polarization in addition of RHCP and LHCP too [5-8]. In some cases, the polarization is switched between vertical and horizontal linear polarization [9,10]. Proposed [11-14]. Adopting an electrical and mechanical method as well as active elements may provide reconfigurable antennas in terms of frequency band [15-17], polarization [18], pattern [19] and multiapplication [20] in some UWB antennas these elements are used to obtain alterable notched-bands. For this purpose some designs include RF MEMS [21], PIN diodes [22], microfluidic [23] and Varactor diodes [24,25,26].

In this paper, a novel CPW-Fed microstrip antenna which uses two PIN diodes to switch between RHCP and LHCP, is introduced. This antenna is designed to work in center frequency of 2.4 GHz which is applicable in WLAN system.

This proposed CP reconfigurable antennas with concise structure are easy to be manufactured and can be used in various wireless communication systems. Section 2 demonstrates the design principle and the configurations of CP reconfigurable patch antennas with L elements on the patch and on the ground. Section 3 describes the simulated and experimental performances of the two patch antennas in details. The conclusions are
drawn in Section 4.

## II. DESIGN PRINCIPLE AND ANTENNA CONFIGURATIONS

Figure 1 shows the geometry and dimensions of the proposed antenna, which consists of a rectangular ground plane with dimension of L and W and a square slot in the center of ground. Four inverted-L-shape grounded strips around the corners, and an inverse vertical T-shape strip between two upper inverted-Lshape strips are embedded in the square slot.

The proposed antenna is designed on an FR4 substrate with a loss tangent of 0.02 , permittivity of 4.4 , and a thickness of 1 mm . The antenna is fed by a 50 -ohm CPW having a single strip of width $\mathrm{W}_{\mathrm{f} 1}=5 \mathrm{~mm}$ and two identical gaps of width $\mathrm{g}=0.4 \mathrm{~mm}$. The single strip of the CPW is protruded into the slot by a width of $\mathrm{W}_{\mathrm{f} 1}, \mathrm{~W}_{\mathrm{f} 2}$, $W_{f 3}$ and $W_{f 4}$. Two parameters, $W_{f 1}$ and $g$ are adjusted to produce $50 \Omega$ impedance for feeding of the antenna. Other parameters of feeding strip such as $\mathrm{W}_{\mathrm{f} 2}, \mathrm{~W}_{\mathrm{f} 3}, \mathrm{~W}_{\mathrm{f} 4}$ and the width of them are embedded and adjusted for impedance matching and resonance bandwidth improvement.

The CP operation of the proposed antenna is chiefly related to the four grounded inverted-L strips inserted around the corners of the square slot.


Fig. 1. (a) Geometry of the proposed antenna, (b) photograph of the fabricated antenna, and (c) dimension of proposed antenna: $\mathbf{L}_{1}=9, \mathbf{L}_{2}=11, \mathbf{L}_{3}=12.5, \mathbf{L}_{4}=7.5$, $\mathbf{L}_{5}=23, \mathbf{L}_{\mathbf{6}}=5.5, \mathbf{L}_{7}=4, \mathbf{S}_{\mathbf{1}}=1, \mathbf{S}_{\mathbf{2}}=2, \mathbf{D}_{\mathbf{1}}=14, \mathbf{D}_{\mathbf{2}}=35, \mathbf{D}_{\mathbf{3}}=7$, $\mathbf{W}_{\mathbf{f 1}}=5, \mathbf{W}_{\mathrm{f} 2}=8, \mathbf{W}_{\mathrm{f} 3}=5, \mathbf{W}_{\mathrm{f} 4}=7, \mathbf{L}_{\mathbf{f} 2}=3.3, \mathbf{L}_{\mathrm{f} 3}=16.5, \mathbf{L}_{\mathbf{f} 4}=1$, $\mathbf{g}=\mathbf{0 . 4}, \mathrm{K}=\mathbf{1}$ (unit: mm ).

In Fig. 1 the path of current in upper strips can be controlled by use of two PIN diodes. To feed PIN diodes by DC supply, two stubs with dimension of $1 \times 1.5 \mathrm{~mm}$ are used. Each stub has one 100 pF capacitor in one side and other side is connected to PIN diode. To make diodes ON we can use these stubs for giving positive DC voltage to diodes [22].

When diode is in the OFF-state, it works like a small capacitor which can be considered as an open circuit. When diode is in ON-state it works like a small
resistance. In an ideal state, this resistance can be considered as a short circuit.

PIN diodes used in the proposed antenna are BAR64-02W diodes. According to datasheet of this diode, in ON-state it has $2.1 \Omega$ resistance and in OFFstate it equals to 0.17 pF capacitance.

## III. EXPERIMENTAL RESULTS AND DISCUSSION

In each step of the design procedure, the full-wave analyses of the proposed antenna were performed using Ansoft HFSS (ver. 13). For simulation of the diodes in on state we model them by a resistance of $2.1 \Omega$. We also model the diodes in off state with a capacitance of 0.17 pF .

The proposed antenna with dimensions in Fig. 1 (c) has been fabricated on an FR4 substrate with a loss tangent of 0.02 , permittivity of 4.4 , rectangular dimensions of $75 \times 70 \mathrm{~mm}$, and thickness of 1 mm . The photograph of fabricated antenna is shown in Fig. 1 (b). In Fig. 2, the measurement and simulated results of in RHCP and LHCP state are shown. An Agilent E8363C vector network analyzer has been used to measure antenna parameters. Embedding inverted-L-shape grounded strips at the upper corner of square slots make the CP polarization possible. These strips are separated by two PIN diodes. When D1 is ON and D2 is OFF, the polarization of the antenna will be RHCP, and when D2 is ON and D 1 is OFF , the polarization of the antenna will be LHCP. So by making the diodes ON or OFF different polarization will be obtained.


Fig. 2. Simulated and measured reflection coefficient of the antenna for RHCP and LHCP.

The simulated and measured axial ratio (AR) results in RHCP and LHCP states is shown in Fig. 3. As it is seen, the AR for RHCP and LHCP states is the same and in frequency range of $2.180 \sim 2.595$, the AR is lower than 3 dB . In this bandwidth, it can be considered a circular polarization for proposed antenna.

The L-shape strips at the lower corners are for AR improvement and increasing of the antenna bandwidth. Center frequency of AR are affected by length of L6.

This length is chosen to have minimum axial ratio at frequency of 2.4 GHz . As we can see in Fig. 4, by increasing the length L6 the axial ratio bandwidth shifts to lower frequencies.


Fig. 3. Measured and simulated AR for: (a) RHCP and (b) LHCP.


Fig. 4. Simulated AR values for different values of L6.
Current distributions on the patch antenna when it is fed from OFF/ON state of PIN diode are shown in Fig. 5, respectively. The symmetry in current distributions is mainly due to preserved symmetry in the antenna design. When diodes are ON, the current distribution is stronger and enforces the current distribution on the main patch for circular polarization.

The inversed T-shape strip embedded between upper L-shape strips will increase the gain of the antenna and make it smoother in the bandwidth. The simulated results for the gain of the proposed antenna in RHCP and LHCP state are shown in Fig. 6. In this figure, the measured results of the gain in LHCP state is shown too.


Fig. 5. Simulated current distribution on the antenna frequency 20.4 GHz : (a) PIN diode OFF and (b) PIN diode ON.


Fig. 6. Measured and simulated results for antenna gain in RHCP and LHCP.

The gain of proposed antenna is upper than 2 dB in the desired bandwidth and in center frequency 2.4 GHz it is 3.2 dB . In Fig. 6, it can be seen that as the operation frequency increases, the antenna gain is increased too. The antenna gain in the AR bandwidth in the best mood is 3.6 dB . The gain of the antenna has a direct relationship with the length of the antenna. Figure 7 shows the gain of the antenna for different values of L . Increasing the length of the antenna will increase the gain of the antenna and it has a negligible effect on the AR and return loss. The radiation pattern of the proposed antenna is demonstrated respectively in Fig. 8 (a) H-plan and Fig. 8 (b) E-plan. Also Figs. 9 (a) and (b) shows respectively comparison of radiation pattern for RHCP and LHCP.


Fig. 7. Gain of the proposed antenna for various values of $L$.


Fig. 8. Radiation pattern of antenna: (a) H-plan and (b) E-plan.


Fig. 9. Radiation pattern of antenna: (a) RHCP antenna and (b) LHCP antenna.

## IV. CONCLUSION

A novel polarization reconfigurable antenna has been presented. The antenna is simple to design and fabricate and exploits PIN diode switches to deliver reconfigurable capability. This antenna uses four inverted-L grounded strips for the excitation of two orthogonal resonant modes for CP radiation. Measured results have good agreement with simulated ones. The proposed antenna is suitable for Bluetooth/WLAN ( $2400-2484 \mathrm{MHz}$ ) frequencies.

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# Terahertz Dielectric Sensor Based on Novel Hexagon Meta-Atom Cluster 

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#### Abstract

In this paper, we report meta-atom sensor based on planar hexagon split ring resonators. The subwavelength structure is designed to operate in terahertz frequency band. A modified version of split ring resonator geometry is simulated for sensing dielectric changes by placing thin dielectric layers as sample materials on the full frontal surface of sensor. The effective parameters are retrieved using Nicolson-Ross and Weir method. The meta-atom sensor shows significant changes in resonant frequency as a function of transmission (magnitude of $S_{21}$ parameter) response, which was observed when the sensor is loaded with the dry layer of dielectric materials of different dielectric constants. This paper contributes new shape of metaatom structure used as a terahertz dielectric sensor. The proposed sensor can be used in multitudinous terahertz near field sensing applications.


Index Terms - Dielectric sensor, meta-atom, near field, split ring resonator, terahertz.

## I. INTRODUCTION

Meta-atoms or metamaterials are attractive manmade materials that can influence the light waves in astonishing manners. The structure of metamaterial is primarily constructed of subwavelength metallic resonators printed all together on dielectric substrate materials. Their electromagnetic properties are mainly consequent from the resonating metal structure rather than from atoms and or molecules as they do in conventional materials [1].

Meta-atoms can be manufactured to get a wide range of electromagnetic characteristics at desired frequencies. Such characteristics are still not founded in naturally occurring materials, which is why they named 'meta', which means beyond the materials. The natural materials typically occupy the positive real electric permittivity and magnetic permeability; whereas,
negative values of the permittivity and permeability are possibly attainable in nature through the radiation manipulation [2]. Meta-atoms, e.g., thin metallic wires [3], can reduce and shift the fundamental frequency to a lower part of the frequency spectrum, thus resulting in a negative permittivity and permeability at lower frequencies. In nature, achieving negative values of permeability is uncommon but can be obtained from magnetic resonances in ferro-magnets at high frequencies. Meta-atoms, such as split-ring resonators (SRR) [4] and cut-wire pairs [5], can exhibit magnetic dipoles and negative permeability in response to magnetic waves up to the optical regime [6]. Achieving negative values of electromagnetic responses in metaatoms open ways to realize double-negative characteristics, in which the permittivity and permeability are less than zero at the same frequencies resulting in negative-index material. Such types of sophisticated materials have never been occurred in the nature [7].

In their initial stages, the meta-atoms were tested in combination with the transmission wires to exhibit effective parameters of negative permittivity and permeability [8]. Negative index materials have incited a very wide interest in meta-atoms due to their strange behavior, and became the hub of metamaterial research and extend its operation in visible frequency spectrum [9].

Meta-atoms offered volume of opportunities in order to improve functional abilities of existing microwave and optical components and devices with exploring unexampled applications. Current research explored so far super lenses [10], biosensors based on meta-atoms, which are sensitive to small changes in the amount and response of a sample [11] and invisibility cloaks for the camouflage of an object from being detected [12]. Terahertz metamaterial research is newly emerged technology; that is why fundamental studies,
novel designs and advanced metamaterial applications are yet to be sufficiently explored. It is conceived that this novel research field will have great impact on science and engineering.

The split ring resonators have been used as fundamental circuits in numerous meta-atom applications. Because of their fascinating properties, they are still at the top of all their counterparts. They proved their effectiveness in high frequency applications where the other circuits do not. The artificial structures exhibit negative resonances at negative refractive index regions, which is impossible for any natural material. Meta-atom resonators find useful applications in detection of gas leakage and defects [13] infrared and thermal emission detectors [14] and in imaging [15,16].

Split ring resonators of different geometries are used as a basic unit cell for sensor clusters because of their unique characteristics of having negative permeability, permittivity and refractive index, which is numerically proved in open literature. Initially, meta-atoms were proposed for microwave frequency band and later they were introduced in terahertz and infrared frequency. In recent years, meta-atoms have proved their worth in terahertz nondestructive sensing applications because of the non-ionizing characteristics. There are many analytical models of split ring resonators are reported up to now.

Split ring resonator based meta-atom sensor is a circuit that can provide specific quantitative analytical information. Split ring resonators are arranged in circular and rectangular geometries for various scientific applications. The effect of substrate material cannot be ignored at very high frequencies; also metal strips offer very high loss [17]. The loss can be minimized by utilizing very thin and low permittivity substrate material [18]. Considering high loss situation, low permittivity substrate is utilized in this report.

There are a number of geometrical shapes reported in the literature demonstrating the usage of SSR. S-shape resonators [19], omega resonators [20], various shapes of hexagons [ $21,22,23,24,25$ ] and $v$-shape resonators [26] and other geometries are reported for left-handed meta-atoms applications. Meta-atoms with double negative index have attracted the interest of the scientists, especially in the terahertz regime [27].

Meta-atoms exhibit concentrated electromagnetic field, which is necessary to get the improved selectivity of sensors for detection of quite minute amount of analytes [28]. Such detection ability opens minds for new applications to be explored through the use of metaatoms. For example, meta-atoms have replaced the use of metallic conductors in many applications where surface plasmons were employed [29]. The sub wavelength sized meta-atoms are capable to be used as sensing devices at high frequencies [30]. Resonant modes of two dimensional sub wavelength resonators are
suitable for sensing applications [31]. The nondestructive property of meta-atoms makes them highly suitable candidate for label free sensing of biochemical substances. Meta-atoms are also proposed for sensing of dielectrics by using electric permittivity near-zero narrow waveguide channels [32]. A meta-atom based microwave nondestructive evaluation sensor to detect materials with smaller imperfections compared to a wavelength was reported in [33]. It is revealed through studies that the sensitivity and resolution of ordinary sensors can be significantly enhanced by incorporation of meta-atoms.

Split ring resonators with different shapes are used for the sensors and microelectronic devices. Split ring resonator based biosensor with a small electrical size to detect the occurrence of bio molecular binding was experimentally demonstrated [34]. The structure of that biosensor was consisted of two pairs of SRR and a planar microwave transmission line.

So far, meta-atom based thin dielectric layer sensing structures have proved their effectiveness in the field of sensing. These electrically small devices are potential candidates for future scientific applications.

## II. MATERIAL AND METHODS

The meta-atoms are periodically arranged in the form of cluster, which is illustrated in Fig. 1. Meta-atoms are of particular interest in the terahertz regime because of high spectral resolution, where most natural materials exhibit only weak electric and magnetic responses, and hence, cannot be utilized for sensing of minute samples. The introduction of terahertz meta-atom is believed to be an important step that can further advance terahertz research and development. Simulation results demonstrate the responses and their effective parameters like the real parts of negative permeability and electric permittivity.


Fig. 1.4 by 4 novel meta-atom cluster.

The increase in the number of split rings will increase the number of split gaps and metallization on the substrate; thus, an increase in the surface electric field will be observed on the split gap areas and overall surface of the metamaterial unit cell. The increasing values of overall capacitance, which includes gap and surface capacitance, will reduce the operating frequency as they are inversely proportional to each other. A simple inductor and capacitor $(L C)$ tank circuit can represent the analogy of split ring resonator. The split rings form the magnetic inductance and can be considered as inductors. The capacitance is mainly formed in and around split gap areas.

The split ring resonator exhibit electromagnetic resonance when the electric energy stored in capacitor; i.e., gap is in balance with the magnetic energy stored in the inductors, i.e., split rings. The changes in capacitance, $C$ and inductance, $L$ due to dielectric loading from biomolecule leads to a considerable shift in the frequency of resonance [35] as shown in equation (1):

$$
\begin{equation*}
f_{C}=\frac{1}{2 \pi \sqrt{L C}} \tag{1}
\end{equation*}
$$

The unit cell of the dielectric sensor is designed with new shape of hexagonal split ring resonators (HSRR). Two HSRR are aligned face to face with modified gaps at the top and bottom spaced with $1.5 \mu \mathrm{~m}$ to each other on a thin dielectric substrate. Figure 2 shows the geometric dimensions of the HSRR. The proposed metaatom cluster is simulated using Computer Simulation Technology (CST) studio suite 2014 to compute the complex scattering constitutive parameters. The simulated scattering parameters are obtained for the retrieval of effective parameters.


Fig. 2. Meta-atom unit cell design structure.
The effective parameters of hexagon split ring resonators are extracted using Nicolson-Ross and Weir method [36,37]. The Kramers-Kronig relationship [38] is further applied in order to get improved results. The unit cell dimensions are $30 \mu \mathrm{~m} \times 30 \mu \mathrm{~m} \times 0.5 \mu \mathrm{~m}=450 \mu \mathrm{~m}^{3}$. The width of inner and outer gap area is made $1.5 \mu \mathrm{~m}$.

The split ring is made of gold strips with the permittivity $\varepsilon_{\mathrm{r}}=11.9$.

The gold strips are printed on the substrate. Selection of the material strip is based on the fact that electrical conductivity of gold and annealed copper is $5.8 \times 10^{7}$ Siemens per meter. The strip thickness is $0.017 \mu \mathrm{~m}$. The use of low permittivity materials causes deeper resonances at terahertz frequency [39]. Due to this reason, RT5880LZ with relative permittivity $\left(\varepsilon_{r}\right)$ of 1.96 and permeability $\left(\mu_{r}\right)$ of 1 is used as a substrate material to achieve smaller unit to wavelength ratio. The cell dimensions are summarized in Table 1.

Table 1: Meta-atom unit cell dimensions

| Parameters | Dimensions $(\mu \mathrm{m})$ |
| :--- | :---: |
| Gap $(g 1, g 2, g 3, g 4)$ | 1.5 |
| Strip width $(s)$ | 1 |
| Strip spacing $(v)$ | 1 |
| Strip length $(l 1, l 2)$ | 10.062 |
| Horizontal width $(w)$ | 20 |
| Substrate thickness | 0.5 |

The effective parameters like permittivity and permeability are calculated using equations (2) and (3) as:

$$
\begin{align*}
& \mu_{r}=\frac{2}{j k_{0} d} \times \frac{1-v_{2}}{1+v_{2}}  \tag{2}\\
& \varepsilon_{r}=\frac{2}{j k_{0} d} \times \frac{1-v_{1}}{1+v_{1}} \tag{3}
\end{align*}
$$

In above equations, ' $k_{0}$ ' is the wave number and ' $d$ ' is the substrate thickness.

The scattering parameters are represented as the sum and difference terms as given in equations (4) and (5):

$$
\begin{align*}
& v_{1}=S_{21}+S_{11}  \tag{4}\\
& v_{2}=S_{21}-S_{11} \tag{5}
\end{align*}
$$

## A. Quality factor of the resonant meta-atom cluster

Quality factor or Q factor is an important figure of merit that needs to be considered when describing the sensitivity of the meta-atom cluster based dielectric sensors. The Q factor of a resonance peak or dip can be calculated from the resonant frequency $\left(f_{0}\right)$ and the frequency bandwidth $(\Delta f)$ of the resonant peak at -3 dB power point [40], as shown in equation (6). Quality factors in the microwave portion of terahertz frequency operated meta-atoms are observed approximately 10 [41]. Unloaded Q factor of reported meta-atom cluster is calculated using -3 dB bandwidth formula and the result is summarized in Table 2.

$$
\begin{equation*}
Q=f_{0} / \Delta f \tag{6}
\end{equation*}
$$

Table 2: Unloaded Q factor at resonant frequency

| Resonant Frequency | Quality Factor |
| :---: | :---: |
| 3.9 THz | 95 |

The value of Q factor is proportional to the location of resonant frequency. This value is also dependent on the sharpness of the transmission. The deeper and narrower transmission dip with near to zero reflection results in higher value of Q factor.

## III. RESULTS AND DISCUSSION

The sensor is constituted by hexagon split ring resonators, which are periodically arranged on a thin dielectric substrate material. Perpendicular incidence external field is applied in order to get strong electric and magnetic field response from meta-atom sensor. The direction of incidence is such that it is perpendicular to the metamaterial surface plane to observe the transmission spectra of the metamaterial unit cell. The electric and magnetic field is polarized in parallel to the long edges of the sensor along $y$-axis and $z$-axis respectively. The perpendicular incident waves can induce electric response when the electric field polarization is parallel to the long edges of the structure, and the parallel incident waves are easy to infuse the magnetic response when there is a loop in the metamaterial split ring resonator structure. The strong $L C$ resonance can also be observed by the surface electric field distribution, and that the electric field is mainly focused on the upper and lower capacitive gap area as shown in Fig. 3.


Fig. 3. Surface electric field distribution localized in the split gaps of hexagonal meta-atom unit cell.

The localization of surface electric field distribution is concentrated on the small gap areas because of increased capacitance. The overall surface electric field of sensor is not attributed only to the field at the split gaps.

The effective complex permeability of proposed meta-atom sensor at resonant frequency is shown in Fig. 4. According to that, the real value of complex permeability is negative at the frequency at the resonant
frequency. There is only one instance where the real part of effective permittivity goes negative, and that is the region of resonance. The effective permittivity graph is shown in Fig. 5. The real part of electric permittivity and magnetic permeability exhibit a sharp negative value around the fundamental resonant frequency and remains negative in the frequency region from 3.9 to 4.1 THz .

Split ring resonators are asymmetric structures and mainly used in microwave and terahertz applications because of the presence of loop structure in their structural geometry. At the electric resonant frequency, the current flows parallel to the polarization direction, which indicates that the meta-atom split ring resonator acts like an electric dipole. The flowing surface current in the long metallic wires generates magnetic response, which is why, the retrieved permeability goes negative around the resonant frequency. In comparison to the magnetic response, the electric response is stronger, which can be observed in negative value of electric and magnetic response of the retrieved permittivity and permeability.


Fig. 4. Effective permeability.


Fig. 5. Effective permittivity.

The reason of this response is the perpendicular incidence and parallel polarization of electric field component. When flowing current on the two corners of split ring resonator goes in phase causes less induction in the metallic wires and magnetic field becomes weaker at resonant frequency.

A stop band is observed at the resonant frequency under unloading condition or when the sample layer is not loaded on the surface of sensor. At the same instant, the real part of the effective permittivity goes sharp to the negative value. The real part of the retrieved permeability also becomes negative around the resonant frequency. Simultaneous negative values of permittivity and permeability can cause refractive index to exhibit negative value. The imaginary value of effective complex permittivity is appeared to be positive, which somehow satisfies the conditions for passivity and causality keeping in view of limitations related to Nicholson-Ross and Weir method [42], in which the meta-atom cluster behaves as a power source with no power dissipation. The dielectric constant and thickness of substrate is kept constant in all experimental simulations along with the sample thickness, which is maintained to 100 nanometer. Scaling down the sensor size to the suitable values will result in sensing the presence of thinner sample layers. There is a shift in the transmission observed when the meta-atom cluster based sensor was loaded with three different dielectric materials of different dielectric constants, as shown in Fig. 6.


Fig. 6. Transmission spectra of meta-atom cluster under unloading and loading conditions.

Changing electric field causes the change in refractive index that yields the shift in transmission on frequency domain when the structure is loaded with dielectric materials of different permittivity. These materials were simulated for different loading conditions and are tabulated in Table 3.

Table 3: Dielectric materials used for sample loadings

| Material | Relative <br> Permittivity | Relative <br> Permeability | Shift <br> $\Delta f / f$ |
| :---: | :---: | :---: | :---: |
| Rogers <br> Ultralam 2000 | 2.5 | 1 | 0.2 THz |
| Rogers <br> RO 3003 | 3 | 1 | 0.5 THz |
| Polyimide | 3.5 | 1 | 1.1 THz |

Unloaded transmission ( $\mathrm{S}_{21}$ magnitude) is observed at the resonant frequency when the surface of the sensor was not exposed to the sample material. Transmission shift was observed when the cluster was loaded consecutively with Rogers Ultralam 2000, Rogers RO 3003 and Polyimide.

## IV. CONCLUSION

The planar hexagon meta-atom cluster based dielectric sensor reported in this paper exhibits left handed characteristics at THz frequency band. The presence of the thin dry dielectric layers on the surface of the sensor was observed as the transmission $\left(\mathrm{S}_{21}\right.$ parameter magnitude) is shifted towards lower frequency values. Significant changes were observed under loading samples with higher dielectric constants. Fabrication and dielectric characterization of such metaatom cluster based sensor is the future extension of this research work.

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# Using MATLAB to Model Inhomogeneous Media in Commercial Computational Electromagnetics Software 

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#### Abstract

This paper presents a new method to model inhomogeneous media in commercial electromagnetics software, especially FEKO. In this method, the inhomogeneous medium is fragmented to some homogeneous pieces. If the size of these pieces is chosen correctly, then the electromagnetic behaviors of them and inhomogeneous medium are the same. Since creating these homogeneous pieces in FEKO manually is very difficult and time consuming, MATLAB is employed to create these pieces in FEKO.


Index Terms - FEKO, inhomogeneous media, MATLAB.

## I. INTRODUCTION

These days, the computational electromagnetic software products, like FEKO [1], become essential tools for any electromagnetic design procedure. These products can simulate a various type of electromagnetic media and devices such as antennas, waveguides, filters, couplers, radomes and so on. So, many designers use them to verify their designs. But most of them cannot model the inhomogeneous media in a userfriendly way.

On the other hand, the usage of inhomogeneous media is quickly increasing due to their enormous applications. For example, the inhomogeneous media are used as antenna radome, substrate of microstrip devices and device coating [2-4]. And also, they are used to design microwave filters [5] and frequency selective surfaces [6].

This paper presents new toolboxes to model inhomogeneous media in computational electromagnetics software. These toolboxes are based on MATLAB [7] which is a powerful numerical computing environment and is widely used for research, academic and industrial purposes. A toolbox that is based on MATLAB has some advantages, e.g., the user can utilize the generalpurpose functions of MATLAB to customize it.

In this paper, modeling of inhomogeneous medium in FEKO is presented, but the proposed method can be
easily applied to other commercial computational electromagnetics software, such as CST [8], HFSS [9].

## II. DESIGN PROCEDURE

In the presented method, the inhomogeneous medium is fragmented to $N$ homogeneous pieces and the inhomogeneous medium is estimated by these homogeneous pieces. If the dimensions of pieces are very smaller than wavelength or the inhomogeneous medium parameters are about constant in each piece, then the electromagnetic behavior of fragmented medium is similar to the one for inhomogeneous medium. In other words, the inhomogeneous medium is modeled by some homogeneous pieces, which their sizes are depended on the simulation frequency and inhomogeneous medium parameters.

In this method, a large number of homogeneous media should be created in FEKO to model inhomogeneous media. But creation of these pieces in FEKO manually is very difficult, time consuming and almost impossible and it is necessary to automate it.

To solve this problem, FEKO is controlled by using MATLAB [8] and a toolbox is created in MATLAB in which inhomogeneous medium is estimated to some homogeneous small pieces and create these pieces in FEKO. The output of this toolbox is a FEKO file that contains modeled inhomogeneous medium.

## A. Using MATLAB to create media in FEKO

FEKO in addition to having a CAD environment for modeling various types of media and geometries, has a scripting interface for advanced users which is named Edit FEKO. In Edit FEKO environment, user can utilize all the capabilities of FEKO by using known and defined commands.

Considering this particular capability of FEKO, any structure can be created in FEKO by using MATLAB. To do this, MATLAB must write all necessary Edit FEKO commands to an ASCII file that its suffix is PRE. This file could be opened in Edit

FEKO and any other commands can be added to it depending on user needs. After simulation by FEKO, the modeled structure and its results are available in POST FEKO.

## B. Inhomogeneous media modeling

There is two ways in FEKO to model a homogeneous medium in Cartesian coordinate. The first is to use QU command to create cubical dielectric elements. This is the simplest way to model a dielectric or magnetic cube in Edit FEKO, but periodic boundary conditions cannot be applied to the media which are created by this command. Hence, this way is useful to model finite inhomogeneous media.

Another way is to use BP and ME commands. The BP command creates a flat parallelogram which its type is determined by using ME command. So, dielectric media can be created by combining these two commands. Periodic boundary condition can be applied to the media which are created by the second method. So, this method is useful to model infinite inhomogeneous media. Two toolboxes are presented in this paper. The first toolbox can be modeled infinite inhomogeneous media and the second one is used to model finite inhomogeneous media.

## C. Infinite structures

To model and simulate infinite inhomogeneous structures in two dimensions, as discussed above, the inhomogeneous medium is fragmented to several homogeneous media using MATLAB as shown in Fig. 1.

Fig. 1. (a) A typical infinite inhomogeneous medium, and (b) its estimation by some homogeneous media.

The medium parameters of each homogeneous piece are estimated by the average weights of inhomogeneous parameters as given in equations 1,2 and 3 :

$$
\begin{align*}
& \varepsilon_{n}= \frac{1}{\alpha_{n}-\alpha_{n-1}} \int_{\alpha_{n-1}}^{\alpha_{n}} f(\alpha) d \alpha,  \tag{1}\\
& n=1,2, \ldots, N \\
& \mu_{n}= \frac{1}{\alpha_{n}-\alpha_{n-1}} \int_{\alpha_{n-1}}^{\alpha_{n}} g(\alpha) d \alpha,  \tag{2}\\
& n=1,2, \ldots, N \\
& \sigma_{n}= \frac{1}{\alpha_{n}-\alpha_{n-1}} \int_{\alpha_{n-1}}^{\alpha_{n}} h(\alpha) d \alpha .  \tag{3}\\
& n=1,2, \ldots, N
\end{align*}
$$

In these equations, $\varepsilon_{n}, \mu_{n}$ and $\sigma_{n}$ are medium parameters of $n^{\text {th }}$ piece and $\alpha_{n-1}$ and $\alpha_{n}$ are its start and end position, respectively.

It is remarkable that in this toolbox, while the variations of inhomogeneous medium parameters are more severe, more fragmentation is done and vice versa. So, it needs shorter time to simulate.

Figure 2 shows the toolbox for infinite media. Inputs of this toolbox are $\varepsilon_{r}, \mu_{r}$ and $\sigma$ of inhomogeneous medium, the direction of homogeneity and its range, minimum fragmentation size, variation tolerance and the address of output file.

More fragmentation is generated if minimum fragmentation size is decreased. If difference of medium parameters of two nearby pieces is less than variation tolerance value, then these two pieces will be merged together.

In the right side of toolbox window, the fragmented media and parameters of each section are shown.


Fig. 2. Presented toolbox to model infinite inhomogeneous media.

In order to verify the proposed method, an infinite inhomogeneous medium is modeled in FEKO by presented toolbox. The parameters of the modeled medium are $\varepsilon_{r}(z)=4 e^{5 z}, \mu_{r}=1, \quad \sigma(z)=0$ and its thickness is 20 cm along z axis. The medium is infinite along x and y axes.

A plane wave with $T E^{z}$ polarization is illuminated to it and the angle of incidence is $\theta^{i}$. The frequency of plane wave is 1 GHz and its electric field strength is $1 \mathrm{~V} / \mathrm{m}$. The reflection and transmission coefficients of this structure are obtained by simulation. Figure 3 shows this modeled structure with periodic boundary condition in FEKO.

This structure has analytical solution [9]; therefore, the results of simulation can be compared with analytical results. Figure 4 depicts the simulation and analytical results for assumed structure.


Fig. 3. The estimated model of mentioned structure in FEKO.


Fig. 4. The amplitute of transmition and reflection coefficient obtained from analytical solution and simulation.

As can be seen in Fig. 4, the proposed method acts as expected and its results have exact agreement with analytical results.

Another slob with constitutive parameters $\varepsilon_{r}(z)=4+5 z / d, \mu_{r}=1, \sigma(z)=0$ is modeled by the proposed toolbox. The thickness of slab is 20 cm . A plane wave impinges normally on the slab and the reflection and transmission coefficient of the slab are simulated and the results are compared to an analytical solution [10] that is plotted in Fig. 5. As shown in this figure, the simulated and analytical results are in full compliance.


Fig. 5. The amplitute of transmition and reflection coefficient obtained from analytical solution and simulation.

## D. Finite structures

To model finite inhomogeneous structures in FEKO as discussed above, the inhomogeneous medium is divided to several homogeneous cubes using MATLAB as depicted in Fig. 6.


Fig. 6. (a) A typical finite inhomogeneous medium, and (b) its estimation by some homogeneous cubes.

Figure 7 shows the toolbox for finite inhomogeneous media. Its inputs are medium
dimensions in $\mathrm{x}, \mathrm{y}$ and z axes, $\mathcal{E}_{r}, \mu_{r}$ and $\sigma$ functions, the size of small homogeneous cubes and the address of output file which its type is PRE file.

A finite inhomogeneous medium with $\mu_{r}=1$, $\varepsilon_{r}=\log \left(x^{2}+y^{2}+z^{2}+1\right)+1$ and $\sigma=0$ is modeled by proposed toolbox. The dimensions of medium are equal in three axes and are equal to 20 cm . The modeled medium is depicted in Fig. 8.

A plane wave with $T E^{z}$ polarization is illuminated to the issued structure at $\theta^{i}=135^{\circ}$ and $\phi^{i}=-135^{\circ}$. The frequency of plane wave is 1 GHz and its electric field strength is $1 \mathrm{~V} / \mathrm{m}$.

The radar cross section (RCS) of issued structure is simulated and ploted in xy-plane as shown in Fig. 9.


Fig. 7. Presented toolbox to model finite inhomogeneous meida.


Fig. 8. The estimated model of mentioned structure in FEKO.


Fig. 9. Radar cross section of proposed finite structure.

## III. CONCLUSION

In this paper, a new method is presented in which inhomogeneous media are modeled in FEKO by using MATLAB. In this method, inhomogeneous medium is fragmented to some homogeneous pieces and these pieces are created in FEKO by MATLAB. Two toolboxes are presented in this paper to implement this method for finite and infinite inhomogeneous media. To verify the proposed method, a structure which has analytical solution is modeled by this method. The simulation results and analytical solutions have exact agreement.

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# Influence of the Simulation Parameters on the Normalized Impedance Derived by the Random Coupling Model Simulation 

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#### Abstract

The random coupling model (RCM, introduced by the "chaos group" in the University of Maryland, is found of great use in making statistical predictions of the induced voltages and currents on objects or components within complicated (wavechaotic) cavities when excited by external high power microwave (HPM) radiation. A key point to applying the RCM to a real system is to generate the normalized cavity impedance, which can be described by the random matrix theory (RMT), from the cavity loss parameter by using random matrix Monte Carlo simulation. The influences of the simulation parameters on the statistics of the generated normalized impedance are presented and discussed in this paper. It's found that the statistics of the normalized impedance only depends on the loss parameter, $\alpha$, which agrees with the theory. When $\alpha$ increases, the variances of the eigenvalues, the diagonal elements and the off-diagonal elements of the normalized impedance are exponentially damped with different damping factor, which are experimentally verified in the paper.


Index Terms - Cavity loss parameter, normalized impedance matrix, random coupling model.

## I. INTRODUCTION

The coupling of high power electromagnetic (HPEM) waves with systems such as cars, aircraft, ships, and et. al., has drawn a lot of attention. One problem in treating these problems is the short wave length nature of the radiation. When the wavelength of the radiation becomes much smaller than the enclosure size of the target system, the coupling properties depend in great detail on the size and shape of the enclosure, the geometry of the coupling ports, and on the frequency of the radiation [1]. Furthermore, the electromagnetics quantities within the enclosure will be very sensitive to the enclosure shape, the internal object positions and
orientations, the external radiation frequency, and the coupling ports geometry. At present, even with a lot of fast and powerful computers that utilize efficient 3-D numerical simulation, addressing this problem is still a great challenge because of numerous computational time and CPU resources.

To deal with this problem, the "chaos group" at the University of Maryland introduced the random coupling model, which is a statistical model that can characterize the fluctuations of the impedance and scattering matrices of wave-chaotic metallic-enclosed cavity coupled with one port [2] and multiple ports [3]. This model has been extended to make statistical predictions of the induced voltages and currents on components within the enclosure when excited by external short wave-length EM radiation [4].

Considering the short trajectories effects, Hart et. al., show that the statistics of the impedance matrix, $\boldsymbol{Z}_{\text {cav }}$, of a wave-chaotic cavity coupled with $N$ ports, can be divided into two parts that describe the universal and system-specific properties of the cavity as, $[5,6]$ :

$$
\begin{equation*}
\boldsymbol{Z}=j \Im\left[\boldsymbol{Z}_{\text {ave }}\right]+\left(\Re\left[\boldsymbol{Z}_{\text {ave }}\right]\right)^{1 / 2} \boldsymbol{z}\left(\Re\left[\boldsymbol{Z}_{\text {ave }}\right]\right)^{1 / 2} \tag{1}
\end{equation*}
$$

The matrix, $\boldsymbol{Z}_{\text {cav }}$, is the ensemble average of cavity impedance which describes the system-specific details of the cavity.

The normalized impedance matrix, $\boldsymbol{z}$, can be derived from the random matrix theory and the random plane wave hypothesis [2,3]. The $N \times N$ normalized impedance matrix for the time reversal symmetry (TRS) electromagnetic-wave systems within which the medium is characterized by real, symmetric permittivity and permeability tensors, is shown as:

$$
\begin{equation*}
\boldsymbol{z}_{N}=\frac{1}{j \pi} \sum_{n=1}^{M} \frac{\boldsymbol{w}_{N} \boldsymbol{w}_{N}^{T}}{\left(k^{2}-k_{n}^{2}\right) / \Delta k_{n}^{2}-j \alpha} \tag{2}
\end{equation*}
$$

where $\boldsymbol{w}_{\mathrm{N}}$ is $N$ dimensional vector whose elements are Gaussian random variables with zero mean and unit
variance, $\alpha$ is the cavity loss parameter, $k$ is the wave number corresponding to the incoming frequency, $k_{\mathrm{n}}$ is the wavenumber of cavity eigenvalues, $\Delta k_{\mathrm{n}}{ }^{2}$ is the mean spacing of the adjacent eigenvalues and for a 3D cavity $\Delta k_{\mathrm{n}}^{2}=2 \pi^{2} /(k V)$ ( $V$ is the cavity volume).

For the TRS system, the probability density function (PDF) of the normalized nearest neighbor eigenfrequency spacing $\varepsilon$, defined as equation (3), follows a certain universal curves which is the well-known Wigner distribution as shown in equation (4), [7]:

$$
\begin{gather*}
\varepsilon=\frac{k_{n+1}^{2}-k_{n}^{2}}{\Delta k_{n}^{2}}  \tag{3}\\
P(\varepsilon)=\frac{\pi}{2} \varepsilon \operatorname{Exp}\left(-\frac{\pi \varepsilon^{2}}{4}\right) . \tag{4}
\end{gather*}
$$

In this paper, $2 \times 2$ normalized impedance matrix $z$ is considered. A large ensemble of $z$ is generated based on equation (2) through random matrix Monte Carlo simulation (which will be described in Section II). In Section III and IV, the influence of the simulation parameter $M$ and $\alpha$ on the statistics of $z$ will be discussed respectively. According to the simulation results, the statistics of $z$ only depends on $\alpha$ and the relation between them is experimentally verified in Section V.

## II. RANDOM MATRIX MONTE CARLO SIMULATION

According to equation (2), the point to generate the normalized impedance $z$ is to produce $M$ independent normalized eigenvalues $k_{\mathrm{n}}{ }^{2} / \Delta k_{\mathrm{n}}{ }^{2}$ with the PDF of nearest spacing $\varepsilon$ following the Wigner distribution. An alternative approach given in [7] is to generate an $M \times M$ real symmetric random matrix corresponding to the Gaussian orthogonal ensemble (GOE) in which the diagonal elements are independent Gaussian-distributed with zero mean and unit variance, and the off-diagonal elements have the same distribution with the diagonal elements except for the variance equaling to 0.5 .

The distribution of the eigenvalues, $\lambda_{\mathrm{M}}$, of the random matrix is shown in Fig. 1 (a), for $M=6000$ and it's not uniform. By introducing a mapping function $\varsigma\left(\lambda_{\mathrm{M}}, M\right)$ (as shown in equation (5)), each $\lambda_{\mathrm{M}}$ is converted into a new variable $\lambda$ 'м which is uniformly-distributed in $(-M / 2, M / 2)$, as shown in Fig. 1 (b). The PDF of the normalized spacing of $\lambda^{\prime}$ ' is plotted in Fig. 2, which agrees well with the Wigner distribution:

$$
\begin{equation*}
\lambda_{M}^{\prime}=\frac{M}{2 \pi}\left[\pi+2 \sin ^{-1}\left(\frac{\lambda_{M}}{\sqrt{2 M}}\right)+2 \frac{\lambda_{M}}{\sqrt{2 M}} \frac{\sqrt{2 M-\lambda_{M}^{2}}}{\sqrt{2 M}}\right]-\frac{M}{2} \tag{5}
\end{equation*}
$$

Based on the above approach, it seems that two simulation parameters, $M$ and $\alpha$, may have influence on the statistical properties of the generated normalized impedance matrix $z$. In this paper, with each given
( $M, \alpha$ ), 100,000 normalized matrix, $z$, are generated and the eigenvalues, $\lambda_{z}$, of all the $z$ are grouped into one set that contains 200,000 elements. The values of $M$ and $\alpha$ are chosen and shown in Table 1.


Fig. 1. (a) Distribution of the eigenvalues, $\lambda_{\mathrm{M}}$, of $6000 \times 6000$ sized random matrix corresponding to GOE, and (b) distribution of the mapped eigenvalue, $\lambda^{\prime}{ }_{M}$, converted from $\lambda_{M}$ shown in (a) through equation (5).


Fig. 2. The PDF of the normalized nearest neighbor eigenfrequency spacing for the mapped eigenvalues $\lambda_{\mathrm{M}}$ which agrees with the Wigner distribution.

Table 1: Selections of simulation parameters

| $M$ | $\alpha$ |
| :---: | :---: |
| 500 | $0.1-15$ in a step of 0.1 |
| 1000 | $0.1-15$ in a step of 0.1 |
| 6000 | $1-100$ a step of 1 |

## III. VARIATION OF THE STATISTICS OF $\lambda_{z}$ FOR DIFFERENT VALUES OF $M$

Figures 3 to 5 show the PDFs of the real part, $\operatorname{Re}\left[\lambda_{z}\right]$, and the imaginary part, $\operatorname{Im}\left[\lambda_{z}\right]$, of the eigenvalues of the normalized impedance matrix with different $M$ for $\alpha$ equaling to $0.1,6$ and 15 respectively. It can be seen that the value of $M$ doesn't have significant effect on the statistics of the normalized impedance with a given $\alpha$ while $\alpha<15$. In consideration of the simulation time which consumed most in calculating the eigenvalues of random matrices with high order, $M$ can be chose to 1000.


Fig. 3. (a) PDFs of the real part, and (b) the imaginary part of $\lambda_{z}$ with different values of $M$ when $\alpha$ equals to 0.1 .


Fig. 4. (a) PDFs of the real part, and (b) the imaginary part of $\lambda_{z}$ with different values of $M$ when $\alpha$ equals to 6 .


Fig. 5. (a) PDFs of the real part, and (b) the imaginary part of $\lambda_{z}$ with different values of $M$ when $\alpha$ equals to 15 .

## IV. VARIATION OF THE STATISTICS OF $\lambda_{z}$ FOR DIFFERENT VALUES OF $\alpha$

When $\alpha=0$, the eigenvalues of the normalized impedance matrix are purely imaginary quantities. In this limit, [3] has shown that the eigenvalues are Lorentzian distributed with zero mean and unit width. When $\alpha=\infty$, both the real part and the imaginary part of the eigenvalues will be Gaussian distributed with the mean value equal to 1 and 0 , respectively.

The PDFs of (a) the real part and (b) the imaginary part of the grouped eigenvalues of the normalized impedance matrix with different values of $\alpha$ are shown in Fig. 6. It can be seen that as $\alpha$ increase, the PDF of $\operatorname{Re}\left[\lambda_{z}\right]$ evolves from being peaked between $\operatorname{Re}\left[\lambda_{z}\right]=0$ and $\operatorname{Re}\left[\lambda_{z}\right]=1$, into a Gaussian-type distribution that peaked at $\operatorname{Re}\left[\lambda_{z}\right]=1$ for large $\alpha$, and the PDF of $\operatorname{Im}\left[\lambda_{z}\right]$ begins to
sharpen up, developing a Gaussian appearance, which is in good agreement with the description in [7].

The variances of the real part and the imaginary part of the eigenvalues of $z$ are identical and [7] gives the relation between them and the loss parameter which is shown in equation (6):

$$
\begin{equation*}
\sigma_{\operatorname{Re}\left[\lambda_{z}\right]}^{2}=\sigma_{\operatorname{Im}\left[\lambda_{z}\right]}^{2}=\frac{1}{\pi \alpha}, \quad \text { for } \alpha \gg 1, \tag{6}
\end{equation*}
$$

where, $\sigma^{2}$ is the variance, $\operatorname{Re}\left[\lambda_{z}\right]$ and $\operatorname{Im}\left[\lambda_{z}\right]$ denote the real part and the imaginary part of the eigenvalues respectively.
a)

b)


Fig. 6. (a) PDFs of the real part, and (b) the imaginary parts of $\lambda_{z}$ with different values of $\alpha$.

A more accurate result can be derived from Fig. 7, that is:

$$
\begin{equation*}
\sigma_{\operatorname{Re}\left[\lambda_{z}\right]}^{2}=\sigma_{\operatorname{Im}\left[\lambda_{z}\right]}^{2}=\frac{4}{3 \pi \alpha} . \tag{7}
\end{equation*}
$$

Based on Fig. 8, the relation between the variances of the diagonal elements of $\boldsymbol{z}$ and the loss parameter is:

$$
\begin{equation*}
\sigma_{\operatorname{Re}\left[z_{j j}\right]}^{2}=\sigma_{\operatorname{Im}\left[z_{j j}\right]}^{2}=\frac{1}{\pi \alpha}, \tag{8}
\end{equation*}
$$

where, the $z_{\mathrm{ij}}(\mathrm{j}=1$ or 2$)$ denotes the diagonal element of the normalized impedance matrix $z$.

The relation between the variances of the offdiagonal elements and the loss parameter is shown in Fig. 9 and equation (9), which is in good agreement with that given in [8]:

$$
\begin{equation*}
\sigma_{\operatorname{Re}\left[z_{j}\right]}^{2}=\sigma_{\operatorname{Im}\left[z_{i j}\right]}^{2}=\frac{1}{2 \pi \alpha} . \tag{9}
\end{equation*}
$$



Fig. 7. The variances of real part and imaginary part of the eigenvalues of $z$ vary with increasing $\alpha$.


Fig. 8. The variances of real part and imaginary part of the diagonal elements of $\boldsymbol{z}$ vary with increasing $\alpha$.


Fig. 9. The variances of real part and imaginary part of the off-diagonal elements of $z$ vary with increasing $\alpha$.

## V. EXPERIMENTAL VERIFICATION

To verify the results given in part III and IV, an experiment is carried out on an empty computer case ( $40 \mathrm{~cm} \times 40 \mathrm{~cm} \times 20 \mathrm{~cm}$ ) which is excited by two ports as shown in Fig. 9. The measurement is typically carried by measuring the scattering matrix $\boldsymbol{S}$, which will be transferred to the impedance matrix $\boldsymbol{Z}$, obtained through standard bilinear relationship:

$$
\begin{equation*}
\boldsymbol{Z}=\boldsymbol{Z}_{0}^{1 / 2}(\boldsymbol{I}+\boldsymbol{S})(\boldsymbol{I}-\boldsymbol{S})^{-1} \boldsymbol{Z}_{0}^{1 / 2} \tag{10}
\end{equation*}
$$

where, $\boldsymbol{Z}_{0}$ is a diagonal matrix of the characteristic impedance of the transmission line connected to the ports of cavities which is $50 \Omega$ in our experiment and $I$ is the unit matrix.

In order to realize a larger ensemble of the cavity impedance matrix for analyzing its statistics, a mode stirrer which comprises of a shaft and two metallic coated, orthogonally oriented blades is employed, as shown in Fig. 10. By rotating the mode stirrer in control of the stepper motor, the orientation of the blades is changed and each orientation corresponds to a different inner configuration. The blades are rotated for 100 different orientations in this paper.

For each configuration, the scattering parameters between two ports are measured by network analyzer from 6 GHz to 7 GHz and the number of points is set to 1000.

Then the normalized impedance matrix can be calculated from the cavity impedance matrix through equation (1). The variances of the eigenvalues, the diagonal elements and the off-diagonal elements are listed in Table 2 with the relevant loss parameters calculated by equations (7), (8) and (9) respectively. For each loss parameter, $100,000,2 \times 2$ normalized impedance matrices are generated by doing Monte Carlo simulation with $M=1000$.


Fig. 10. Experimental setup.
To compare the statistics of these generated normalized impedance matrices with different loss parameters, the PDFs of the eigenvalues of $\boldsymbol{z}$ are chosen to be compared. The PDFs of (a) the real part, and (b) the imaginary part of the eigenvalues of $\boldsymbol{z}$ are shown in Fig. 11. It's obvious that the PDFs of the real and imaginary parts of the eigenvalues of the Monte Carlo simulated normalized impedance with the losses listed in Table 2 are almost identical, which are in good agreement with those derived from the measured data.

Table 2: The variances of the eigenvalues and elements of $z$

| $\sigma^{2}\left(\times 10^{-2}\right)$ | $\lambda_{\mathrm{z}}$ | $\mathrm{Z}_{11}$ | $\mathrm{Z}_{22}$ | $\mathrm{Z}_{12}$ | $\mathrm{Z}_{21}$ |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\operatorname{Re}$ | 6.67 | 5.66 | 4.71 | 2.65 | 2.49 |
| $\operatorname{Im}$ | 6.68 | 5.69 | 4.70 | 2.64 | 2.50 |
| $\alpha$ | 6.36 | 5.61 | 6.76 | 6.02 | 6.38 |



Fig. 11. PDFs of: (a) the real part, and (b) the imaginary part of the eigenvalues of the normalized impedance derived from the measured data (red curve) and those from the Monte Carlo simulated normalized impedance with different loss parameters listed in Table 2.

## VI. CONCLUSIONS

It is concluded that, the statistics of the normalized impedance only depends on the cavity loss parameter $\alpha$, which is in good agreement with the theoretical result. When $\alpha$ increases, the variances of the real part and the imaginary part of the eigenvalues, the diagonal elements and the off-diagonal elements of the normalized impedance matrix are damped as a function of $\alpha$ shown in equations (7), (8) and (9) respectively, which has been experimentally verified.

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# Optimization of Impedance Bandwidth of a Stacked Microstrip Patch Antenna with the Shape of Parasitic Patch's Slots 

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#### Abstract

In this paper, a novel configuration of wideband stacked microstrip antenna for $\mathrm{X} / \mathrm{Ku}$ band is presented and analyzed. By cutting five narrow rectangular and one trapezoidal slot on parasitic patch with different dimensions, the impedance bandwidth and resonance frequency of the proposed antenna is adjusted. Also, the effect of incorporated parallel slots on driven patch is examined based on equivalent circuit of E-shaped microstrip antenna. Antenna characteristics are simulated by CST simulator and far-field radiation patterns of simulated and measured results of an array of the proposed antenna are compared.


Index Terms - Equivalent circuit, stacked microstrip antenna, $\mathrm{X} / \mathrm{Ku}$ band.

## I. INTRODUCTION

Low gain, narrow bandwidth and low efficiency are confined microstrip antenna's applications beside their attractive features such as low weight, small size and ease of integration with microwave integrated circuits (MIC) [1].

Suffering from very narrow bandwidth poses efforts to design wideband microstrip antennas. Different methods like cutting slots in microstrip patch antenna [2] and stacking [3] have been reported to enhance the bandwidth of microstrip antennas. Impedance mismatch is reduced by a slot which is cut in microstrip patch antenna. In that way, the bandwidth increases. Also, by using multilayered substrates in microstrip antennas, degree of freedom to optimize antenna's performance characteristics such as bandwidth and gain increases [4].

Based on these approaches, the stacked microstrip antennas have appeared. In these structures, commonly two conducting patches are used in each layer. The bottom patch as a driven patch is excited by a coaxial probe and the upper patch is a parasitic patch [5].

In many reports such as [6] and [7], E-shaped rectangular patch antenna is used as the driven patch in stacked microstrip antennas. By referring to [8], an E-shaped rectangular patch is known as a wideband antenna due to two parallel slots cut into the rectangular patch. So, this antenna can be a proper driven patch to enhance stacked microstrip bandwidth.

In this paper, the E-shaped rectangular patch antenna is chosen as a driven patch. Contrast to common stacked antennas which have a simple rectangular patch as a parasitic patch, in this paper, a rectangular patch with six slits that have different lengths and widths. Also, one trapezoidal slot is cut in parasitic patch. This kind of parasitic patch can add different poles to antennas return loss. In fact, by inserting different slots with different dimensions and shapes in parasitic patch, the bandwidth of stacked antennas can be adjusted and the resonance bandwidth of them can be shifted to expected frequencies based on equivalent circuit of proposed antennas.

According to several applications for $\mathrm{X} / \mathrm{Ku}$ band such as vehicle tracking, weather forecasting radars, dimensions of driven and parasitic patches are optimized to work in $\mathrm{X} / \mathrm{Ku}$ band. The proposed antenna is simulated in CST and simulated results are compared with measurement.

## II. ANTENNA DESIGN AND THEORETICAL CONSIDERATIONS

The geometry of the proposed antenna is presented in Fig. 1. In the present work, the patch is fed by co-axial cable ( 50 ohm ). As shown in Fig. 1, the E- shaped patch is printed on the lower substrate as the driven patch. Dimensions of such patch are optimized to work in $\mathrm{X} / \mathrm{Ku}$ band. Based on [9], the equivalent circuit of E-shaped is illustrated in Fig. 2. It can be seen, $\Delta C$ which is added due to two parallel slots, plays the main role in changing
the input impedance according to the equation 1,2 and 3 , which is modified based on small value of $\Delta C$.

In [9], the $\Delta C$ is given by:

$$
\begin{gather*}
\operatorname{Zin}=\frac{1}{R+j \omega L_{2}+\frac{1}{j \omega C_{2}}},  \tag{1}\\
C_{2}=\frac{\Delta C \cdot C_{1}}{\Delta C+C_{1}} \approx \Delta C,  \tag{2}\\
\Delta C=2 l_{2} \frac{\varepsilon_{0}}{\pi}\left[\ln \left(2 \frac{1+\sqrt{k^{\prime}}}{1-\sqrt{k^{\prime}}}\right)\right]+\ln \operatorname{coth}\left(\frac{\pi w_{2}}{4 h_{2}}\right)+0.013 \frac{h_{2}}{w_{2}}, \tag{3}
\end{gather*}
$$

where

$$
\begin{gather*}
k^{\prime}=\sqrt{1-k^{2}}  \tag{4}\\
k^{2}=\frac{\left(\frac{2\left(2 w_{2}+w f\right)}{w_{2}}-1\right)}{\left(1+\frac{2 w_{2}+w f}{w_{2}}\right)\left(\frac{w f}{w_{2}}\right)} \tag{5}
\end{gather*} .
$$

In equation (3), the length of etched slots along a resonance edge has the main parameter to calculate. So, by varying $l_{2}$ and $\mathrm{w}_{2}$, the input impedance can be controlled. To determine E-shaped antenna's dimensions, at the first step based on [1], the length and width of a rectangular patch are calculated for resonation in desire frequency. The length and width of E-shaped microstrip patch antenna are chosen same as the length and width of a rectangular patch:

$$
\begin{gather*}
L_{P}=\frac{c}{2 f_{r} \sqrt{\frac{\varepsilon_{r}+1}{2}}},  \tag{6}\\
\varepsilon_{\text {reff }}=\frac{\varepsilon_{r}+1}{2}+\frac{\varepsilon_{r}-1}{2}\left[1+12 \frac{h_{1}}{L_{P}}\right]^{-1 / 2},  \tag{7}\\
L_{e f f}=\frac{c}{2 f_{r} \sqrt{\varepsilon_{r e f f}}},  \tag{8}\\
\Delta L=0.421 h \frac{\left(\varepsilon_{\text {reff }}+0.3\right)\left(\frac{L_{P}}{h}+0.264\right)}{\left(\varepsilon_{\text {reff }}-0.258\right)\left(\frac{L_{P}}{h}+0.8\right)} . \tag{9}
\end{gather*}
$$

In the next step, the amount of $\mathrm{C}_{1}$ and $\mathrm{L}_{1}$ which is shown in Fig. 2, are calculated based on [1]. $\Delta C$ should be around 100 times smaller than $C_{1}$ to satisfy the equation (2). According to this point, $l_{2}$ and $\mathrm{w}_{2}$ are estimated. As the result of this analysis, the impedance bandwidth can be adjusted based on equation (1). To improve VSWR, two slits are etched along non resonance edges. In the next step, to enhance the impedance bandwidth, a wideband structure is chosen as the parasitic patch which is located on top layer. A rectangular patch with seven slots is selected to improve band width. According to different lengths and widths of
these slots, the band width of the antenna can control and widens up to $23 \%$. Also, different shapes of such slots have impressive effect on VSWR due to the alternation that is accrued in equivalent circuit of the stacked antenna based on [10]. Dimensions of the proposed stacked antenna are mentioned in Table 1. The thickness of lower layer $\left(\mathrm{h}_{2}\right)$ and top layer $\left(\mathrm{h}_{1}\right)$ are 1.65 mm and RO4003 is chosen as the substrate for both layers in demonstrated structure.


Fig. 1. (a) E-shaped microstrip antenna as the driven patch in lower layer, (b) rectangular microstrip antenna with six rectangular slits and a trapezoidal slot as the parasitic patch in the top layer, and (c) side view of the proposed stacked antenna.


Fig. 2. Equivalent circuit of the E-shaped patch antenna.
Table 1: Dimensions of the proposed stacked microstrip antenna

| Parameters | Dimensions (mm) |
| :---: | :---: |
| Wp | 20 |
| Lp | 30 |
| Ws | 0.3 |
| $\mathrm{W}_{1}$ | 2.5 |
| $\mathrm{W}_{2}$ | 10 |
| $1_{2}$ | 7.5 |
| $\mathrm{W}_{\mathrm{f}}$ | 5 |
| $\mathrm{L}_{\text {s }}$ | 3 |
| L | 15 |
| W | 12 |
| Ls1 | 6.5 |
| Ls2 | 9.5 |
| Ws1 | 2 |
| Ls3 | 8.5 |
| Ws2 | 0.3 |
| Ls4 | 7.5 |
| Ws3 | 0.2 |
| Ls5 | 6.5 |
| Ws4 | 0.1 |
| Ls6 | 6.3 |
| Ws5 | 0.1 |
| Ls7 | 6 |
| Ws6 | 0.1 |
| Ws7 | 0.1 |
| Ls8 | 5.5 |
| $\mathrm{d}_{1}$ | 6 |
| $\mathrm{d}_{2}$ | 5.3 |
| $\mathrm{d}_{3}$ | 4.6 |
| $\mathrm{d}_{4}$ | 4.1 |
| $\mathrm{d}_{5}$ | 3.6 |
| $\mathrm{d}_{6}$ | 3.1 |
| $\mathrm{d}_{7}$ | 2.6 |

In this paper, to design antenna which its center frequency is 12 GHz , the calculated length is 18.3 mm . This dimension causes $\mathrm{C}_{1}$ to become around 1 pF . In that way, by choosing $\Delta C \sim 0.01 \mathrm{pF}$, the dimensions of parallel slots on E-shaped antenna is calculated based on equation (3).

## III. RESULTS AND DISCUSSION

Variation of $S_{11}$ with different values of $l_{2}$ is shown in Fig. 3. As illustrated in Fig. 3, $l_{2}$ as the length of the etched slots along a resonance edge on driven patch, has the significant impact on shifting resonance frequency. By increasing $l_{2}$, the resonance frequency decreases due to increase in electrical length of slots on driven patch.


Fig. 3. Variation of $\mathrm{S}_{11}$ with different values of $l_{2}$.
By adding parasitic patch on E-shaped microstrip antenna, mutual capacitance is added to equivalent circuit of the proposed antenna [12]. Based on [13], this mutual capacitance's value depends on top layer thickness. Variation of reflection coefficient with upper layer thickness is simulated and shown in Fig. 4. By increasing the upper layer thickness, mismatch of the antenna decreases in wide range of frequencies. In that way, the impedance bandwidth will enhance dramatically. This extend in the impedance bandwidth, is the result of the decrease in the mutual capacitance which is created between driven and parasitic patches [11].


Fig. 4. Variation of $S_{11}$ with upper layer thickness.

Finally, to improve antenna's gain, the stacked structure is used as the element of an array. To confirm this, far field pattern of single and array structures are compared in Fig. 5.


Fig. 5. Far field pattern of the proposed single and array antenna.

By considering the plane of the antenna is theta $=90^{\circ}$, for specific application that antenna's gain should be improved between phi $=0^{\circ}$ and $\mathrm{phi}=30^{\circ}$, the proposed antenna has the better gain as the array structure with 29.2 mm distances between two elements.

For the fabricated array antenna which is shown in Fig. 6, array's gain of simulation and measurement of the representative structure are shown in Fig. 7. It can be seen that the simulated and the measured results are in a good agreement. As can be seen in Fig. 7, the main lobe of the proposed antenna is around $\varphi=70^{\circ}$ at the plane $\theta=90^{\circ}$.


Fig. 6. (a) The parasitic patch of proposed antenna, and (b) the driven patch of proposed antenna.


Fig. 7. Antenna far-field radiation pattern at $\theta=90^{\circ}$.

## IV. CONCLUSION

A novel design of wideband stacked microstrip antenna has been constructed by cutting six different slots with different areas on parasitic patch. This modification on parasitic patch antenna shape, enhanced the bandwidth of the microstrip antenna up to $23 \%$, which shows improvement in comparison with the recent existing data [14]. Based on the equivalent circuit of $E$ shaped microstrip antenna, the frequency band that antenna works is adjusted. To improve antenna gain, the proposed antenna has been used as the element of an array. The far-field radiation patterns of simulated and measured results are compared, which shows acceptable agreement.

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# Design of Balanced SIW Filter with Transmission Zeroes and Linear Phase 

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#### Abstract

This paper provides a design method for balanced bandpass filters (BPFs) with high performance based on substrate integrated waveguide (SIW) structure. A novel balanced SIW filter with the characteristics of transmission zeroes, linear phase and wideband common-mode suppression is proposed. By analyzing the equivalent circuits of the proposed SIW filter under differential-mode (DM) and common-mode (CM) excitations, the DM transmission with CM suppression characteristic of the filter is demonstrated. The source-load coupled microstrip lines are introduced to realize the negative coupling and the design method for filters with source-load coupling is given. Good agreement is demonstrated between the simulated and the measured ones


Index Terms - Balanced filter, linear phase, substrate integrated waveguide (SIW), transmission zeroes.

## I. INTRODUCTION

Balanced circuits have drawn much attention as they have higher immunity to environmental noise and low electromagnetic interference compared with singleended circuits. As the key components, various balanced filters have been widely studied and demonstrated [1-7]. In the early times, the microwave differential filters were developed by microstrip line structures, such as the stretched or coupled transmission lines, the coupled stepped impedance resonators (SIR), the stepped impedance slotline multiple-mode resonators (MMR) and the double-sided parallel-strip lines (DSPSL) [1-5]. To overcome the drawbacks of high radiation loss, low power handling capability, low-factor, and maintain the benefits of low-cost, compact size and good integration, the substrate integrated waveguide (SIW) balanced filters was proposed [6,7]. In [6], the balanced bandpass filters (BPFs) are realized by the structures of half-mode substrate integrated waveguide (HMSIW) and folded HMSIW. The common-mode (CM) suppression is achieved by applying a non-coupling slot and the spectral separation of differential-mode (DM)-CM resonances in the HMSIW and folded HMSIW cases, respectively. The proposed BPFs can achieve the CM
rejection level more than 40 dB over a wide frequency range. To improve the filter selectivity, a differential BPF with two transmission zeros is presented in [7] based on SIW structure. The CM suppression is realized by a new balanced SIW section on single-layer substrate technology. However, to meet stringent requirements imposed on the most recent wireless standards, a flat group delay filter response should be guaranteed to avoid signal blur besides sharp rejection.

This paper proposes a balanced SIW BPF with transmission zeroes, linear phase and wideband common-mode suppression. By analyzing the equivalent circuits of the proposed SIW filter under DM and CM excitations, the DM transmission with CM suppression characteristic of the filter is demonstrated. Another innovative point of the paper is that the source-load coupled microstrip lines are introduced and the design method for filters with source-load coupling is given. To the best of our knowledge, there is no reported work done so far on balanced BPFs with both linear phase and highly selectivity. The proposed balanced BPF is designed using the SIW scheme at 10 GHz and can achieve almost perfectly flat group delay over the central $60 \%$ of the pass band.

## II. BALANCED FILTER DESIGN

The balanced filter is designed on F4B substrate, with thickness of 0.5 mm , relative permittivity of 2.65 , and dielectric loss tangent of 0.001 (at 10 GHz ). The geometry of the proposed balanced BPF is shown in Fig. 1 (a). The four-port circuit is ideally symmetric with respect to the vertical and horizontal symmetry plane. It is composed of six SIW cavities which are represented by $R_{l}, R_{2}, R_{3}, R_{4}, R_{l}^{\prime}$, and $R_{4}{ }^{\prime}$, respectively.

## A. Common-mode analysis

Under CM operation, the vertical symmetry plane becomes a perfect magnetic wall and the CM equivalent circuit is shown in Fig. 1 (b). $R_{l}$ and $R_{4}$ are the original resonators of the proposed balanced BPF, which operate in $\mathrm{TE}_{101}$ for the first resonant mode. The cavity $2\left(C_{2}\right)$ and cavity $3\left(C_{3}\right)$ are half of the original resonators $R_{2}$ and $R_{3}$ with the vertical symmetry plane being a magnetic wall
and the other three sidewalls being electric wall. In this case, the modes for $R_{2}$ and $R_{3}$ are $\mathrm{TE}_{101}$ for the first resonant mode. As $R_{l}$ and $R_{4}$ are designed to resonant at the operating frequencies, the resonant frequencies of $C_{2}$ and $C_{3}$ with similar size of $R_{1}$ and $R_{4}$ will not be in the operating pass-band. Thus, it performs a bandstop characteristic under CM excitations. To verify the above inference, simulated frequency responses under CM excitations are given in Fig. 2. We can see that the CM transmission is suppressed to be lower than -17 dB in a wideband.


Fig. 1. Geometry and schematic topologies of the proposed balanced SIW filter: (a) geometry of the balanced BPF, (b) equivalent 2-port half bisection under CM operation, and (c) equivalent 2-port half bisection under DM operation.


Fig. 2. Simulated results of the CM response.

## B. Differential-mode analysis

While for DM operation, the vertical symmetry plane becomes a perfect electric wall, and the DM circuit can be obtained as shown in Fig. 1 (c). $D_{2}$ and $D_{3}$ are half of $R_{2}$ and $R_{3}$ with all four sidewalls being the electric wall. In this case, the modes for $R_{2}$ and $R_{3}$ are $\mathrm{TE}_{102}$ for the first resonant mode.

A 2-port 4-pole generalized chebyshev filter with both high selectivity and linear phase is synthesized with
zeros [2.5j, -2.5j, 1.4,-1.4]. Zeros [2.5j,-2.5j] in the imaginary axis are used to produce transmission zeros and zeros $[1.4,-1.4]$ in the real axis are used to improve the phase. The synthesized S-parameters including magnitude and group delay with center frequency of $f_{0}=10 \mathrm{GHz}$ and bandwidth of $B W=400 \mathrm{MHz}$ are plotted as the dotted curves in Fig. 3, with the coupling matrix [8]:

$$
M=\left[\begin{array}{ccccccc} 
& S & 1 & 2 & 3 & 4 & L \\
S & 0 & 1.0425 & 0 & 0 & 0 & -0.0298 \\
1 & 1.0425 & 0 & 0.9226 & 0 & 0.1471 & 0 \\
2 & 0 & 0.9226 & 0 & 0.6488 & 0 & 0 \\
3 & 0 & 0 & 0.6488 & 0 & 0.9266 & 0 \\
4 & 0 & 0.1471 & 0 & 0.9226 & 0 & 1.4025 \\
L & -0.0298 & 0 & 0 & 0 & 1.4025 & 0
\end{array}\right]
$$

Fig. 3. Synthesized and simulated frequency responses of the equivalent 2-port half bisection under DM operation: (a) S-parameters and (b) group delay.

The dimensions of $d_{1}, d_{2}, d_{3}$ and $l_{m}$ in Fig. 1 (a) for the required $M_{14}, M_{12}, M_{23}$ and $M_{S l}$ can be determined from Fig. 4 (a)-(c) with the method in [9] respectively.

The $50-\Omega$ coupled microstrip lines in Fig. 1 (a) are proposed to realize the source-load coupling in this paper. While magnetic coupling (positive coupling in the coupling matrix) can be achieved with an inductive window between two adjacent SIW resonators [10], the coupled microstrip lines can achieve the electric coupling (negative coupling in the coupling matrix). Thus, both positive and negative couplings can be
realized in the same plane. However, there is no relative handling with the source-load coupling $M_{S L}$ in the existing literature. The proposed $50-\Omega$ coupled microstrip lines to realize the source-load coupling are treated as two coupled resonators in this paper shown in Fig. 5 (a) for the first time. The relationship between the source-load coupling $M_{S L}$ and the distance $g_{t}$ between the coupled microstip lines is shown in Fig. 5 (b). Then the dimension of $g_{t}$ for the required $M_{S L}$ can be determined from Fig. 5 (b) [9].


Fig. 4. Design curves for the 2-port BPF: (a) relationship between the coupling coefficient M14/M23 and the iris distance d between resonator 1 and 4 or resonator 2 and 3 , (b) relationship between the coupling coefficient M12 and the iris distance $d$ between resonator 1 and 2, and (c) relationship between the coupling coefficient MS1 and the insertion length of 1 m .


Fig. 5. Geometry of the source-load coupling and the design curve: (a) geometry of the source-load coupling and (b) relationship between the source-load coupling coefficient $M_{S L}$ and the distance $g_{t}$ between microstip lines.

After optimization, the simulated results of the 2port BPF are plotted as the solid curves in Fig. 3. The mismatch of the group delay in the stop-band is due to the existence of the transmission zeroes. In addition to this, good agreement can be achieved between the synthesized results and the simulated ones.

## C. Design of the balanced filter

The procedure for the design of the balanced SIW filter with both transmission zeros and linear phase is outlined as follows:
Step 1) Determine the requirement of the balanced filter. Based on the desired frequency response, center frequency, bandwidth and transmission zeros can be determined.
Step 2) Design the 2-port filter. The 2-port filter is synthesized according to the requirement in step 1 and the coupling matrix are calculated [8]. Then, the dimensions of the 2-port filter can be determined from the extracted design curves with the method in [9].
Step 3) Realize the balance filter. By duplicating the 2-port filter along the vertical symmetry plane, The balanced filter can be achieved.
Based on the above analysis of the CM and DM operations, a balanced BPF with transmission zeroes, linear phase and wideband common-mode suppression can be achieved with the main design parameters: $g_{t}=1.4$ $\mathrm{mm}, l_{m}=3.29 \mathrm{~mm}, l_{l}=12.87 \mathrm{~mm}, l_{2}=25.28 \mathrm{~mm}, w=13$
$\mathrm{mm}, w_{m}=1.35 \mathrm{~mm}, d_{l}=1.9 \mathrm{~mm}, d_{2}=4.5 \mathrm{~mm}, d_{3}=4.08 \mathrm{~mm}$. The simulated results of the balanced BPF under DM and CM operations are plotted as the dotted curves in Figs. 6 (a) and (b), respectively. The group delay responses of the balanced BPF are plotted as the dotted curves in Fig. 6 (c).


Fig. 6. Measured and simulated responses of the filter: (a) DM responses, (b) CM responses, and (c) group delay responses.

## III. RESULTS AND DISCUSSION

Figure 7 shows the photograph of the fabricated filter. The simulated and measured results of the filter are plotted in Fig. 6. The measured central frequency is 10.02 GHz , and $3-\mathrm{dB}$ bandwidth is 400 MHz . The inband insertion loss and return loss are better than -3.5 dB and -12 dB , respectively. The two transmission zeroes are located at 9.55 GHz and 10.5 GHz . The group delay
equalization is over $60 \%$ of the pass-band. The measured results include the influence of the limited fabrication precision and measurement errors, thus they are somewhat worse than the simulated results


Fig. 7. Photograph of the fabricated differential filter.

## IV. CONCLUSIONS

In this paper, a new balanced SIW BPF with high performances is proposed. The design of the balanced filter is simplified through designing a 2-port filter with high performance and duplicating it along the vertical symmetry plane. The source-load coupled microstrip lines are introduced and the design method for filters with source-load coupling is given. Simulated and measured results show that the presented filter has the performances of linear phase, high out-of-band rejection, and good common suppression which can be applied to the microwave system of high quality.

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# Compact Dual-Wideband BPF Based on Quarter-Wavelength Open Stub Loaded Half-Wavelength Coupled-Line 

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#### Abstract

In this paper, a novel dual-wideband bandpass filter (BPF) is presented by using quarterwavelength open stub loaded half-wavelength coupledline. Equivalent voltage-current analysis method is applied to analyze this structure, which shows it has two tunable transmission zeros and dual-wideband frequency response. As an example, a dual-wideband BPF covering 1.228/1.57/6.8 GHz for GPS (Link 1 and Link 2) and RFID applications is designed, fabricated and measured. The fabricated filter has a compact size of $0.043 \lambda_{\mathrm{g}} \times 0.213 \lambda_{\mathrm{g}}$. The measured results show that the fabricated filter has the merits of low insertion loss, good return loss and high band-to-band isolation. The proposed dual-band BPF also has a very simple physical topology and quick design procedure.


Index Terms - Bandpass filter (BPF), coupled-line, dual-wideband, stub-loaded resonator.

## I. INTRODUCTION

Modern dual-mode communication system requires a dual-band bandpass filter (BPF) to enhance the electrical performance of the radio frequency end. In recent years, many structures have been proposed to meet the above requirement. In [1], two sets of uniform-impedance half-wavelength resonators are used to design a dual-narrowband BPF for 1.8 GHz DCS and 2.4 GHz WLAN applications. A dualpassband BPF with multi-spurious suppression is realized by using asymmetrical stepped-impedance resonators in [2]. In [3], compact dual-band BPFs with controllable bandwidths are proposed by using stub loaded multiple-mode resonator. In [4], the quad-mode resonator is applied to design a compact and highselectivity dual-mode dual-band BPF. Modified coupled-line is another effective structure to design dual-band BPF. It is widely known that coupled-line is a classical structure used in single-band BPF design, mainly due to its compact 1-D planar physical configuration and high passband selectivity. In [5,6], S.

Lee and Y. Lee firstly introduce capacitive or inductive stubs in traditional coupled-line structure to achieve dual-band frequency response, and the transverse dimension of coupled-line-type BPF is decreased simultaneously. However, these two dual-band BPFs suffer from relatively large circuit size, complicated physical topology and design procedure. In the author's previous work [7,8], two stub loaded coupled-line dualband BPFs have been proposed, and a good filter performance and compact circuit size has been achieved. Nevertheless, the insertion loss in [7] and out-of-band rejection in [8] need further improvements. In addition, the bandwidth in [7] cannot meet the requirement of modern dual high-data-rate communication system.

In this paper, a novel quarter-wavelength open stub loaded half-wavelength coupled-line is proposed, which has dual-band frequency performance. By using a halfwavelength transmission line to cascade the proposed two stub loaded coupled-line, a dual-wideband BPF with large dual-band central frequency ratio can be designed. As an example, a dual-wideband BPF for $1.228 / 1.57 \mathrm{GHz}$ GPS and 6.8 GHz RFID applications is designed, fabricated and measured. Equivalent voltagecurrent analysis method is applied to analyze this dualband BPF, and the corresponding design rules are given for the filter design.

## II. THEORY ANALYSIS

## A. ABCD parameters and S parameters

Figure 1 (a) gives the transmission line model of proposed dual-wideband BPF. It consists of two quarter-wavelength open stub loaded half-wavelength coupled-line and one half-wavelength transmission line. In order to analyze this structure, equivalent voltage and current analysis method is used, and the corresponding model is given in Fig. 1 (b). Thus, the $A B C D$ parameters of proposed dual-wideband BPF can be given as follows:

$$
\left[\begin{array}{cc}
A_{F} & B_{F}  \tag{1}\\
C_{F} & D_{F}
\end{array}\right]=\left[\begin{array}{ll}
A_{c i} & B_{c i} \\
C_{c i} & D_{c i}
\end{array}\right]\left[\begin{array}{ll}
A_{t} & B_{t} \\
C_{t} & D_{t}
\end{array}\right]\left[\begin{array}{ll}
A_{c o} & B_{c o} \\
C_{c o} & D_{c o}
\end{array}\right]
$$

where

$$
\left[\begin{array}{ll}
A_{t} & B_{t} \\
C_{t} & D_{t}
\end{array}\right]=\left[\begin{array}{cc}
\cos (2 \theta) & j Z \sin (2 \theta) \\
j Y \sin (2 \theta) & \cos (2 \theta)
\end{array}\right] \quad Y=1 / Z
$$

If even-mode electrical length of coupled-line $\left(\theta_{e}\right)$ equaling to odd-mode electrical length of coupled-line $\left(\theta_{o}\right)$ are assumed, the following two equations can be obtained from the [9] as follows:

$$
\begin{align*}
& {\left[\begin{array}{c}
v_{1}-v_{2} \\
i_{1}-i_{2}
\end{array}\right]=\left[\begin{array}{cc}
\cos (2 \theta) & j Z_{c o} \sin (2 \theta) \\
j Y_{c o} \sin (2 \theta) & \cos (2 \theta)
\end{array}\right]\left[\begin{array}{c}
v_{4}-v_{3} \\
-\left(i_{4}-i_{3}\right)
\end{array}\right],}  \tag{2a}\\
& {\left[\begin{array}{c}
v_{1}+v_{2} \\
i_{1}+i_{2}
\end{array}\right]=\left[\begin{array}{cc}
\cos (2 \theta) & j Z_{c e} \sin (2 \theta) \\
j Y_{c e} \sin (2 \theta) & \cos (2 \theta)
\end{array}\right]\left[\begin{array}{c}
v_{4}+v_{3} \\
-\left(i_{4}+i_{3}\right)
\end{array}\right],} \tag{2b}
\end{align*}
$$

where

$$
\begin{array}{ll}
Z_{c e}=Z_{c} \sqrt{\left(1+k_{c}\right) /\left(1-k_{c}\right)} & Y_{c e}=1 / Z_{c e}, \\
Z_{c o}=Z_{c} \sqrt{\left(1-k_{c}\right) /\left(1+k_{c}\right)} & Y_{c o}=1 / Z_{c o} .
\end{array}
$$

The coupled-line in Fig. 1 (b) has the boundary condition of $v_{3}=-i_{3} Z_{L}=j i_{3} Z_{s} \cot \theta$ and $v_{4}=0$. After substituting these two conditions into the equations (2), the $A B C D$ matrix of quarter-wavelength open stub loaded half-wavelength coupled-line can be derived as:

$$
\begin{gather*}
{\left[\begin{array}{ll}
A_{c i} & B_{c i} \\
C_{c i} & D_{c i}
\end{array}\right]=\left[\begin{array}{ll}
\frac{u_{1}}{u_{5}} & -\frac{u_{3}}{u_{7}}+\frac{u_{1} u_{6}}{u_{5} u_{7}} \\
\frac{u_{2}}{u_{5}} & -\frac{u_{4}}{u_{7}}+\frac{u_{2} u_{6}}{u_{5} u_{7}}
\end{array}\right],}  \tag{3a}\\
{\left[\begin{array}{cc}
A_{c o} & B_{c o} \\
C_{c o} & D_{c o}
\end{array}\right]=\frac{1}{u_{1} u_{4}-u_{2} u_{3}}\left[\begin{array}{cc}
u_{4} u_{5}-u_{2} u_{6} & -u_{1} u_{6}+u_{3} u_{5} \\
-u_{2} u_{7} & -u_{1} u_{7}
\end{array}\right],} \tag{3b}
\end{gather*}
$$

where

$$
\begin{gathered}
u_{1}=-j\left[\left(Z_{c e}+Z_{c o}\right) \sin (2 \theta)\right] / 2, \\
u_{2}=-\cos (2 \theta), \\
u_{3}=j\left[\left(Z_{c o}-Z_{c e}\right) \sin (2 \theta)\right] / 2 \\
u_{4}=\left[\left(Y_{c o}-Y_{c e}\right) Z_{s} \cot \theta \sin (2 \theta)\right] / 2 \\
u_{5}=-j\left[\left(Z_{c o}-Z_{c e}\right) \sin (2 \theta)\right] / 2 \\
u_{6}=j\left[2 Z_{s} \cot \theta \cos (2 \theta)-\left(Z_{c e}+Z_{c o}\right) \sin (2 \theta)\right] / 2, \\
u_{7}=-\frac{2 \cos (2 \theta)+\left(Y_{c e}+Y_{c o}\right) Z_{s} \cot \theta \sin (2 \theta)}{2}
\end{gathered}
$$

Since the proposed dual-wideband BPF is symmetrical, its $S$-parameters can be then given by:

$$
\begin{align*}
& S_{11}=S_{22}=\frac{A_{F}+B_{F} / Z_{0}-C_{F} Z_{0}-D_{F}}{A_{F}+B_{F} / Z_{0}+C_{F} Z_{0}+D_{F}}  \tag{4a}\\
& S_{21}=S_{12}=\frac{2\left(A_{F} D_{F}-B_{F} C_{F}\right)}{A_{F}+B_{F} / Z_{0}+C_{F} Z_{0}+D_{F}} \tag{4b}
\end{align*}
$$



Fig. 1. (a) Transmission line model of proposed dualwideband BPF, and (b) equivalent voltage and current analysis model.

## B. Transmission zeros

The transmission zeros of proposed dual-wideband BPF is dependent on the quarter-wavelength open stub loaded half-wavelength coupled-line and independent on the half-wavelength transmission lines, so that the transmission zeros satisfy:

$$
\begin{equation*}
A_{c i, o} D_{c i, o}=B_{c i, o} C_{c i, o} . \tag{5}
\end{equation*}
$$

After simplifying the equations (3), it will be derived that:

$$
\begin{equation*}
u_{1} u_{4}=u_{2} u_{3} . \tag{6}
\end{equation*}
$$

When $\theta=0, \pi / 2$ and $\pi$ at the designing frequency $f_{0}$, respectively, it can be verified that the equation (6) is built. Thus, the proposed dual-wideband BPF has fixed transmission zeros at $0, f_{0}$ and $2 f_{0}$, respectively, within the frequency range $\left[0,2 f_{0}\right]$. Substituting $u_{1} \sim u_{6}$ into the equation (6), it can be gotten that:

$$
\begin{equation*}
\tan ^{2} \theta=\left(Z_{c} \sqrt{1-k_{c}^{2}}+4 Z_{s}\right) /\left(Z_{c} \sqrt{1-k_{c}^{2}}\right) \tag{7}
\end{equation*}
$$

The proposed dual-wideband BPF has a pair of tunable transmission zeros which are symmetrical along $f_{0}$. Its frequency locations are given as follows:

$$
\begin{gather*}
f_{z 1}=\frac{2 f_{0}}{\pi} \arctan \left(\sqrt{\frac{Z_{c} \sqrt{1-k_{c}^{2}}+4 Z_{s}}{Z_{c} \sqrt{1-k_{c}^{2}}}}\right)  \tag{8a}\\
f_{z 2}=\frac{2 f_{0}}{\pi}\left(\pi-\arctan \left(\sqrt{\frac{Z_{c} \sqrt{1-k_{c}^{2}}+4 Z_{s}}{Z_{c} \sqrt{1-k_{c}^{2}}}}\right)\right) \tag{8b}
\end{gather*}
$$

These two transmission zeros have the relationship of $0<f_{z 1}<f_{0}<f_{z 2}<2 f_{0}$, and repeat at every frequency range $\left[2 n f_{0}, 2(n+1) f_{0}\right]$, where $n$ is an integer.

## C. Design rules

It can be verified that the proposed dual-wideband BPF has a symmetrical frequency response along the design frequency $f_{0}$. That is, two passbands of the proposed dual-wideband BPF has an equal value of absolute bandwidth $B W$. Under the initial designing parameters of $Z=140 \Omega$ and $k_{c}=0.4$, Fig. 2 plots the variation of $f_{c 2} / f_{c 1}$ and $B W / f_{0}$ versus different values of $r_{c}=Z_{c} / Z$ and $r_{s}=Z_{s} / Z$, where $f_{c 1}$ and $f_{c 2}$ represents the central frequency of the first and second passband, respectively. It can be seen in Fig. 2 that $f_{c 2} / f_{c 1}$ increases as $r_{c}$ increases, but it decreases as $r_{s}$ increases. It can be also seen in Fig. 2 that $B W$ increases as $r_{s}$ increases, and as $r_{c}$ increases, BW increases firstly but then decreases. Figure 3 gives the variation of $\left|S_{21}\right|$ and $\left|S_{11}\right|$ versus different values of $Z$ and $k_{c}$ under fixed $r_{c}=r_{s}=1.0$. It can be seen in Fig. 3 (a) that $Z$ has minor effect on $\left|S_{21}\right|$ but it can be used to tune the $\left|S_{11}\right|$ slightly. It can be seen in Fig. 3 (b) that the BW of two passbands becomes wide as $k_{c}$ increases.

In summary, in the dual-wideband design process, the designing parameters $r_{s}$ and $r_{c}$ can be tuned to achieve the desired frequency position of two passbands. The designing parameter $k_{c}$ can be used to control the $B W$ of two passbands and the designing parameter $Z$ can be then tuned to acquire a good return loss. In addition, it should be noted that the BW of two passbands cannot be controlled individually due to its symmetrical frequency response.


Fig. 2. Variation of $f_{c 2} / f_{c 1}$ and $\mathrm{BW} / f_{0}$ versus different values of $r_{c}$ and $r_{s}$.


Fig. 3. Variation of $\left|S_{21}\right|$ and $\left|S_{11}\right|$ versus different values of: (a) $Z\left(k_{c}=0.4\right.$ fixed $)$, and (b) $k_{c}(Z=140 \Omega$ fixed $)$.

## III. SIMULATION AND MEASUREMENT

According to the above discussion, the initial designing parameters of dual-wideband BPF are preselected as $Z_{c}=147 \Omega, k_{c}=0.42, Z=140 \Omega$ and $Z_{s}=150 \Omega$, under which the first passband covers $1.228 / 1.575 \mathrm{GHz}$ and the second passband covers 6.8 GHz . The dualwideband BPF is designed on the substrate ARlon DiClad $880\left(\varepsilon_{r e}=2.2, h=0.508 \mathrm{~mm}, \tan \delta=0.0009\right)$. Figure 4 (a) gives the layout of fabricated dualwideband BPF. In Fig. 4 (a), the half-wavelength microstrip line and the loaded quarter-wavelength stubs are folded, so as to achieve size reduction. The whole structure is optimized by using the full wave EM simulator HFSS to consider the impact of bends, the grounded vias, the impedance discontinuities and the unequal even-/odd-mode phase velocities. The optimized physical dimensions are also labeled in Fig. 4 (a). Figure 4 (b) shows the photograph of fabricated dual-wideband BPF with the circuit size of $0.043 \lambda_{\mathrm{g}} \times 0.213 \lambda_{\mathrm{g}}$, where $\lambda_{\mathrm{g}}$ represents the guided wave-length of $50 \Omega$ microstrip line at the central frequency of the first passband.


Fig. 4. (a) Layout, and (b) photograph of fabricated dual-wideband BPF.

The simulated and measured results of fabricated dual-band BPF are plotted in Fig. 5. Good agreement
can be observed between the simulation and measurement. There are some discrepancies which are attributed to the fabrication error as well as SMA connectors. The measured central frequencies (CFs) and 3 dB FBW of two passbands are $1.54 \mathrm{GHz} / 6.88 \mathrm{GHz}$ and $60 \% / 11.5 \%$, respectively. The measured insertion losses (ILs) at $1.228 \mathrm{GHz}, 1.575 \mathrm{GHz}$ and 6.8 GHz are $0.4 \mathrm{~dB}, 0.4 \mathrm{~dB}$ and 0.9 dB , respectively. The return losses of two passbands are better than 26 dB and 15 dB , respectively. The band-to-band isolation is better than 20 dB from 2.5 GHz to 6.1 GHz .

Table 1 gives a performance comparison with some reported coupled-line-type dual-band BPF. In Table 1, CF, FBW and IL represents the central frequency, fractional bandwidth and insertion loss, respectively. After comparison, it obviously shows that the proposed dual-wideband BPF has the merits of low insertion loss, compact circuit size, wide passband, large dual-band central frequency ratio, simple physical topology and quick design procedure.


Fig. 5. Simulated and measured results of fabricated dual-wideband BPF.

Table 1: Performance comparison with some reported coupled-line-type dual-band BPFs

|  | CF (GHz) | 3 dB FBW | IL at CF (dB) | Circuit Size $\left(\lambda \mathrm{g}^{2}\right)$ |
| :---: | :---: | :---: | :---: | :---: |
| Ref. [5] | $2.4,5.2$ | $8 \%, 3.69 \%$ | $1.6,2.5$ | $0.189 \times 0.733$ |
| Ref. [6] (Filter B) | $2.0,5.0$ | $12 \%, 3 \%$ | $1.0,3.0$ | - |
| Ref. [7] (Filter A) | $2.4,5.8$ | $5.8 \%, 2.1 \%$ | $1.59,2.59$ | $0.312 \times 0.304$ |
| Ref. [8] (Filter B) | $2.48,6.63$ | $43.2 \%, 16.5 \%$ | $0.33,0.74$ | $0.12 \times 0.17$ |
| This Work | $1.54,6.88$ | $60 \%, 11.5 \%$ | $0.4,0.9$ | $0.043 \times 0.213$ |

## IV. CONCLUSION

A dual-wideband BPF covering $1.228 / 1.57 / 6.8 \mathrm{GHz}$ for GPS (Link 1 and Link 2) and RFID applications is presented by using proposed quarter-wavelength open stub loaded half-wavelength coupled-line. The fabricated dual-wideband BPF has a compact circuit area of $0.043 \lambda_{\mathrm{g}} \times 0.213 \lambda_{\mathrm{g}}$. Measured results also show its merits of low insertion loss, good return loss, sharp passband selectivity and good band-to-band isolation.

The proposed filter has simple topology and design procedure. All these merits make it attractive in modern dual-wideband communication system.

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# Study of Various C-Shaped Armatures in Electromagnetic Launcher 

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#### Abstract

The current density distribution on the cross section of the rails is affected by the geometry and dimensions of the rails and armature. This paper analyzed a rectangular railgun that is formed by two parallel rails and an armature with various geometries. Rail thickness $\left(w_{r}\right)$, width $\left(h_{r}\right)$, and separation $\left(s_{r}\right)$ between two rails are equal to $2 \mathrm{~cm}, 4 \mathrm{~cm}$ and 4 cm , respectively. C-shaped armatures have three corners that are named front, back and arm side of armature which rounded step by step. All case studies simulated with the Finite Element Method Three Dimensions (FEM3D). For all steps, the inductance gradient, normal force, current density $(J)$ distribution and maximum values of $J$ are computed. The force between rails and armature named normal force. This force and pressure can be changed the rails and armature form. Friction force is increasing with increasing normal force. Maximum current densities occur at the armature corners and contact section between the rails and armature. These phenomena can produce a hot point that fuse the railgun and must be considered in armature and rail designing. This paper investigates the effect of armature geometry and dimensions on current density distribution, maximum value of current density, inductance gradient and normal force or normal pressure on armature.


Index Terms - Current density, FEM, inductance gradient, normal force, railgun.

## I. INTRODUCTION

Armature and rails are the two main components of a railgun that are usually made up of materials with higher electrical conductivity. In a simple railgun, the magnetic flux density is generated around rails by passing electric current through them. Magnetic force has two components (normal and axial) which are exerted on armature due to magnetic flux density and the current passed through the armature. The axial force $\left(F_{x}\right)$ is proportional to the inductance gradient $\left(L^{\prime}\right)$ and passing current $(I)$ through the rails [1-4]:

$$
\begin{equation*}
F_{x}=\frac{1}{2} L^{\prime} I^{2} . \tag{1}
\end{equation*}
$$

The distribution of electric current density over the
armature is very high at the contact edges between the armature and rails, and sharp corners of the armature. These points become very hot due to Ohmic losses, hence deformed and after each launch reduce working life of the rails $[5-8]$. In recent years, significant advances researches have been reported for the railgun. Armature geometry can be assumed simple shape such as cube C and U -shape [9-15]. Passing currents through the up and bottom of the C -shape cause repulsive force between them. This force causes enormous pressure on the inner cross section of rails. This pressure can lead to rail breakage or rail bending too.

To reduce the losses and normal force on armature (contact with rails), we can reduce the amplitude of the input current. But reducing the amplitude of applied current will be decreased the force on the armature.

In Fig. 1 shows a railgun with C-shape armature in 3D and side view of 2D. The objective of this work is to analyze the C-shape armature with and without any rounded in the front, throat and rear side. These structures are simulated with FEM and calculated the inductance gradient, $J_{\max }$, and normal force. These quantities are dependent on various sizes of armature and rounded radiuses. We presented the optimize dimensions for minimum value of the $J_{\max }$ and maximum value of the inductance gradient.


Fig. 1. Structure of railgun: (a) 3D railgun and (b) side view.

## II. PROBLEM STATEMENT

A railgun consist of two parallel rails and a solid armature. Rails and armature are formed a closed current loop. Both rails made of copper and connected to an electrical power supply, and solid armature made of aluminum. The dimensions of the copper rails are as follows; width $\left(h_{r}\right)$, separation $\left(s_{r}\right)$ and thickness $\left(w_{r}\right)$ are 4,4 , and 2 cm , respectively.

## A. Railgun structure and parameters

Figure 2 (a) shows the rear view of railgun. The width of armature $\left(h_{a}\right)$ is less than or equal rail's width.

Figure 2 (b) displays the side view of C-shape armature with details of dimensions and applied force.

According to Fig. 2 (b), we design three curvatures at the front, rear and throat of the C -shape armature with $R_{1}, R_{2}$ and $R_{3}$ radius, respectively.

In this paper, first C -shape armature without any rounded (Fig. 1), second C-shape armature with rounded in the front, throat and rear side are simulated and analyzed. Inductance gradient, $J_{\max }$, and normal force are calculated for various sizes of $X_{C}, Y_{C}, R_{1}, R_{2}$ and $R_{3}$. Optimized results according to minimum value of the $J_{\max }$ and maximum value of the inductance gradient for various geometries and sizes are presented in the two different tables.

## B. Force diagram

The electromagnetic force $(\boldsymbol{F})$ on the armature is depicted in Fig. 3. For the calculation of the electromagnetic force with ANSYS, we assume that the injected current has a constant amplitude.

We used FEM to compute the magnetic force for two and three-dimensional. For 2D, we first calculated the magnetic energy $\left(E_{m}\right)$ than,

$$
\begin{equation*}
F=\nabla E_{m} \tag{2}
\end{equation*}
$$

and for 3-D simulation,

$$
\begin{equation*}
\vec{F}=\int \vec{J} \times \vec{B} d v \tag{3}
\end{equation*}
$$

where $\boldsymbol{J}$ and $\boldsymbol{B}$ are current density and magnetic flux density, respectively.


Fig. 2. (a) Rear view of railgun, and (b) side view of Cshape armature.


Fig. 3. The electromagnetic force and components.
$F$ has two components, axial force $\left(F_{x}\right)$ and normal force $\left(F_{y}\right)$. The axial force $\left(F_{x}\right)$ is propulsion force that can move the armature along the rails that is shown in Figs. 1-3. The friction force is a function of the normal force that is exerted by the normal force $\left(F_{y}\right)$ and the friction coefficient.

## C. Boundary conditions and modeling

Both rails are connected to electrical power supply and the total current flow is the same in two rails, but opposite directions that is displayed in Fig. 1. According to the Fig. 4 (a), the structure is symmetric to $x-z$ and $x-y$ plans, and only the first quadrant shown in Fig. 4 (b) is modeled.

The $x-y$ plan (in 2D view $y$ axis) is a symmetrical boundary and replaced by "magnetic wall" or $\boldsymbol{H}_{i}=\mathbf{0}$, and the $x$-z plan (in 2D view $z$-axis) is an asymmetrical boundary and can be replaced by "electrical wall" or $\boldsymbol{H}_{\boldsymbol{n}}=\mathbf{0}$. We proposed the three models for 3D simulation of the railgun: 1) a half of the rails and armature by using magnetic wall, 2) one rail and a half of the armature by using electric wall, 3) a half of a rail and a quarter of the armature, that are shown in Figs. 5 (a), (b) and (c), respectively. Finally, this paper modeled only the quadrant of total structure (see Fig. 5 (c)). The symmetrical and asymmetrical boundaries are replaced by magnetic and electrical walls, respectively.


Fig. 4. Boundary conditions in rear view of railgun with C-shape armature.


Fig. 5. 3D railgun: (a) half magnetic wall, (b) half electric wall, and (c) a quadrant of 3D railgun using magnetic and electric walls.

## III. NUMERICAL RESULTS

In this section, inductance gradient, distribution of the current density and normal force are calculated for with and without rounded in each corner. The optimum structures with different size are obtained by considering two factor maximum value of inductance gradient and minimum value of $J_{\max }$.

## A. Inductance gradient and normal force

Table 1 shows the $L^{\prime}, J_{\max }$ and $F_{y}$ for $h_{a}=h_{r}=4 \mathrm{~cm}$ and different values of $X_{C}$ and $Y_{C}$ without rounded all the corners [5]. According to this table, the inductance gradient show minor variations of approximately $2 \%$. The normal force variations show an increase of size more than 2.5 times for different values.

For the maximum current density by the way, a maximum increase less than $20 \%$ is observed. $h_{a}$ is reduced to 1.6 cm , and $L^{\prime}$ obtained 0.5374 and $0.5238 \mu \mathrm{H} / \mathrm{m}$ for $X_{C}=Y_{C}=2 \mathrm{~cm}$ and $X_{C}=Y_{C}=3 \mathrm{~cm}$, respectively.
$L^{\prime}$ and $F_{y}$ are computed for C -shape armature with rounded front side and shown in Table 2. Rounded radius $\left(R_{1}\right)$ equals to $0.50,1.00,1.50$ and 1.90 cm . This Table illustrated that $F_{y}$ decreased slightly with increasing $R_{1}$. The $L^{\prime}$ increased with increasing $R_{1}$. The rate of variations for $L^{\prime}$ for $X_{C}=Y_{C}=3 \mathrm{~cm}$ is larger than other sizes. $L^{\prime}$ and $F_{y}$ are calculated for C -shape armature with rounded front and arm side and shown in Table 3. Rounded radius for arm side $\left(R_{2}\right)$ equals to $0.30,0.36$, 0.40 and 0.50 cm . Finally, back side is rounded with $R_{3}$ radius. $R_{3}$ equals to $0.45,0.90$ and 1.35 cm . Table 4 shows $L^{\prime}$ and $F_{y}$ for different sizes of all dimensions. According to this table, $L^{\prime}$ and $F_{y}$ are increased with
increasing $R_{3}$. $h_{a}$ is reduced to 2 cm , and $L^{\prime}$ obtained $0.5571 \mu \mathrm{H} / \mathrm{m}$ for $X_{C}=Y_{C}=2 \mathrm{~cm}, R_{1}=1.8 \mathrm{~cm}, R_{2}=0.44 \mathrm{~cm}$, $R_{3}=1.35 \mathrm{~cm}$, which is larger than $0.49467 \mu \mathrm{H} / \mathrm{m}$ for $h_{a}=4 \mathrm{~cm}$. For $X_{C}=Y_{C}=3 \mathrm{~cm}, R_{1}=1.8 \mathrm{~cm}, R_{2}=0.2 \mathrm{~cm}$, $R_{3}=1.35 \mathrm{~cm}, L^{\prime}$ is $0.5963 \mu \mathrm{H} / \mathrm{m}$, which is larger than and $0.54771 \mu \mathrm{H} / \mathrm{m}$.

Table 1: The inductance gradient, maximum current density and normal force applied to the C -shape armature without rounded for different value of $X_{C}$ and $Y_{C}$

| $\begin{gathered} X_{C} \\ (\mathrm{~cm}) \end{gathered}$ | $\begin{gathered} Y_{C} \\ (\mathrm{~cm}) \end{gathered}$ | $\begin{gathered} L^{\prime} \\ (\mu \mathrm{H} / \mathrm{m}) \end{gathered}$ | $\begin{gathered} J_{\max } \\ \left(10^{12} \mathrm{~A} / \mathrm{m}^{2}\right) \end{gathered}$ | $\begin{gathered} F_{y} \\ (\mathrm{kN}) \end{gathered}$ |
| :---: | :---: | :---: | :---: | :---: |
| 1 | 1 | 0.4804 | 1.31 | 132 |
| 2 |  | 0.4843 | 1.39 | 254 |
| 3 |  | 0.4844 | 1.55 | 380 |
| 1 | 2 | 0.4812 | 1.32 | 131 |
| 2 |  | 0.4852 | 1.39 | 241 |
| 3 |  | 0.4832 | 1.53 | 349 |
| 1 | 3 | 0.4804 | 1.26 | 115 |
| 2 |  | 0.4823 | 1.27 | 197 |
| 3 |  | 0.4772 | 1.47 | 276 |

Table 2: The inductance gradient and normal force applied to the C-shape armature with rounded at front side

|  | $X_{C}=Y_{C}=1 \mathrm{~cm}$ |  | $X_{C}=Y_{C}=2 \mathrm{~cm}$ |  | $X_{C}=Y_{C}=3 \mathrm{~cm}$ |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $R_{1}$ <br> $(\mathrm{~cm})$ | $F_{y}$ <br> $(\mathrm{kN})$ | $L^{\prime}$ <br> $(\mu \mathrm{H} / \mathrm{m})$ | $F_{y}$ <br> $(\mathrm{kN})$ | $L^{\prime}$ <br> $(\mu \mathrm{H} / \mathrm{m})$ | $F_{y}$ <br> $(\mathrm{kN})$ | $L^{\prime}$ <br> $(\mu \mathrm{H} / \mathrm{m})$ |
| 0.50 | 129 | 0.4808 | 237 | 0.4870 | 271 | 0.4812 |
| 1.00 | 125 | 0.4817 | 232 | 0.4885 | 268 | 0.4881 |
| 1.50 | 121 | 0.4832 | 226 | 0.4919 | 271 | 0.4969 |
| 1.90 | 117 | 0.4861 | 222 | 0.4962 | 274 | 0.5061 |

Table 3: The inductance gradient and normal force applied to the C-shape armature with rounded at front and arm side

| $X_{C}$ <br> $(\mathrm{~cm})$ | $Y_{C}$ <br> $(\mathrm{~cm})$ | $R_{1}$ <br> $(\mathrm{~cm})$ | $R_{2}$ <br> $(\mathrm{~cm})$ | $F_{y}$ <br> $(\mathrm{kN})$ | $L^{\prime}$ <br> $(\mu \mathrm{H} / \mathrm{m})$ |
| :---: | :---: | :---: | :---: | :---: | :---: |
| 2.40 | 2.40 | 1.60 | 0.36 | 225 | 0.4952 |
| 2.40 | 2.00 | 1.60 | 0.30 | 254 | 0.4961 |
| 2.40 | 1.80 | 1.00 | 0.50 | 234 | 0.4876 |
| 2.00 | 2.00 | 1.00 | 0.40 | 197 | 0.4867 |
| 1.60 | 2.00 | 1.00 | 0.30 | 164 | 0.4850 |

Table 4: The inductance gradient and normal force applied to the C-shape armature with rounded at front, back and arm side

|  | $X_{C}=Y_{C}=2 \mathrm{~cm}$ |  | $X_{C}=Y_{C}=3 \mathrm{~cm}$ |  |
| :---: | :---: | :---: | :---: | :---: |
|  | $R_{1}=1.8 \mathrm{~cm}, R_{2}=0.44 \mathrm{~cm}$ | $R_{1}=1.8 \mathrm{~cm}, R_{2}=0.2 \mathrm{~cm}$ |  |  |
| $R_{3}$ | $F_{y}(\mathrm{kN})$ | $L^{\prime}(\mu \mathrm{H} / \mathrm{m})$ | $F_{y}(\mathrm{kN})$ | $L^{\prime}(\mu \mathrm{H} / \mathrm{m})$ |
| 0.45 | 183 | 0.49037 | 263 | 0.5003 |
| 0.90 | 184 | 0.49102 | 267 | 0.5349 |
| 1.35 | 185 | 0.49467 | 274 | 0.5477 |

## B. Optimization according to $L^{\prime}$ and maximum value of current density

We want to reduce the maximum value of current density and increase inductance gradient. For both conditions two tables are presented. Table 5 shows the optimum structures according to inductance gradient. The maximum value of $L^{\prime}$ is $0.53555 \mu \mathrm{H} / \mathrm{m}$ for the C shape armature without rounded corners. When all corners are rounded, $L^{\prime}$ increasing to 0.54771 and $0.59625 \mu \mathrm{H} / \mathrm{m}$ for $h_{a}$ equals to 4 and 2 cm , respectively.

Table 6 shows the minimum value of $J_{\max }$. According to this table, minimum value of $J_{\max }$ is $1.09 \times 10^{12} \mathrm{~A} / \mathrm{m}^{2}$ for rounded all three corners.

Table 5: Optimization according to maximum value of the inductance gradient for various geometries
(Units: $L^{\prime}(\mu \mathrm{H} / \mathrm{m})$ and $J_{\max }\left(10^{12} \mathrm{~A} / \mathrm{m}^{2}\right)$ )

| $X_{C}$ | $Y_{C}$ | $R_{1}$ | $R_{2}$ | $R_{3}$ | $h_{a}$ | $J_{\max }$ | $L^{\prime}$ |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| 3 | 3 | 1.8 | 0.44 | 1.35 | 2 | 4.30 | 0.5962 |
| 3 | 3 | 1.8 | 0.44 | 1.35 | 4 | 1.97 | 0.5477 |
| 2.4 | 2 | 1.6 | 0.3 | - | 4 | 1.40 | 0.4961 |
| 3 | 3 | 1.9 | - | - | 4 | 1.39 | 0.5061 |
| 2 | 2 | - | - | - | 1.6 | 2.16 | 0.5356 |

Table 6: Optimization according to minimum value of the maximum current density for various geometries (Unit: cm)

| $X_{C}$ | $Y_{C}$ | $R_{1}$ | $R_{2}$ | $R_{3}$ | $h_{a}$ | $J_{\max }$ <br> $\left(10^{12} \mathrm{~A} / \mathrm{m}^{2}\right)$ | $L^{\prime}$ <br> $(\mu \mathrm{H} / \mathrm{m})$ |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| 2 | 2 | 1.8 | 0.2 | 1.35 | 4 | 1.09 | 0.49088 |
| 2 | 2 | 1.00 | 0.4 | - | 4 | 1.22 | 0.48674 |
| 3 | 3 | 0.5 | - | - | 4 | 1.25 | 0.48126 |
| 2 | 2 | - | - | - | 4 | 1.39 | 0.48526 |
| 1 | 3 | - | - | - | 4 | 1.26 | 0.48040 |

## C. Current and normal force distribution on the armature

Due to the skin effect, the current tends to flow on the outer surface on the armature. Figure 6 shows the current density distribution on the quadrant of C -shape armature for $X_{C}=Y_{C}=3 \mathrm{~cm}$ with rounded in all corners. For $h_{a}=4$ and 2 cm , these distributions are shown in Figs. 6 (a) and (b), respectively. Velocity skin effect can be by higher current density concentrations at the outer edge of rear armature surface.

With compared between Figs. 6 (a) and (b), can be said the $J_{\max }$ increased with decreasing $h_{a}$. Figure 7 shows the normal force distribution on the quadrant of C-shape armature for $X_{C}=Y_{C}=3 \mathrm{~cm}$ with rounded in all corners. For $h_{a}=4$ and 2 cm , these distributions are shown in Figs. 7 (a) and (b), respectively.

Figure 8 shows the current density distribution on the quadrant of C-shape armature for $X_{C}=Y_{C}=2 \mathrm{~cm}$ with rounded in all corners. For $h_{a}=4$ and 2 cm , these distributions are shown in Figs. 8 (a) and (b), respectively.

According to this figure, the $J_{\max }$ occurs in two places. That is located at the junction of rails and front and back side of armature. The $J_{\max }$ at the arm side in Fig. 8 increased than in Fig. 6. With compared between Figs. 8 (a) and (b), can be said the current density is increased with decreasing $h_{a}$. Figure 9 shows the normal force distribution on the quadrant of C -shape armature for $X_{C}=Y_{C}=2 \mathrm{~cm}$ with rounded in all corners. For $h_{a}=4$ and 2 cm , these distributions are shown in Figs. 9 (a) and (b), respectively.


Fig. 6. Current density distribution on the C -shape armature for $X_{C}=Y_{C}=3 \mathrm{~cm}$ : (a) $h_{a}=4 \mathrm{~cm}$ and (b) $h_{a}=2 \mathrm{~cm}$.


Fig. 7. Normal force distribution on the C -shape armature for $X_{C}=Y_{C}=3 \mathrm{~cm}$ : (a) $h_{a}=4 \mathrm{~cm}$ and (b) $h_{a}=2 \mathrm{~cm}$.


Fig. 8. Current density distribution on the C -shape armature for $X_{C}=Y_{C}=2 \mathrm{~cm}$ : (a) $h_{a}=4 \mathrm{~cm}$ and (b) $h_{a}=2 \mathrm{~cm}$.


Fig. 9. Normal force distribution on the C -shape armature for $X_{C}=Y_{C}=2 \mathrm{~cm}$ : (a) $h_{a}=4 \mathrm{~cm}$ and (b) $h_{a}=2 \mathrm{~cm}$.

## IV. CONCLUSION

This paper investigated the effect of C -shape armature geometry on the inductance gradient, normal force and the maximum electrical current density. According to the results of this paper can be said, increasing $X_{C}$ results in the slightly variations of $L^{\prime}$, increase the $J_{\max }$ and $F_{y}$. Increasing $Y_{C}$ results in the slightly variations of $L^{\prime}$ and $J_{\max }$ and decrease the $F_{y}$. Variations of the all rounded radius result in slightly on the normal force. Increasing the $X_{C}$ and $Y_{C}$ result in the effect of $R_{1}, R_{2}$ and $R_{3}$ on $L^{\prime}$ and $J_{\max }$ and $F_{y}$ will be more.

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# Tesla Transformer and its Response with Square Wave and Sinusoidal Excitations 

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#### Abstract

This paper analyses the output of Tesla transformer from input defined as square wave and sine wave and its transfer function obtained from its equivalent circuit. The transfer function presented is analyzed in terms of the time, and the output is obtained when applying an input defined as a step and a sine function. When using square wave, the high gain obtained is proved that is due to a sum of responses obtained through positive and negative step that forms the square wave. However, the gain obtained when the excitation is a sine wave is higher than square wave excitation. Thus, in this paper is shown that the Tesla transformer works with sinusoidal excitation too, and present higher gain than square wave excitation, both higher than expected in classical transformer theory (turns ratio). All analysis presented were based in simulating operation using MATLAB® comparing with experimental data.


Index Terms - Pulse transformers, resonance, Tesla transformers, transfer function, transformers.

## I. INTRODUCTION

Tesla transformer [1,2] is a pulse transformer [3,4] that works at double resonance [5], used to generate high voltages, and so to generates high energy applied to systems as particle accelerators (particle colliders) [6], and others [7]. The theoretical foundation of Tesla transformer defines a double capacitive-inductive circuit, where the primary is excited by a square wave, which resonates with secondary, increasing the output voltage to kilovolts or megavolts.

Several works analyzing the Tesla transformer and the base of the high voltage that is an exception to the rule of the classical transformer theory (turns ratio) [8]. Example is the works of Costa [9-11], which analyzes the effects of induced electromotive force (EMF) at transformers built by planar and ring coils [12], effects of parasitic capacitances [13], going to the resonance with square wave excitation [14]. In these works, a transfer function is obtained, which is based in a specific response, whose result to square wave
excitation defines a sum of responses that generates very high gains [1].

In the same way, using experimental results and other analysis of this response, an interesting result about Tesla transformer resonance is found in [15], where the excitation is a sine wave, whose response is higher than the found results of square wave excitation.

New analysis of this system are realized here, which is based in the transfer function of the Tesla transformer, whose parameters are referred to capacitive, inductive and resistive elements, instead of resonance frequencies shown at [1,10-12]. Thus, in this work are presented these results, which are simulated with MATLAB®, as well as experimental, showing that the Tesla transformer presents higher gain when excited with sinusoidal wave, than excited by square wave.

Thus, this paper is presented as follows: in Section II is presented the equivalent circuit and its transfer function formulation. In Section III is shown step response, as well as transient response to sinusoidal excitation. In Section IV are analyzed the responses at steady state for these excitation forms, showing a comparative between gains and, at Section V are presented the conclusions of this work.

## II. EQUIVALENT CIRCUIT AND TRANSFER FUNCTION OF TESLA TRANSFORMER

Considering the circuit shown in Fig. 1 (a), that is the equivalent circuit of the Tesla transformer, which is shown based on impedances at Fig. 1 (b), where:

$$
\begin{align*}
& Z_{1}=\frac{1}{s C_{1}} / / s L_{1}=\frac{s L_{1}}{1+s^{2} L_{1} C_{1}}, \\
& Z_{2}=s M, \\
& Z_{3}=\frac{1}{s C_{2}} / / s L_{2}=\frac{s L_{2}}{1+s^{2} L_{2} C_{2}},  \tag{1}\\
& Z_{R_{1}}=R_{1}, \\
& Z_{R_{2}}=R_{2},
\end{align*}
$$

then, the transfer function $G(s)=V_{0}(s) / V_{i}(s)$ is:

$$
\begin{equation*}
G(s)=\frac{V_{0}(s)}{V_{i}(s)}=\frac{a s}{f s^{4}+d s^{3}+e s^{2}+c s+b} \tag{2}
\end{equation*}
$$

where

$$
\begin{align*}
& a=L_{1} L_{2}, \\
& b=\left(L_{1}+L_{2}+M\right) R_{1}, \\
& c=\left(L_{2}+M\right) L_{1},  \tag{3}\\
& d=C_{2} L_{1} L_{2} M, \\
& e=\left(\left(C_{1}+C_{2}\right) L_{1} L_{2}+\left(C_{1} L_{1}+C_{2} L_{2}\right) M\right) R_{1}, \\
& f=C_{1} C_{2} L_{1} L_{2} M R_{1},
\end{align*}
$$

being $R_{1}, R_{2}$ the resistances, $L_{1}, L_{2}$ the inductances, $C_{1}$, $C_{2}$ the capacitances and $M$ the mutual inductance, with index 1 and 2 being referenced to the primary and secondary, respectively.


Fig. 1. (a) Equivalent circuit of Tesla transformer, and (b) equivalent circuit based on impedances.

Applying impulse to this transfer function and obtaining the inverse Laplace transform, we found:

$$
\begin{equation*}
f_{\uparrow}(t)=a \sum_{k}\left(k e^{k t} /\left(4 f k^{3}+3 d k^{2}+2 e k+c\right)\right) \tag{4}
\end{equation*}
$$

with $k$ being the roots of the polynomial in $w$ :

$$
\begin{equation*}
P(w)=f w^{4}+d w^{3}+e w^{2}+c w+b \tag{5}
\end{equation*}
$$

with $a, b, c, d, e$ and $f$ defined as shown previously (Eq. (3)).

The impulse response of this function is shown in Fig. 2, where is observed that the transfer function present real and complex conjugate exponential terms (roots of the polynomial $P(w)$ ), what defines exponential and sinusoidal functions at response.


Fig. 2. (a) Impulse response of Tesla transformer, and (b) zoom showing double sinusoidal response.

## III. RESPONSES OF TESLA TRANSFORMER TO SQUARE WAVE AND SINUSOIDAL EXCITATIONS

Based on transfer function $G(s)$ (Eq. (2)), applying unitary step $\left(V_{i}(s)=1 / s\right)$, the response is:

$$
\begin{equation*}
V_{0}(s)=\frac{a s}{f s^{4}+d s^{3}+e s^{2}+c s+b} \frac{1}{s} \tag{6}
\end{equation*}
$$

Making the inverse Laplace transform, then the result found is:

$$
\begin{equation*}
f(t)=a \sum_{k}\left(e^{k t} /\left(4 f k^{3}+3 d k^{2}+2 e k+c\right)\right) \tag{7}
\end{equation*}
$$

with $k$ being the roots of the polynomial in $w$ :

$$
\begin{equation*}
P(w)=f w^{4}+d w^{3}+e w^{2}+c w+b \tag{8}
\end{equation*}
$$

which can be seen at Fig. 3, for the specific case where: $R_{1}=0.5 \Omega, R_{2}=0.89 \Omega, L_{1}=0.433 \mu H, L_{2}=1.85 \mu H$, $C_{1}=59.5 \mathrm{p} F, C_{2}=52.5 \mathrm{pF}$ and $M=2.801 \mu H$, as data found in [9-11], referring to planar transformer with 10 turns at primary coil and 20 turns at secondary coil.


Fig. 3. (a) Step response of the Tesla transformer, and (b) zoom showing double sinusoidal oscillation.

Thus, when applied an inverted unitary step (negative sign), the result for this function is only the inverted sign of the function $f(t)$.

By other side, considering the application of sinusoidal excitation to $G(s)$, or:

$$
\begin{equation*}
V_{0}(s)=\frac{a s}{f s^{4}+d s^{3}+e s^{2}+c s+b} \frac{\omega}{s^{2}+\omega^{2}}, \tag{9}
\end{equation*}
$$

and applying the inverse Laplace transform, the result found is:

$$
\begin{align*}
& v_{0}(t)=\frac{a \omega\left(\left(b-e \omega^{2}+f \omega^{4}\right) \cos (\omega t)+\omega\left(c-d \omega^{2}\right) \sin (\omega t)\right)}{b x+\omega^{2} y+f^{2} \omega^{8}} \\
& -a \omega\left[f^{2} \omega^{4} \sum_{k}\left(\frac{k^{3} e^{k t}}{q(k)}\right)-e^{2} \omega^{2} \sum_{k}\left(\frac{k e^{k t}}{q(k)}\right)-f^{2} \omega^{6} \sum_{k}\left(\frac{k e^{k t}}{q(k)}\right)\right. \\
& -d^{2} \omega^{4} \sum_{k}\left(\frac{k e^{k t}}{q(k)}\right)-b d \sum_{k}\left(\frac{k^{2} e^{k t}}{q(k)}\right)+c d \omega^{2} \sum_{k}\left(\frac{k e^{k t}}{q(k)}\right) \\
& +b f \sum_{k}\left(\frac{k^{3} e^{k t}}{q(k)}\right)-b f \omega^{2} \sum_{k}\left(\frac{k e^{k t}}{q(k)}\right)+2 e f \omega^{4} \sum_{k}\left(\frac{k e^{k t}}{q(k)}\right) \\
& +b c \sum_{k}\left(\frac{e^{k t}}{q(k)}\right)-c f \omega^{2} \sum_{k}\left(\frac{k^{2} e^{k t}}{q(k)}\right)-d e \omega^{2} \sum_{k}\left(\frac{k^{2} e^{k t}}{q(k)}\right) \\
& \left.-e f \omega^{2} \sum_{k}\left(\frac{k^{3} e^{k t}}{q(k)}\right)-b d \omega^{2} \sum_{k}\left(\frac{e^{k t}}{q(k)}\right)+b e \sum_{k}\left(\frac{k e^{k t}}{q(k)}\right)\right] / \\
& \left(b x+\omega^{2} y+f^{2} \omega^{8}\right), \tag{10}
\end{align*}
$$

where $x=b-2 e \omega^{2}+2 f \omega^{4}$ and $y=c^{2}-\left(2 c d+e^{2}\right) \omega^{2}+$ $\left(d^{2}-2 e f\right) \omega^{4}$ and,

$$
\begin{equation*}
q(k)=4 f k^{3}+3 d k^{2}+2 e k+c \tag{11}
\end{equation*}
$$

For this case, using the same parameters previously applied to step excitation example $\left(R_{1}=0.5 \Omega, R_{2}=0.89 \Omega\right.$, $L_{1}=0.433 \mu H, L_{2}=1.85 \mu H, C_{1}=59.5 \mathrm{p} F, C_{2}=52.5 \mathrm{p} F$ and $M=2.801 \mu H$ ), the transient response is shown at Fig. 4, considering an excitation at low frequencies.

This same output can be seen as:

$$
\begin{equation*}
V_{0}(s)=\frac{p(s)}{q(s)} \frac{\omega}{s^{2}+\omega^{2}} \tag{12}
\end{equation*}
$$

where the polynomial $q(s)=f s^{4}+d s^{3}+e s^{2}+c s+b$ can be seen as:

$$
\begin{equation*}
q(s)=\left(s+q_{1}\right)\left(s+q_{2}\right) \cdots\left(s+q_{4}\right) \tag{13}
\end{equation*}
$$

whose roots are real and complex conjugate, may present all roots distinct, as well as with multiplicity, with known results of the linear systems. In both cases, the steady state response is:

$$
\begin{equation*}
v_{0 s s}(t)=Y|G(j \omega)| \sin (\omega t+\varphi) \tag{14}
\end{equation*}
$$

with $\phi$ being an angle lag and $Y$ the peak at output.


Fig. 4. Responses of Tesla transformer at low frequencies to sinusoidal excitation, where all low frequencies occur an overlap of responses as shown in [1].

## IV. RESPONSES OF TESLA TRANSFORMER FOR STEADY STATE

Considering steady state, the Tesla transformer shows an output that can present low or high amplitude, depending on the excitation frequency at input. Both in the case of the square wave excitation as the sinusoidal excitation, according to excitation frequency tends to resonance, this gain increases rapidly, reaching high values, which do not follow classical transformer theory (turn ratio).

Considering first the input excitation as a square wave, we have that the step response is given by Eq. (7). Consequently, the excitation with an inverted step (step with negative sign) generates this same response with negative sign. How a square wave can be seen as a sequence of steps up and down, accordingly shown previously, then the response of the Tesla transformer for low frequencies (without resonance) is a series of responses up and down over each rise and fall of the square wave. However, as the square wave frequency increases, these responses overlap, summing up when the responses peak have same sign and subtracting when have inverted signs. These results can be seen at Fig. 5.


Fig. 5. Response of Tesla transformers to square wave at rise and fall: (a) sum and (b) subtraction.

When the square wave frequency approaches the frequency of the system response, this sum of responses
increases output voltage, as shown at Fig. 6.
Also, when the square wave frequency tends to frequency of the response, the system reaches resonance, giving an output with high gain, defined by:

$$
\begin{align*}
v_{0}(t)= & 2.023 \times 10^{5} / \exp \left(3.361 \times 10^{10} t\right)- \\
& 5.021 \times 10^{5} / \exp \left(1.26 \times 10^{6} t\right)+ \\
& 0.29 \cos \left(1.307 \times 10^{8} t\right) / \exp \left(3.55 \times 10^{4} t\right)+ \\
& 0.52 \sin \left(1.3075 \times 10^{8} t\right) / \exp \left(3.55 \times 10^{4} t\right) \tag{15}
\end{align*}
$$

shown at Fig. 7, that is the result for the specific case to values of inductances, capacitances and resistances found in [9-11] for the case of the planar transformer with 10 turns at primary and 20 turns at secondary, which presents in simulation result the gain $G=v_{0} / v_{i}=465$.


Fig. 6. Resonance of Tesla coil; frequency of square wave approximately equal to frequency of step response: (a) simulated response for transient response (sum of responses), and (b) experimental result.

(a)

(b)

Fig. 7. Steady state of Tesla transformer excited with square wave in resonance: (a) general response and (b) zoomed.

By other side, considering sinusoidal excitation, on experimental results found in [15], we see that the output at resonance is greater than square wave excitation. Taking the results of the Eq. (9), we have at low frequencies the result shown in Fig. 4. As the sinusoidal excitation frequency increases, approaching to resonance frequency, the system responds with a higher growth than sum of responses of the square wave excitation.

The resonance frequency of Tesla transformer is reached when:

$$
\begin{equation*}
\omega=\frac{1}{\sqrt{L_{1} C_{1}}}=\frac{1}{\sqrt{L_{2} C_{2}}} \tag{16}
\end{equation*}
$$

As this value of $\omega$ is a pole of Eq. (9), the system tends to present an output with infinite growth (making $s=j \omega$ ). In this way, as seen mathematically, the system output rapidly increases, as the case of the shown example of the Eq. (15), what can be seen at Fig. 8, where the gain at steady state is $G=v_{0} / v_{i}=719.1$, since that the input is unitary.

Comparing the gain values obtained with square wave excitation and sinusoidal excitation at their maximum peaks, we find:

$$
\begin{equation*}
G_{\mathrm{sin}} / G_{s q}=719.1 / 465=1.546 . \tag{17}
\end{equation*}
$$

This result, when compared with experimental results as example shown in Fig. 6, we see that the gain is lesser due to limitations of the used equipment, but does not invalidate the obtained results.

(a)

(b)

(c)

Fig. 8. Resonant response of Tesla transformer to sinusoidal excitation: (a) transient response, (b) general response, and (c) zoomed response of steady state.

## V. CONCLUSION

In this paper was seen the Tesla transformer response at square wave and sinusoidal excitation, where was obtained the transfer function and the responses of these inputs in time domain. It is noted both mathematically as experimentally the effects of high gain due to these inputs, proving that the square wave excitation defines an output, whose response is a sum of step responses (positive and negative), and with sinusoidal excitation, the gain is higher than square wave at steady state. Thus, it is shown that the Tesla transformer operates with sinusoidal excitation and the obtained gains for this case are higher than obtained gains referring to square wave excitation, as shown both simulation as experimental, for the presented specific case, as shown in [15].

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